Datasheet

RENESAS

RL78/G12

RENESAS MCU

R01DS0193EJ0210
Rev.2.10
Mar 25, 2016

True Low Power Platform (as low as 63 µA/MHz), 1.8V to 5.5V operation,
2 to 16 Kbyte Flash, 31 DMIPS at 24MHz, for General Purpose Applications

1. OUTLINE

1.1 Features

Ultra-low power consumption technology
- V_{DD} = single power supply voltage of 1.8 to 5.5 V which can operate at a low voltage
- HALT mode
- STOP mode
- SNOOZE mode

RL78 CPU core
- CISC architecture with 3-stage pipeline
- Minimum instruction execution time: Can be changed from high speed (0.04167 µs: @ 24 MHz operation with high-speed on-chip oscillator) to ultra-low speed (1 µs: @ 1 MHz operation)
- Address space: 1 MB
- General-purpose registers: (8-bit register x 8) x 4 banks
- On-chip RAM: 256 B to 2 KB

Code flash memory
- Code flash memory: 2 to 16 KB
- Block size: 1 KB
- Prohibition of block erase and rewriting (security function)
- On-chip debug function
- Self-programming (with flash shield window function)

Data flash memory Note
- Data flash memory: 2 KB
- Back ground operation (BGO): Instructions are executed from the program memory while rewriting the data flash memory.
- Number of rewrites: 1,000,000 times (TYP.)
- Voltage of rewrites: V_{DD} = 1.8 to 5.5 V

High-speed on-chip oscillator
- Select from 24 MHz, 16 MHz, 12 MHz, 8 MHz, 6 MHz, 4 MHz, 3 MHz, 2 MHz, and 1 MHz
- High accuracy: +/- 1.0 % (V_{DD} = 1.8 to 5.5 V, T_A = -20 to +85 °C)

Operating ambient temperature
- T_A = -40 to +85 °C (A: Consumer applications, D: Industrial applications)
- T_A = -40 to +105 °C (G: Industrial applications) Note

Power management and reset function
- On-chip power-on-reset (POR) circuit
- On-chip voltage detector (LVD) (Select interrupt and reset from 12 levels)

DMA (Direct Memory Access) controller Note
- 2 channels
- Number of clocks during transfer between 8/16-bit SFR and internal RAM: 2 clocks

Multiplier and divider/multiply-accumulator
- 16 bits x 16 bits = 32 bits (Unsigned or signed)
- 32 bits x 32 bits = 32 bits (Unsigned)
- 16 bits x 16 bits + 32 bits = 32 bits (Unsigned or signed)

Serial interface
- CSI : 1 to 3 channels
- UART : 1 to 3 channels
- Simplified I^2C communication : 0 to 3 channels
- I^2C communication : 1 channel

Timer
- 16-bit timer : 4 to 8 channels
- 12-bit interval timer : 1 channel
- Watchdog timer : 1 channel (operable with the dedicated low-speed on-chip oscillator)

A/D converter
- 8/10-bit resolution A/D converter (V_{DD} = 1.8 to 5.5 V)
- 8 to 11 channels, internal reference voltage (1.45 V), and temperature sensor Note

I/O port
- I/O port: 18 to 26
  (N-ch open drain I/O [withstand voltage of 6 V]: 2, N-ch open drain I/O [V_{DD} withstand voltage]: 4 to 9)
- Can be set to N-ch open drain, TTL input buffer, and on-chip pull-up resistor
- Different potential interface: Can connect to a 1.8/2.5/3 V device
- On-chip key interrupt function
- On-chip clock output/buzzer output controller

Others
- On-chip BCD (binary-coded decimal) correction circuit

Note Can be selected only in HS (high-speed main) mode.

Remark The functions mounted depend on the product.
See 1.7 Outline of Functions.

* **There is difference in specifications between every product. Please refer to specification for details.**

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○ ROM, RAM capacities

Code flash	Data flash	RAM	20 pins	24 pins	30 pins
16 KB	2 KB	2 KB	—	—	R5F102AA
	—		—	—	R5F103AA
	2 KB	1.5 KB	R5F1026A Note 1	R5F1027A Note 1	—
	—		R5F1036A Note 1	R5F1037A Note 1	—
12 KB	2KB	1 KB	R5F10269 Note 1	R5F10279 Note 1	R5F102A9
	—		R5F10369 Note 1	R5F10379 Note 1	R5F103A9
8 KB	2 KB	768 B	R5F10268 Note 1	R5F10278 Note 1	R5F102A8
	—		R5F10368 Note 1	R5F10378 Note 1	R5F103A8
4 KB	2KB	512 B	R5F10267	R5F10277	R5F102A7
	—		R5F10367	R5F10377	R5F103A7
2 KB	2 KB	256 B	R5F10266 Note 2	—	—
	—		R5F10366 Note 2	—	—

Notes 1. This is 640 bytes when the self-programming function or data flash function is used. (For details, see **CHAPTER 3 CPU ARCHITECTURE**.)

2. The self-programming function cannot be used for R5F10266 and R5F10366.

Caution When the flash memory is rewritten via a user program, the code flash area and RAM area are used because each library is used. When using the library, refer to RL78 Family Flash Self Programming Library Type01 User's Manual and RL78 Family Data Flash Library Type04 User's Manual.

1.2 List of Part Numbers

Figure 1-1. Part Number, Memory Size, and Package of RL78/G12

<R>

Part No. R 5 F 1 0 2 A A A x x x S P #V0

- Packaging specifications (#V0):
  - #U5 : Tray (HWQFN)
  - #V0, #V5 : Tray (LSSOP30), Tube (LSSOP20)
  - #W5 : Embossed Tape (HWQFN)
  - #X0, #X5 : Embossed Tape (LSSOP30, LSSOP20)
- Package type (SP):
  - SP : LSSOP, 0.65 mm pitch
  - NA : HWQFN, 0.50 mm pitch
- ROM number (Omitted with blank products) (xxx)
- Classification (A):
  - A : Consumer applications, T_A = -40°C to +85°C
  - D : Industrial applications, T_A = -40°C to +85°C
  - G : Industrial applications, T_A = -40°C to +105°C
- ROM capacity (A):
  - 6 : 2 KB
  - 7 : 4 KB
  - 8 : 8 KB
  - 9 : 12 KB
  - A : 16 KB
- Pin count (A):
  - 6 : 20-pin
  - 7 : 24-pin
  - A : 30-pin
- RL78/G12 group (102):
  - 102 Note 1
  - 103 Notes 1, 2
- Memory type (F):
  - F : Flash memory
- Renesas MCU (5)
- Renesas semiconductor product (R)

Notes 1. For details about the differences between the R5F102 products and the R5F103 products of RL78/G12, see **1.1 Differences between the R5F102 Products and the R5F103 Products**.

2. Products only for "A: Consumer applications (T_A = -40 to +85°C)" and "D: Industrial applications (T_A = -40 to +85°C)"

Table 1-1. List of Ordering Part Numbers

	Pin count	Package	Data flash	Fields of Application	Part Number
<R>	20 pins	20-pin plastic LSSOP (4.4 × 6.5 mm, 0.65 mm pitch)	Mounted	A	R5F1026AASP#V5, R5F10269ASP#V5, R5F10268ASP#V5, R5F10267ASP#V5, R5F10266ASP#V5 R5F1026AASP#X5, R5F10269ASP#X5, R5F10268ASP#X5, R5F10267ASP#X5, R5F10266ASP#X5
				D	R5F1026ADSP#V5, R5F10269DSP#V5, R5F10268DSP#V5, R5F10267DSP#V5, R5F10266DSP#V5 R5F1026ADSP#X5, R5F10269DSP#X5, R5F10268DSP#X5, R5F10267DSP#X5, R5F10266DSP#X5
				G	R5F1026AGSP#V5, R5F10269GSP#V5, R5F10268GSP#V5, R5F10267GSP#V5, R5F10266GSP#V5 R5F1026AGSP#X5, R5F10269GSP#X5, R5F10268GSP#X5, R5F10267GSP#X5, R5F10266GSP#X5
			Not mounted	A	R5F1036AASP#V5, R5F10369ASP#V5, R5F10368ASP#V5, R5F10367ASP#V5, R5F10366ASP#V5 R5F1036AASP#X5, R5F10369ASP#X5, R5F10368ASP#X5, R5F10367ASP#X5, R5F10366ASP#X5
				D	R5F1036ADSP#V5, R5F10369DSP#V5, R5F10368DSP#V5, R5F10367DSP#V5, R5F10366DSP#V5 R5F1036ADSP#X5, R5F10369DSP#X5, R5F10368DSP#X5, R5F10367DSP#X5, R5F10366DSP#X5
<R>	24 pins	24-pin plastic HWQFN (4 × 4 mm, 0.5 mm pitch)	Mounted	A	R5F1027AANA#U5, R5F10279ANA#U5, R5F10278ANA#U5, R5F10277ANA#U5 R5F1027AANA#W5, R5F10279ANA#W5, R5F10278ANA#W5, R5F10277ANA#W5
				D	R5F1027ADNA#U5, R5F10279DNA#U5, R5F10278DNA#U5, R5F10277DNA#U5 R5F1027ADNA#W5, R5F10279DNA#W5, R5F10278DNA#W5, R5F10277DNA#W5
				G	R5F1027AGNA#U5, R5F10279GNA#U5, R5F10278GNA#U5, R5F10277GNA#U5 R5F1027AGNA#W5, R5F10279GNA#W5, R5F10278GNA#W5, R5F10277GNA#W5
			Not mounted	A	R5F1037AANA#V5, R5F10379ANA#V5, R5F10378ANA#V5, R5F10377ANA#V5 R5F1037AANA#X5, R5F10379ANA#X5, R5F10378ANA#X5, R5F10377ANA#X5
				D	R5F1037ADNA#V5, R5F10379DNA#V5, R5F10378DNA#V5, R5F10377DNA#V5 R5F1037ADNA#X5, R5F10379DNA#X5, R5F10378DNA#X5, R5F10377DNA#X5
	30 pins	30-pin plastic LSSOP (7.62 mm (300), 0.65 mm pitch)	Mounted	A	R5F102AAASP#V0, R5F102A9ASP#V0, R5F102A8ASP#V0, R5F102A7ASP#V0 R5F102AAASP#X0, R5F102A9ASP#X0, R5F102A8ASP#X0, R5F102A7ASP#X0
				D	R5F102AADSP#V0, R5F102A9DSP#V0, R5F102A8DSP#V0, R5F102A7DSP#V0 R5F102AADSP#X0, R5F102A9DSP#X0, R5F102A8DSP#X0, R5F102A7DSP#X0
				G	R5F102AAGSP#V0, R5F102A9GSP#V0, R5F102A8GSP#V0, R5F102A7GSP#V0 R5F102AAGSP#X0, R5F102A9GSP#X0, R5F102A8GSP#X0, R5F102A7GSP#X0
			Not mounted	A	R5F103AAASP#V0, R5F103A9ASP#V0, R5F103A8ASP#V0, R5F103A7ASP#V0 R5F103AAASP#X0, R5F103A9ASP#X0, R5F103A8ASP#X0, R5F103A7ASP#X0
				D	R5F103AADSP#V0, R5F103A9DSP#V0, R5F103A8DSP#V0, R5F103A7DSP#V0 R5F103AADSP#X0, R5F103A9DSP#X0, R5F103A8DSP#X0, R5F103A7DSP#X0

Note For fields of application, see **Figure 1-1 Part Number, Memory Size, and Package of RL78/G12**.

Caution The ordering part numbers represent the numbers at the time of publication. For the latest ordering part numbers, refer to the target product page of the Renesas Electronics website.

1.3 Differences between the R5F102 Products and the R5F103 Products

The following are differences between the R5F102 products and the R5F103 products.

- ○ Whether the data flash memory is mounted or not
- ○ High-speed on-chip oscillator oscillation frequency accuracy
- ○ Number of channels in serial interface
- ○ Whether the DMA function is mounted or not
- ○ Whether a part of the safety functions are mounted or not

1.3.1 Data Flash

The data flash memory of 2 KB is mounted on the R5F102 products, but not on the R5F103 products.

Product	Data Flash
R5F102 products R5F1026A, R5F1027A, R5F102AA, R5F10269, R5F10279, R5F102A9, R5F10268, R5F10278, R5F102A8, R5F10267, R5F10277, R5F102A7, R5F10266 Note	2KB
R5F103 products R5F1036A, R5F1037A, R5F103AA, R5F10369, R5F10379, R5F103A9, R5F10368, R5F10378 R5F103A8, R5F10367, R5F10377, R5F103A7, R5F10366	Not mounted

Note The RAM in the R5F10266 has capacity as small as 256 bytes. Depending on the customer's program specification, the stack area to execute the data flash library may not be kept and data may not be written to or erased from the data flash memory.

Caution When the flash memory is rewritten via a user program, the code flash area and RAM area are used because each library is used. When using the library, refer to RL78 Family Flash Self Programming Library Type01 User's Manual and RL78 Family Data Flash Library Type04 User's Manual.

1.3.2 On-chip oscillator characteristics

(1) High-speed on-chip oscillator oscillation frequency of the R5F102 products

Oscillator	Condition	MIN	MAX	Unit
High-speed on-chip oscillator oscillation frequency accuracy	T_A = -20 to +85 °C	-1.0	+1.0	%
	T_A = -40 to -20 °C	-1.5	+1.5	
	T_A = +85 to +105 °C	-2.0	+2.0	

(2) High-speed on-chip oscillator oscillation frequency of the R5F103 products

Oscillator	Condition	MIN	MAX	Unit
High-speed on-chip oscillator oscillation frequency accuracy	T_A = -40 to + 85 °C	-5.0	+5.0	%

1.3.3 Peripheral Functions

The following are differences in peripheral functions between the R5F102 products and the R5F103 products.

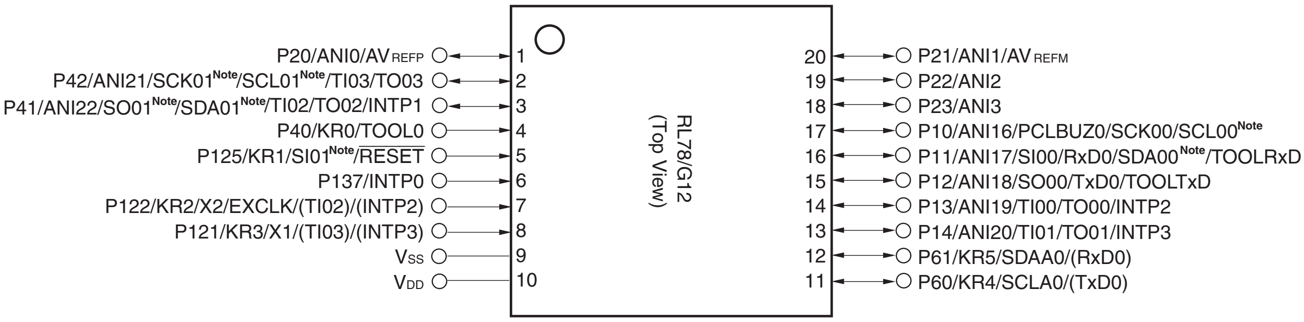
RL78/G12		R5F102 product		R5F103 product	
		20, 24 pin product	30 pin product	20, 24 pin product	30 pin product
Serial interface	UART	1 channel	3 channels	1 channel	
	CSI	2 channels	3 channels	1 channel	
	Simplified I^2C	2 channels	3 channels	None	
DMA function		2 channels		None	
Safety function	CRC operation	Yes		None	
	RAM guard	Yes		None	
	SFR guard	Yes		None	

1.4 Pin Configuration (Top View)

1.4.1 20-pin products

- 20-pin plastic LSSOP (4.4 × 6.5 mm, 0.65 mm pitch)

<R>



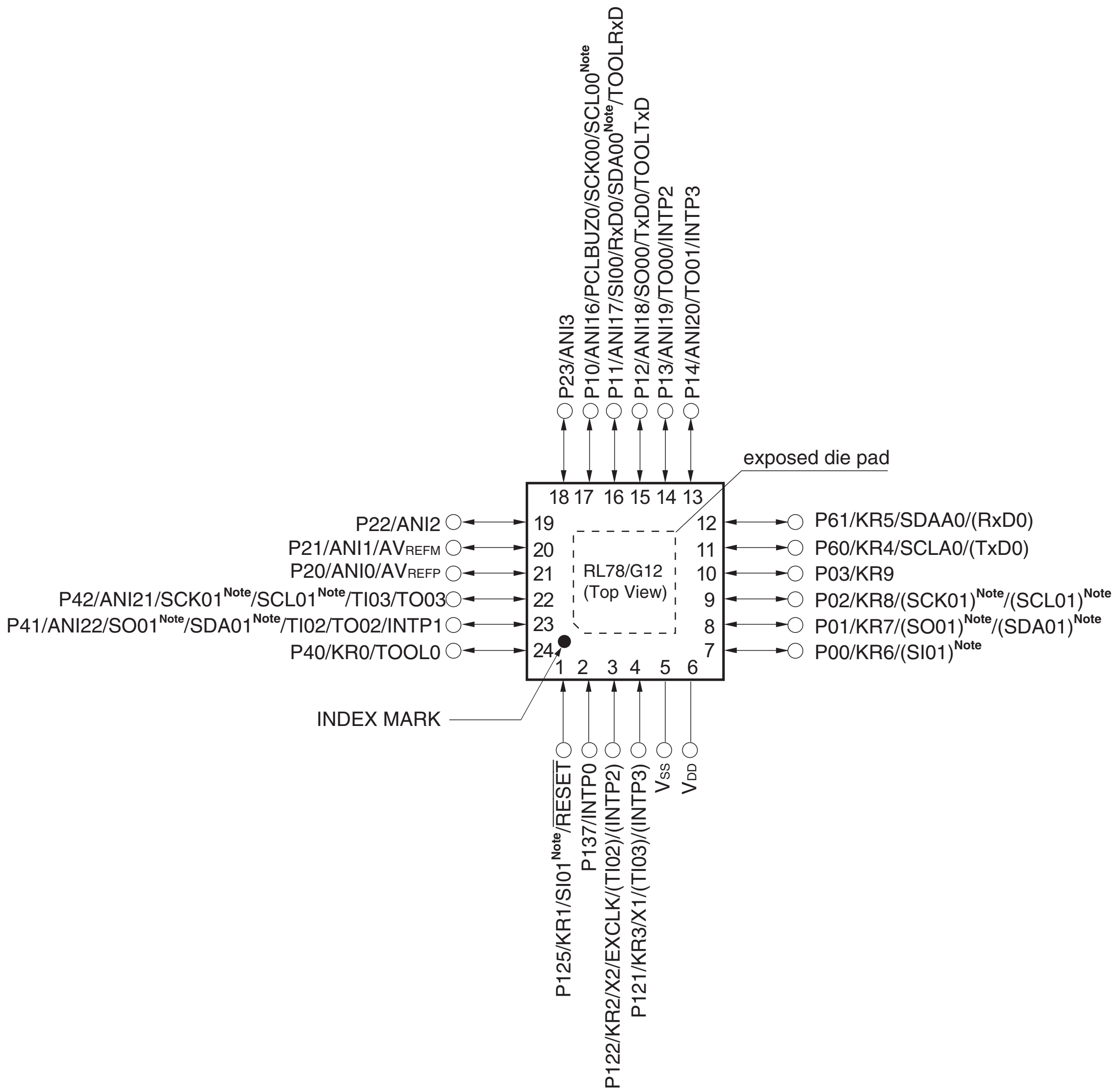
Note Provided only in the R5F102 products.

Remarks 1. For pin identification, see **1.5 Pin Identification**.

2. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). See **Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR)**.

1.4.2 24-pin products

<R> • 24-pin plastic HWQFN (4 × 4 mm, 0.5 mm pitch)



Note Provided only in the R5F102 products.

Remarks 1. For pin identification, see **1.5 Pin Identification**.

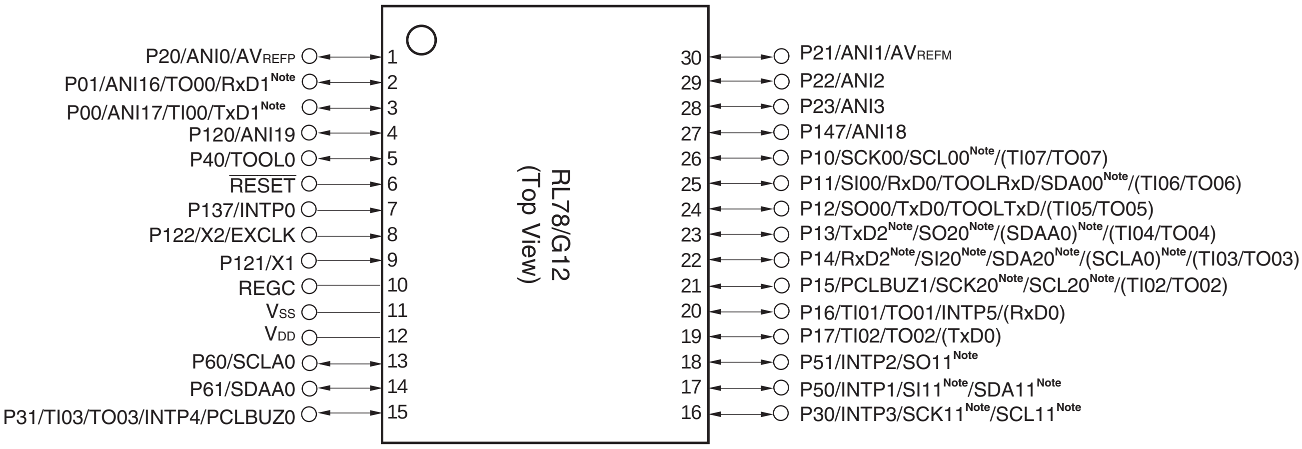
2. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). See **Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR)**.

3. It is recommended to connect an exposed die pad to Vss.

1.4.3 30-pin products

- 30-pin plastic LSSOP (7.62 mm (300), 0.65 mm pitch)

<R>



Note Provided only in the R5F102 products.

Caution Connect the REGC pin to V_{SS} via capacitor (0.47 to 1 μF).

Remarks 1. For pin identification, see **1.5 Pin Identification**.

2. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). See **Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR).**

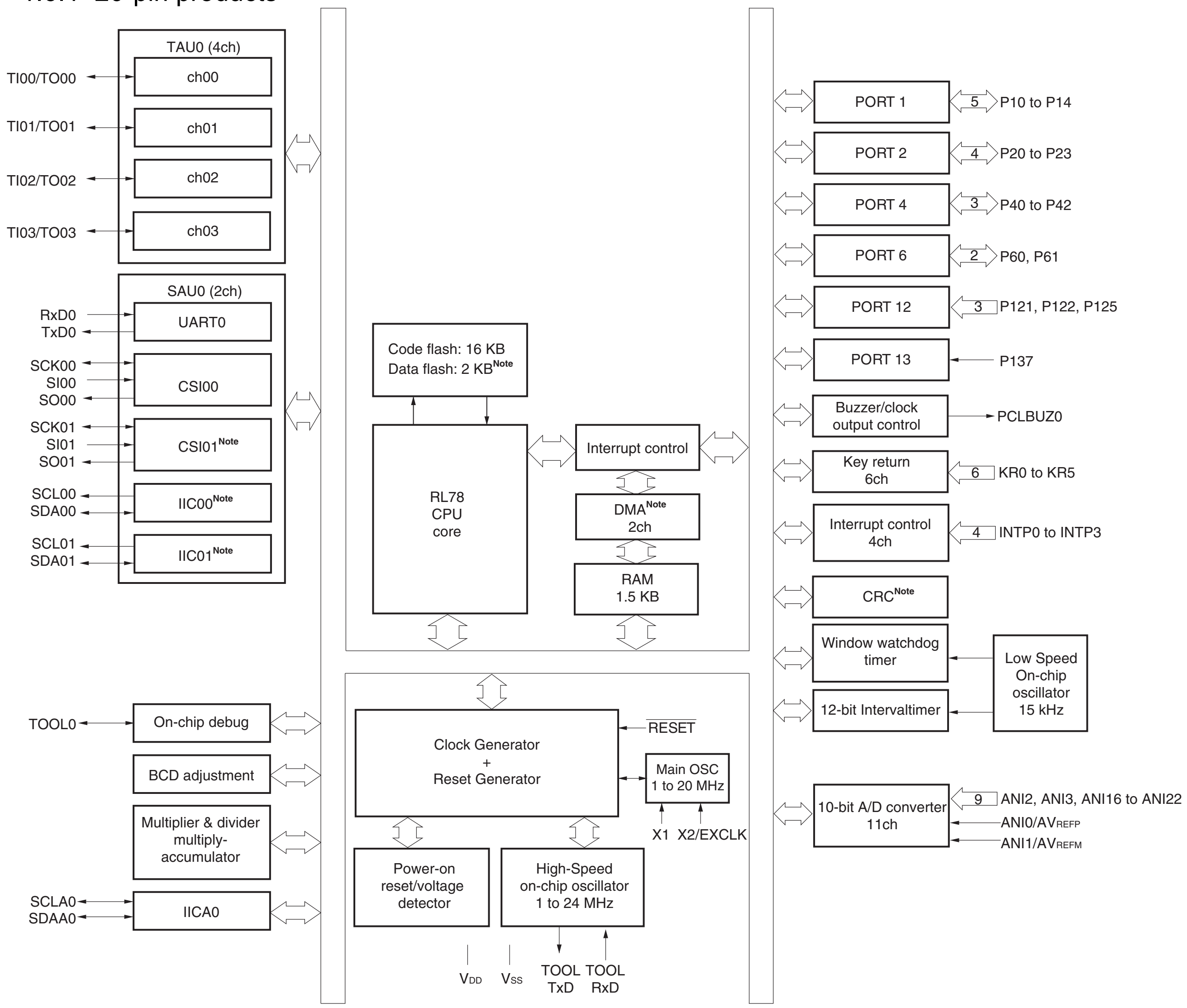
1.5 Pin Identification

ANI0 to ANI3, ANI16 to ANI22:	Analog input
AVREFM:	Analog Reference Voltage Minus
AVREFP:	Analog reference voltage plus
EXCLK:	External Clock Input (Main System Clock)
INTP0 to INTP5	Interrupt Request From Peripheral
KR0 to KR9:	Key Return
P00 to P03:	Port 0
P10 to P17:	Port 1
P20 to P23:	Port 2
P30 to P31:	Port 3
P40 to P42:	Port 4
P50, P51:	Port 5
P60, P61:	Port 6
P120 to P122, P125:	Port 12
P137:	Port 13
P147:	Port 14
PCLBUZ0, PCLBUZ1:	Programmable Clock Output/ Buzzer Output

REGC:	Regulator Capacitance
$\overline{\text{RESET}}$:	Reset
RxD0 to RxD2:	Receive Data
SCK00, SCK01, SCK11, SCK20:	Serial Clock Input/Output
SCL00, SCL01, SCL11, SCL20, SCLA0:	Serial Clock Input/Output
SDA00, SDA01, SDA11, SDA20, SDAA0:	Serial Data Input/Output
SI00, SI01, SI11, SI20:	Serial Data Input
SO00, SO01, SO11, SO20:	Serial Data Output
TI00 to TI07:	Timer Input
TO00 to TO07:	Timer Output
TOOL0:	Data Input/Output for Tool
TOOLRxD, TOOLTxD:	Data Input/Output for External Device
TxD0 to TxD2:	Transmit Data
VDD:	Power supply
VSS:	Ground
X1, X2:	Crystal Oscillator (Main System Clock)

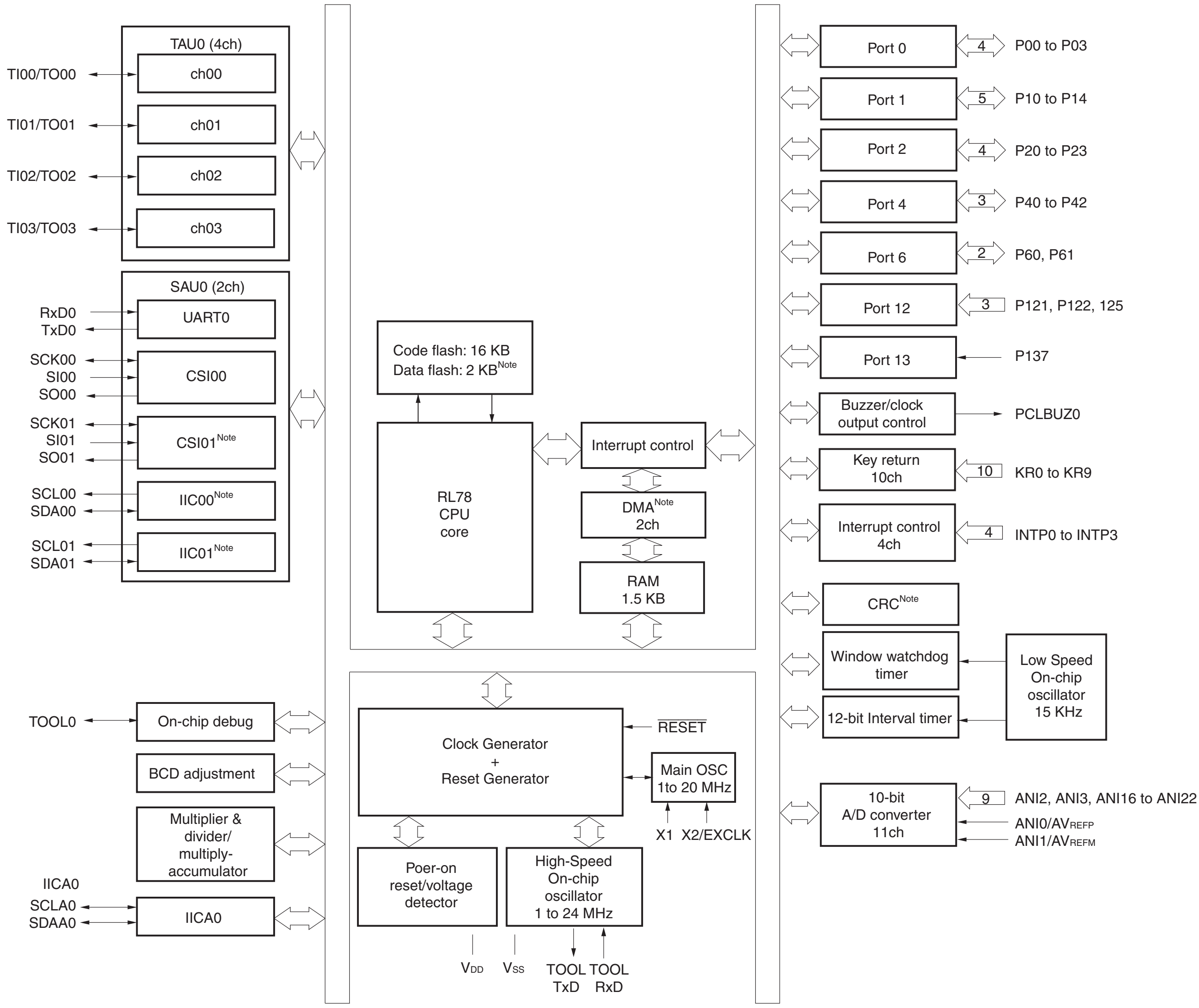
1.6 Block Diagram

1.6.1 20-pin products



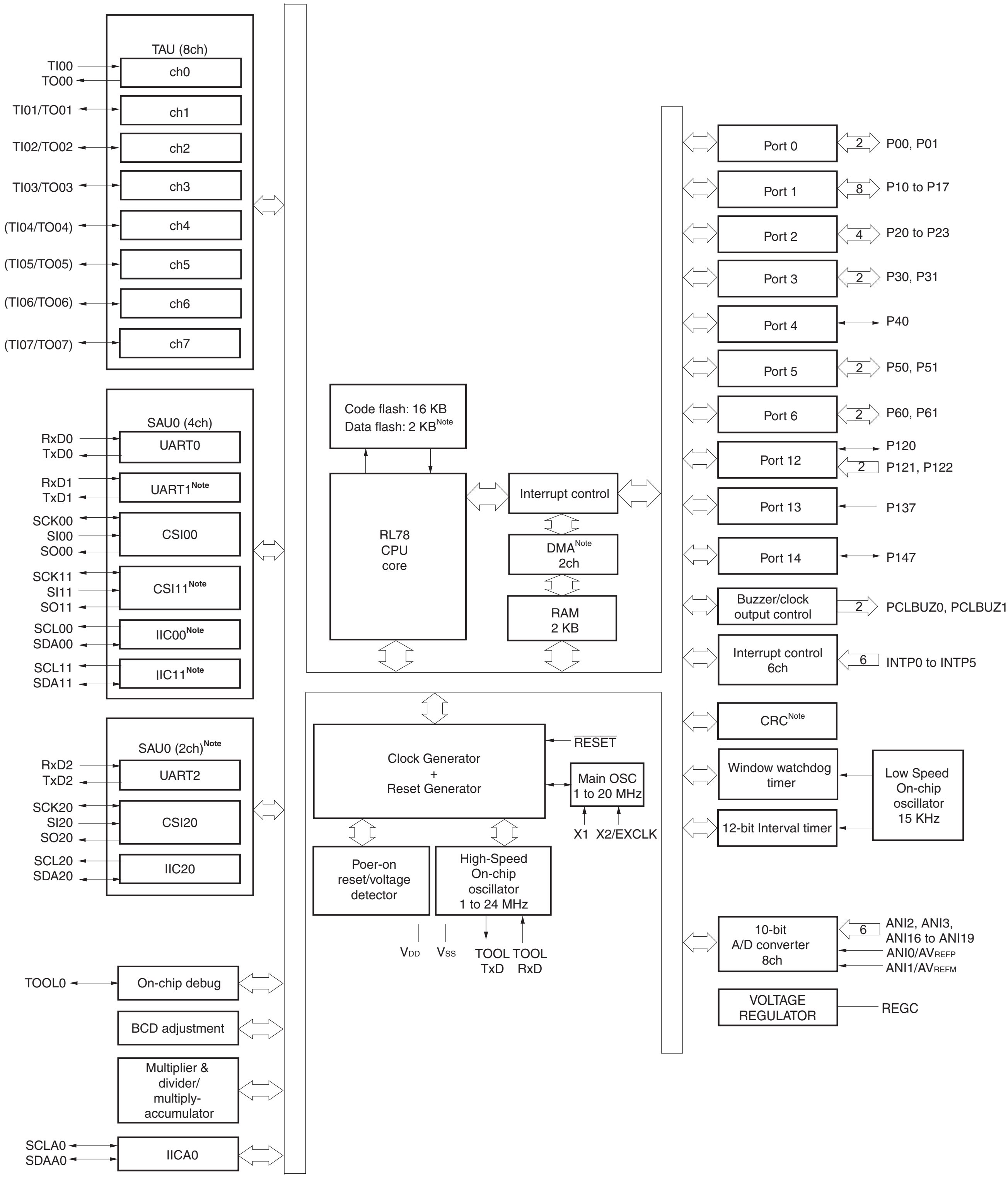
Note Provided only in the R5F102 products.

1.6.2 24-pin products



Note Provided only in the R5F102 products.

1.6.3 30-pin products



Note Provided only in the R5F102 products.

Remark Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). See **Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR)**.

1.7 Outline of Functions

This outline describes the function at the time when Peripheral I/O redirection register (PIOR) is set to 00H.

(1/2)

<table>
<tr><th colspan="2" rowspan="2">Item</th><th colspan="2">20-pin</th><th colspan="2">24-pin</th><th colspan="2">30-pin</th></tr>
<tr><th>R5F1026x</th><th>R5F1036x</th><th>R5F1027x</th><th>R5F1037x</th><th>R5F102Ax</th><th>R5F103Ax</th></tr>
<tr><td colspan="2">Code flash memory</td><td colspan="2">2 to 16 KB [Note 1]</td><td colspan="4">4 to 16 KB</td></tr>
<tr><td colspan="2">Data flash memory</td><td>2 KB</td><td>–</td><td>2 KB</td><td>–</td><td>2 KB</td><td>–</td></tr>
<tr><td colspan="2">RAM</td><td colspan="2">256 B to 1.5 KB</td><td colspan="2">512 B to 1.5 KB</td><td colspan="2">512 B to 2KB</td></tr>
<tr><td colspan="2">Address space</td><td colspan="6">1 MB</td></tr>
<tr><td rowspan="2"><R> Main system clock</td><td>High-speed system clock</td><td colspan="6">X1 (crystal/ceramic) oscillation, external main system clock input (EXCLK)
HS (High-speed main) mode : 1 to 20 MHz (V_{DD} = 2.7 to 5.5 V),
HS (High-speed main) mode : 1 to 16 MHz (V_{DD} = 2.4 to 5.5 V),
LS (Low-speed main) mode : 1 to 8 MHz (V_{DD} = 1.8 to 5.5 V)</td></tr>
<tr><td>High-speed on-chip oscillator clock</td><td colspan="6">HS (High-speed main) mode : 1 to 24 MHz (V_{DD} = 2.7 to 5.5 V),
HS (High-speed main) mode : 1 to 16 MHz (V_{DD} = 2.4 to 5.5 V),
LS (Low-speed main) mode : 1 to 8 MHz (V_{DD} = 1.8 to 5.5 V)</td></tr>
<tr><td colspan="2">Low-speed on-chip oscillator clock</td><td colspan="6">15 kHz (TYP)</td></tr>
<tr><td colspan="2">General-purpose register</td><td colspan="6">(8-bit register × 8) × 4 banks</td></tr>
<tr><td colspan="2" rowspan="2">Minimum instruction execution time</td><td colspan="6">0.04167 μs (High-speed on-chip oscillator clock: f_{IH} = 24 MHz operation)</td></tr>
<tr><td colspan="6">0.05 μs (High-speed system clock: f_{MX} = 20 MHz operation)</td></tr>
<tr><td colspan="2">Instruction set</td><td colspan="6">• Data transfer (8/16 bits)
• Adder and subtractor/logical operation (8/16 bits)
• Multiplication (8 bits × 8 bits)
• Rotate, barrel shift, and bit manipulation (set, reset, test, and Boolean operation), etc.</td></tr>
<tr><td rowspan="4">I/O port</td><td>Total</td><td colspan="2">18</td><td colspan="2">22</td><td colspan="2">26</td></tr>
<tr><td>CMOS I/O</td><td colspan="2">12
(N-ch O.D. I/O
[V_{DD} withstand voltage]: 4)</td><td colspan="2">16
(N-ch O.D. I/O
[V_{DD} withstand voltage]: 5)</td><td colspan="2">21
(N-ch O.D. I/O
[V_{DD} withstand voltage]: 9)</td></tr>
<tr><td>CMOS input</td><td colspan="2">4</td><td colspan="2">4</td><td colspan="2">3</td></tr>
<tr><td>N-ch open-drain I/O
(6 V tolerance)</td><td colspan="6">2</td></tr>
<tr><td rowspan="4">Timer</td><td>16-bit timer</td><td colspan="4">4 channels</td><td colspan="2">8 channels</td></tr>
<tr><td>Watchdog timer</td><td colspan="6">1 channel</td></tr>
<tr><td>12-bit Interval timer</td><td colspan="6">1 channel</td></tr>
<tr><td>Timer output</td><td colspan="4">4 channels
(PWM outputs: 3 [Note 3])</td><td colspan="2">8 channels
(PWM outputs: 7 [Note 3]) [Note 2]</td></tr>
</table>

Notes 1. The self-programming function cannot be used in the R5F10266 and R5F10366.

2. The maximum number of channels when PIOR0 is set to 1.

3. The number of PWM outputs varies depending on the setting of channels in use (the number of masters and slaves). (See **6.9.3 Operation as multiple PWM output function**.)

Caution When the flash memory is rewritten via a user program, the code flash area and RAM area are used because each library is used. When using the library, refer to RL78 Family Flash Self Programming Library Type01 User's Manual and RL78 Family Data Flash Library Type04 User's Manual.

(2/2)

Item		20-pin		24-pin		30-pin	
		R5F1026x	R5F1036x	R5F1027x	R5F1037x	R5F102Ax	R5F103Ax
Clock output/buzzer output		1				2	
		2.44 kHz to 10 MHz: (Peripheral hardware clock: f_{MAIN} = 20 MHz operation)					
8/10-bit resolution A/D converter		11 channels				8 channels	
Serial interface		[R5F1026x (20-pin), R5F1027x (24-pin)] ・ CSI: 2 channels/Simplified I^2C: 2 channels/UART: 1 channel [R5F102Ax (30-pin)] ・ CSI: 1 channel/Simplified I^2C: 1 channel/UART: 1 channel ・ CSI: 1 channel/Simplified I^2C: 1 channel/UART: 1 channel ・ CSI: 1 channel/Simplified I^2C: 1 channel/UART: 1 channel [R5F1036x (20-pin), R5F1037x (24-pin)] ・ CSI: 1 channel/Simplified I^2C: 0 channel/UART: 1 channel [R5F103Ax (30-pin)] ・ CSI: 1 channel/Simplified I^2C: 0 channel/UART: 1 channel					
	I^2C bus	1 channel					
Multiplier and divider/multiply-accumulator		• 16 bits × 16 bits = 32 bits (unsigned or signed) • 32 bits × 32 bits = 32 bits (unsigned) • 16 bits × 16 bits + 32 bits = 32 bits (unsigned or signed)					
DMA controller		2 channels	—	2 channels	—	2 channels	—
Vectored interrupt sources	Internal	18	16	18	16	26	19
	External	5				6	
Key interrupt		6		10		—	
Reset		• Reset by $\overline{\text{RESET}}$ pin • Internal reset by watchdog timer • Internal reset by power-on-reset • Internal reset by voltage detector • Internal reset by illegal instruction execution Note • Internal reset by RAM parity error • Internal reset by illegal-memory access					
Power-on-reset circuit		• Power-on-reset: 1.51 V (TYP) • Power-down-reset: 1.50 V (TYP)					
Voltage detector		• Rising edge : 1.88 to 4.06 V (12 stages) • Falling edge : 1.84 to 3.98 V (12 stages)					
On-chip debug function		Provided					
Power supply voltage		V_{DD} = 1.8 to 5.5 V					
Operating ambient temperature		T_A = –40 to +85°C (A: Consumer applications, D: Industrial applications), T_A = –40 to +105°C (G: Industrial applications)					

Note The illegal instruction is generated when instruction code FFH is executed.
Reset by the illegal instruction execution not issued by emulation with the in-circuit emulator or on-chip debug emulator.

<R>

2. ELECTRICAL SPECIFICATIONS (T_A = –40 to +85°C)

<R> This chapter describes the following electrical specifications.

Target products A: Consumer applications T_A = -40 to +85°C

<R> R5F102xxAxx, R5F103xxAxx

D: Industrial applications T_A = -40 to +85°C

<R> R5F102xxDxx, R5F103xxDxx

G: Industrial applications when T_A = -40 to +105°C products is used in the range of T_A = -40 to +85°C

<R> R5F102xxGxx

Cautions 1. The RL78 microcontrollers have an on-chip debug function, which is provided for development and evaluation. Do not use the on-chip debug function in products designated for mass production, because the guaranteed number of rewritable times of the flash memory may be exceeded when this function is used, and product reliability therefore cannot be guaranteed. Renesas Electronics is not liable for problems occurring when the on-chip debug function is used.

2. The pins mounted depend on the product. Refer to 2.1 Port Functions to 2.2.1 Functions for each product.

2.1 Absolute Maximum Ratings

Absolute Maximum Ratings (T_A = 25°C)

Parameter	Symbols	Conditions		Ratings	Unit
Supply Voltage	V_{DD}			–0.5 to + 6.5	V
REGC terminal input voltage[Note1]	V_{IREGC}	REGC		–0.3 to +2.8 and –0.3 to V_{DD} + 0.3 [Note 2]	V
Input Voltage	V_{I1}	Other than P60, P61		–0.3 to V_{DD} + 0.3[Note 3]	V
	V_{I2}	P60, P61 (N-ch open drain)		–0.3 to 6.5	V
Output Voltage	V_O			–0.3 to V_{DD} + 0.3[Note 3]	V
Analog input voltage	V_{AI}	20-, 24-pin products: ANI0 to ANI3, ANI16 to ANI22 30-pin products: ANI0 to ANI3, ANI16 to ANI19		–0.3 to V_{DD} + 0.3 and –0.3 to AVREF(+)+0.3[Notes 3, 4]	V
Output current, high	I_{OH1}	Per pin	Other than P20 to P23	–40	mA
		Total of all pins	All the terminals other than P20 to P23	–170	mA
			20-, 24-pin products: P40 to P42 30-pin products: P00, P01, P40, P120	–70	mA
			20-, 24-pin products: P00 to P03[Note 5], P10 to P14 30-pin products: P10 to P17, P30, P31, P50, P51, P147	–100	mA
	I_{OH2}	Per pin	P20 to P23	–0.5	mA
		Total of all pins		–2	mA
Output current, low	I_{OL1}	Per pin	Other than P20 to P23	40	mA
		Total of all pins	All the terminals other than P20 to P23	170	mA
			20-, 24-pin products: P40 to P42 30-pin products: P00, P01, P40, P120	70	mA
			20-, 24-pin products: P00 to P03[Note 5], P10 to P14, P60, P61 30-pin products: P10 to P17, P30, P31, P50, P51, P60, P61, P147	100	mA
	I_{OL2}	Per pin	P20 to P23	1	mA
		Total of all pins		5	mA
Operating ambient temperature	T_A			–40 to +85	°C
Storage temperature	T_{stg}			–65 to +150	°C

Notes 1. 30-pin product only.

2. Connect the REGC pin to V_{SS} via a capacitor (0.47 to 1 μF). This value determines the absolute maximum rating of the REGC pin. Do not use it with voltage applied.

3. Must be 6.5 V or lower.

4. Do not exceed $AV_{REF}(+)$ + 0.3 V in case of A/D conversion target pin.

5. 24-pin products only.

Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.

Remarks 1. Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

2. $AV_{REF}(+)$: + side reference voltage of the A/D converter.

3. V_{SS} : Reference voltage

2.2 Oscillator Characteristics

2.2.1 X1 oscillator characteristics

(T_A = –40 to +85°C, 1.8 V ≤ V_{DD} ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Resonator	Conditions	MIN.	TYP.	MAX.	Unit
X1 clock oscillation frequency (f_X)[Note]	Ceramic resonator / crystal oscillator	2.7 V ≤ V_{DD} ≤ 5.5 V	1.0		20.0	MHz
		1.8 V ≤ V_{DD} < 2.7 V	1.0		8.0	

Note Indicates only permissible oscillator frequency ranges. Refer to AC Characteristics for instruction execution time. Request evaluation by the manufacturer of the oscillator circuit mounted on a board to check the oscillator characteristics.

Caution Since the CPU is started by the high-speed on-chip oscillator clock after a reset release, check the X1 clock oscillation stabilization time using the oscillation stabilization time counter status register (OSTC) by the user. Determine the oscillation stabilization time of the OSTC register and the oscillation stabilization time select register (OSTS) after sufficiently evaluating the oscillation stabilization time with the resonator to be used.

Remark When using the X1 oscillator, refer to **5.4 System Clock Oscillator**.

2.2.2 On-chip oscillator characteristics

(T_A = –40 to +85°C, 1.8 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Oscillators	Parameters	Conditions		MIN.	TYP.	MAX.	Unit
High-speed on-chip oscillator clock frequency [Notes 1, 2]	f_{IH}			1		24	MHz
High-speed on-chip oscillator clock frequency accuracy		R5F102 products	T_A = –20 to +85°C	-1.0		+1.0	%
			T_A = –40 to –20°C	-1.5		+1.5	%
		R5F103 products		-5.0		+5.0	%
Low-speed on-chip oscillator clock frequency	f_{IL}				15		kHz
Low-speed on-chip oscillator clock frequency accuracy				-15		+15	%

Notes 1. High-speed on-chip oscillator frequency is selected by bits 0 to 3 of option byte (000C2H) and bits 0 to 2 of HOCODIV register.

2. This only indicates the oscillator characteristics. Refer to AC Characteristics for instruction execution time.

2.3 DC Characteristics

2.3.1 Pin characteristics

(T_A = −40 to +85°C, 1.8 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V) **(1/4)**

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current, high[Note 1]	I_{OH1}	20-, 24-pin products: Per pin for P00 to P03[Note 4], P10 to P14, P40 to P42 30-pin products: Per pin for P00, P01, P10 to P17, P30, P31, P40, P50, P51, P120, P147				−10.0 Note 2	mA
		20-, 24-pin products: Total of P40 to P42 30-pin products: Total of P00, P01, P40, P120 (When duty ≤ 70%[Note 3])	4.0 V ≤ V_{DD} ≤ 5.5 V			−30.0	mA
			2.7 V ≤ V_{DD} < 4.0 V			−6.0	mA
			1.8 V ≤ V_{DD} < 2.7 V			−4.5	mA
		20-, 24-pin products: Total of P00 to P03[Note 4], P10 to P14 30-pin products: Total of P10 to P17, P30, P31, P50, P51, P147 (When duty ≤ 70%[Note 3])	4.0 V ≤ V_{DD} ≤ 5.5 V			−80.0	mA
			2.7 V ≤ V_{DD} < 4.0 V			−18.0	mA
			1.8 V ≤ V_{DD} < 2.7 V			−10.0	mA
		Total of all pins (When duty ≤ 70%[Note 3])				−100	mA
	I_{OH2}	Per pin for P20 to P23				−0.1	mA
		Total of all pins				−0.4	mA

Notes 1. value of current at which the device operation is guaranteed even if the current flows from the V_{DD} pin to an output pin.

2. However, do not exceed the total current value.

3. The output current value under conditions where the duty factor ≤ 70%.

If duty factor > 70%: The output current value can be calculated with the following expression (where n represents the duty factor as a percentage).

- Total output current of pins = (I_{OH} × 0.7)/(n × 0.01)

  <Example> Where n = 80% and I_{OH} = −10.0 mA

  Total output current of pins = (−10.0 × 0.7)/(80 × 0.01) ≅ −8.7 mA

However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.

4. 24-pin products only.

Caution P10 to P12 and P41 for 20-pin products, P01, P10 to P12, and P41 for 24-pin products, and P00, P10 to P15, P17, and P50 for 30-pin products do not output high level in N-ch open-drain mode.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

(T_A = –40 to +85°C, 1.8 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V) **(2/4)**

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current, low[Note 1]	I_{OL1}	20-, 24-pin products: Per pin for P00 to P03[Note 4], P10 to P14, P40 to P42 30-pin products: Per pin for P00, P01, P10 to P17, P30, P31, P40, P50, P51, P120, P147				20.0 Note 2	mA
		Per pin for P60, P61				15.0 Note 2	mA
		20-, 24-pin products: Total of P40 to P42 30-pin products: Total of P00, P01, P40, P120 (When duty ≤ 70%[Note 3])	4.0 V ≤ V_{DD} ≤ 5.5 V			60.0	mA
			2.7 V ≤ V_{DD} < 4.0 V			9.0	mA
			1.8 V ≤ V_{DD} < 2.7 V			1.8	mA
		20-, 24-pin products: Total of P00 to P03[Note 4], P10 to P14, P60, P61 30-pin products: Total of P10 to P17, P30, P31, P50, P51, P60, P61, P147 (When duty ≤ 70%[Note 3])	4.0 V ≤ V_{DD} ≤ 5.5 V			80.0	mA
			2.7 V ≤ V_{DD} < 4.0 V			27.0	mA
			1.8 V ≤ V_{DD} < 2.7 V			5.4	mA
		Total of all pins (When duty ≤ 70%[Note 3])				140	mA
	I_{OL2}	Per pin for P20 to P23				0.4	mA
		Total of all pins				1.6	mA

Notes 1. Value of current at which the device operation is guaranteed even if the current flows from an output pin to the V_{SS} pin.

2. However, do not exceed the total current value.

3. The output current value under conditions where the duty factor ≤ 70%.

If duty factor > 70%: The output current value can be calculated with the following expression (where n represents the duty factor as a percentage).

- Total output current of pins = (I_{OL} × 0.7)/(n × 0.01)

<Example> Where n = 80% and I_{OL} = 10.0 mA

Total output current of pins = (10.0 × 0.7)/(80 × 0.01) ≅ 8.7 mA

However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.

4. 24-pin products only.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

(T_A = –40 to +85°C, 1.8 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V) **(3/4)**

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Input voltage, high	V_{IH1}	Normal input buffer 20-, 24-pin products: P00 to P03[Note 2], P10 to P14, P40 to P42 30-pin products: P00, P01, P10 to P17, P30, P31, P40, P50, P51, P120, P147		0.8V_{DD}		V_{DD}	V
	V_{IH2}	TTL input buffer 20-, 24-pin products: P10, P11 30-pin products: P01, P10, P11, P13 to P17	4.0 V ≤ V_{DD} ≤ 5.5 V	2.2		V_{DD}	V
			3.3 V ≤ V_{DD} < 4.0 V	2.0		V_{DD}	V
			1.8 V ≤ V_{DD} < 3.3 V	1.5		V_{DD}	V
	V_{IH3}	P20 to P23		0.7V_{DD}		V_{DD}	V
	V_{IH4}	P60, P61		0.7V_{DD}		6.0	V
	V_{IH5}	P121, P122, P125[Note 1], P137, EXCLK, $\overline{\text{RESET}}$		0.8V_{DD}		V_{DD}	V
Input voltage, low	V_{IL1}	Normal input buffer 20-, 24-pin products: P00 to P03[Note 2], P10 to P14, P40 to P42 30-pin products: P00, P01, P10 to P17, P30, P31, P40, P50, P51, P120, P147		0		0.2V_{DD}	V
	V_{IL2}	TTL input buffer 20-, 24-pin products: P10, P11 30-pin products: P01, P10, P11, P13 to P17	4.0 V ≤ V_{DD} ≤ 5.5 V	0		0.8	V
			3.3 V ≤ V_{DD} < 4.0 V	0		0.5	V
			1.8 V ≤ V_{DD} < 3.3 V	0		0.32	V
	V_{IL3}	P20 to P23		0		0.3V_{DD}	V
	V_{IL4}	P60, P61		0		0.3V_{DD}	V
	V_{IL5}	P121, P122, P125[Note 1], P137, EXCLK, $\overline{\text{RESET}}$		0		0.2V_{DD}	V
Output voltage, high	V_{OH1}	20-, 24-pin products: P00 to P03[Note 2], P10 to P14, P40 to P42 30-pin products: P00, P01, P10 to P17, P30, P31, P40, P50, P51, P120, P147	4.0 V ≤ V_{DD} ≤ 5.5 V, I_{OH1} = –10.0 mA	V_{DD}–1.5			V
			4.0 V ≤ V_{DD} ≤ 5.5 V, I_{OH1} = –3.0 mA	V_{DD}–0.7			V
			2.7 V ≤ V_{DD} ≤ 5.5 V, I_{OH1} = –2.0 mA	V_{DD}–0.6			V
			1.8 V ≤ V_{DD} ≤ 5.5 V, I_{OH1} = –1.5 mA	V_{DD}–0.5			V
	V_{OH2}	P20 to P23	I_{OH2} = –100 μA	V_{DD}–0.5			V

Notes 1. 20, 24-pin products only.

2. 24-pin products only.

Caution The maximum value of V_{IH} of pins P10 to P12 and P41 for 20-pin products, P01, P10 to P12, and P41 for 24-pin products, and P00, P10 to P15, P17, and P50 for 30-pin products is V_{DD} even in N-ch open-drain mode. High level is not output in the N-ch open-drain mode.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

(T_A = –40 to +85°C, 1.8 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V) **(4/4)**

Parameter	Symbol	Conditions			MIN.	TYP.	MAX.	Unit
Output voltage, low	V_{OL1}	20-, 24-pin products: P00 to P03[Note], P10 to P14, P40 to P42 30-pin products: P00, P01, P10 to P17, P30, P31, P40, P50, P51, P120, P147		4.0 V ≤ V_{DD} ≤ 5.5 V, I_{OL1} = 20.0 mA			1.3	V
				4.0 V ≤ V_{DD} ≤ 5.5 V, I_{OL1} = 8.5 mA			0.7	V
				2.7 V ≤ V_{DD} ≤ 5.5 V, I_{OL1} = 3.0 mA			0.6	V
				2.7 V ≤ V_{DD} ≤ 5.5 V, I_{OL1} = 1.5 mA			0.4	V
				1.8 V ≤ V_{DD} ≤ 5.5 V, I_{OL1} = 0.6 mA			0.4	V
	V_{OL2}	P20 to P23		I_{OL2} = 400 μA			0.4	V
	V_{OL3}	P60, P61		4.0 V ≤ V_{DD} ≤ 5.5 V, I_{OL1} = 15.0 mA			2.0	V
				4.0 V ≤ V_{DD} ≤ 5.5 V, I_{OL1} = 5.0 mA			0.4	V
				2.7 V ≤ V_{DD} ≤ 5.5 V, I_{OL1} = 3.0 mA			0.4	V
				1.8 V ≤ V_{DD} ≤ 5.5 V, I_{OL1} = 2.0 mA			0.4	V
Input leakage current, high	I_{LIH1}	Other than P121, P122	V_I = V_{DD}				1	μA
	I_{LIH2}	P121, P122 (X1, X2/EXCLK)	V_I = V_{DD}	Input port or external clock input			1	μA
				When resonator connected			10	μA
Input leakage current, low	I_{LIL1}	Other than P121, P122	V_I = V_{SS}				–1	μA
	I_{LIL2}	P121, P122 (X1, X2/EXCLK)	V_I = V_{SS}	Input port or external clock input			–1	μA
				When resonator connected			–10	μA
On-chip pull-up resistance	R_U	20-, 24-pin products: P00 to P03[Note], P10 to P14, P40 to P42, P125, $\overline{RESET}$ 30-pin products: P00, P01, P10 to P17, P30, P31, P40, P50, P51, P120, P147		V_I = V_{SS}, input port	10	20	100	kΩ

Note 24-pin products only.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

2.3.2 Supply current characteristics

(1) 20-, 24-pin products

(T_A = –40 to +85°C, 1.8 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V) **(1/2)**

Parameter	Symbol	Conditions					MIN.	TYP.	MAX.	Unit
Supply current[Note 1]	I_{DD1}	Operating mode	HS(High-speed main) mode[Note 4]	f_{IH} = 24 MHz[Note 3]	Basic operation	V_{DD} = 5.0 V		1.5		mA
						V_{DD} = 3.0 V		1.5		
					Normal operation	V_{DD} = 5.0 V		3.3	5.0	mA
						V_{DD} = 3.0 V		3.3	5.0	
				f_{IH} = 16 MHz[Note 3]		V_{DD} = 5.0 V		2.5	3.7	mA
						V_{DD} = 3.0 V		2.5	3.7	
			LS(Low-speed main) mode[Note 4]	f_{IH} = 8 MHz[Note 3]		V_{DD} = 3.0 V		1.2	1.8	mA
						V_{DD} = 2.0 V		1.2	1.8	
			HS(High-speed main) mode[Note 4]	f_{MX} = 20 MHz[Note 2], V_{DD} = 5.0 V		Square wave input		2.8	4.4	mA
						Resonator connection		3.0	4.6	
				f_{MX} = 20 MHz[Note 2], V_{DD} = 3.0 V		Square wave input		2.8	4.4	mA
						Resonator connection		3.0	4.6	
				f_{MX} = 10 MHz[Note 2], V_{DD} = 5.0 V		Square wave input		1.8	2.6	mA
						Resonator connection		1.8	2.6	
				f_{MX} = 10 MHz[Note 2], V_{DD} = 3.0 V		Square wave input		1.8	2.6	mA
						Resonator connection		1.8	2.6	
			LS(Low-speed main) mode[Note 4]	f_{MX} = 8 MHz[Note 2], V_{DD} = 3.0 V		Square wave input		1.1	1.7	mA
						Resonator connection		1.1	1.7	
				f_{MX} = 8 MHz[Note 2], V_{DD} = 2.0 V		Square wave input		1.1	1.7	mA
						Resonator connection		1.1	1.7	

Notes 1. Total current flowing into V_{DD}, including the input leakage current flowing when the level of the input pin is fixed to V_{DD} or V_{SS}. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.

2. When high-speed on-chip oscillator clock is stopped.

3. When high-speed system clock is stopped

4. Relationship between operation voltage width, operation frequency of CPU and operation mode is as follows.

HS(High speed main) mode: V_{DD} = 2.7 V to 5.5 V @1 MHz to 24 MHz
V_{DD} = 2.4 V to 5.5 V @1 MHz to 16 MHz
LS(Low speed main) mode: V_{DD} = 1.8 V to 5.5 V @1 MHz to 8 MHz

Remarks 1. f_{MX}: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)

2. f_{IH}: high-speed on-chip oscillator clock frequency

3. Temperature condition of the TYP. value is T_A = 25°C.

(1) 20-, 24-pin products

(T_A = –40 to +85°C, 1.8 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V) **(2/2)**

Parameter	Symbol	Conditions				MIN.	TYP.	MAX.	Unit
Supply current Note 1	I_{DD2} Note 2	HALT mode	HS (High-speed main) mode Note 6	f_{IH} = 24 MHz Note 4	V_{DD} = 5.0 V		440	1210	μA
					V_{DD} = 3.0 V		440	1210	
				f_{IH} = 16 MHz Note 4	V_{DD} = 5.0 V		400	950	μA
					V_{DD} = 3.0 V		400	950	
			LS (Low-speed main) mode Note 6	f_{IH} = 8 MHz Note 4	V_{DD} = 3.0 V		270	542	μA
					V_{DD} = 2.0 V		270	542	
			HS (High-speed main) mode Note 6	f_{MX} = 20 MHz Note 3, V_{DD} = 5.0 V	Square wave input		280	1000	μA
					Resonator connection		450	1170	
				f_{MX} = 20 MHz Note 3, V_{DD} = 3.0 V	Square wave input		280	1000	μA
					Resonator connection		450	1170	
				f_{MX} = 10 MHz Note 3, V_{DD} = 5.0 V	Square wave input		190	590	μA
					Resonator connection		260	660	
				f_{MX} = 10 MHz Note 3, V_{DD} = 3.0 V	Square wave input		190	590	μA
					Resonator connection		260	660	
			LS (Low-speed main) mode Note 6	f_{MX} = 8 MHz Note 3, V_{DD} = 3.0 V	Square wave input		110	360	μA
					Resonator connection		150	416	
				f_{MX} = 8 MHz Note 3, V_{DD} = 2.0 V	Square wave input		110	360	μA
					Resonator connection		150	416	
	I_{DD3} Note 5	STOP mode	T_A = –40°C				0.19	0.50	μA
			T_A = +25°C				0.24	0.50	
			T_A = +50°C				0.32	0.80	
			T_A = +70°C				0.48	1.20	
			T_A = +85°C				0.74	2.20	

Notes 1. Total current flowing into V_{DD}, including the input leakage current flowing when the level of the input pin is fixed to V_{DD} or V_{SS}. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.

2. During HALT instruction execution by flash memory.

3. When high-speed on-chip oscillator clock is stopped.

4. When high-speed system clock is stopped.

5. Not including the current flowing into the 12-bit interval timer and watchdog timer.

6. Relationship between operation voltage width, operation frequency of CPU and operation mode is as follows.

HS(High speed main) mode: V_{DD} = 2.7 V to 5.5 V @1 MHz to 24 MHz

V_{DD} = 2.4 V to 5.5 V @1 MHz to 16 MHz

LS(Low speed main) mode: V_{DD} = 1.8 V to 5.5 V @1 MHz to 8 MHz

Remarks 1. f_{MX}: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)

2. f_{IH}: high-speed on-chip oscillator clock frequency

3. Except temperature condition of the TYP. value is T_A = 25°C, other than STOP mode

(2) 30-pin products

(T_A = –40 to +85°C, 1.8 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V) **(1/2)**

Parameter	Symbol	Conditions					MIN.	TYP.	MAX.	Unit
Supply current [Note 1]	I_{DD1}	Operating mode	HS (High-speed main) mode [Note 4]	f_{IH} = 24 MHz [Note 3]	Basic operation	V_{DD} = 5.0 V		1.5		mA
						V_{DD} = 3.0 V		1.5		
					Normal operation	V_{DD} = 5.0 V		3.7	5.5	mA
						V_{DD} = 3.0 V		3.7	5.5	
				f_{IH} = 16 MHz [Note 3]		V_{DD} = 5.0 V		2.7	4.0	mA
						V_{DD} = 3.0 V		2.7	4.0	
			LS (Low-speed main) mode [Note 4]	f_{IH} = 8 MHz [Note 3]		V_{DD} = 3.0 V		1.2	1.8	mA
						V_{DD} = 2.0 V		1.2	1.8	
			HS (High-speed main) mode [Note 4]	f_{MX} = 20 MHz [Note 2], V_{DD} = 5.0 V		Square wave input		3.0	4.6	mA
						Resonator connection		3.2	4.8	
				f_{MX} = 20 MHz [Note 2], V_{DD} = 3.0 V		Square wave input		3.0	4.6	mA
						Resonator connection		3.2	4.8	
				f_{MX} = 10 MHz [Note 2], V_{DD} = 5.0 V		Square wave input		1.9	2.7	mA
						Resonator connection		1.9	2.7	
				f_{MX} = 10 MHz [Note 2], V_{DD} = 3.0 V		Square wave input		1.9	2.7	mA
						Resonator connection		1.9	2.7	
			LS (Low-speed main) mode [Note 4]	f_{MX} = 8 MHz [Note 2], V_{DD} = 3.0 V		Square wave input		1.1	1.7	mA
						Resonator connection		1.1	1.7	
				f_{MX} = 8 MHz [Note 2], V_{DD} = 2.0 V		Square wave input		1.1	1.7	mA
						Resonator connection		1.1	1.7	

Notes 1. Total current flowing into V_{DD}, including the input leakage current flowing when the level of the input pin is fixed to V_{DD} or V_{SS}. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.

2. When high-speed on-chip oscillator clock is stopped.

3. When high-speed system clock is stopped

4. Relationship between operation voltage width, operation frequency of CPU and operation mode is as follows.

HS(High speed main) mode: V_{DD} = 2.7 V to 5.5 V @1 MHz to 24 MHz
V_{DD} = 2.4 V to 5.5 V @1 MHz to 16 MHz
LS(Low speed main) mode: V_{DD} = 1.8 V to 5.5 V @1 MHz to 8 MHz

Remarks 1. f_{MX}: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)

2. f_{IH}: high-speed on-chip oscillator clock frequency

3. Temperature condition of the TYP. value is T_A = 25°C.

(2) 30-pin products

(T_A = –40 to +85°C, 1.8 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V) **(2/2)**

Parameter	Symbol	Conditions				MIN.	TYP.	MAX.	Unit
Supply current Note 1	I_{DD2} Note 2	HALT mode	HS (High-speed main) mode Note 6	f_{IH} = 24 MHz Note 4	V_{DD} = 5.0 V		440	1280	μA
					V_{DD} = 3.0 V		440	1280	
				f_{IH} = 16 MHz Note 4	V_{DD} = 5.0 V		400	1000	μA
					V_{DD} = 3.0 V		400	1000	
			LS (Low-speed main) mode Note 6	f_{IH} = 8 MHz Note 4	V_{DD} = 3.0 V		260	530	μA
					V_{DD} = 2.0 V		260	530	
			HS (High-speed main) mode Note 6	f_{MX} = 20 MHz Note 3, V_{DD} = 5.0 V	Square wave input		280	1000	μA
					Resonator connection		450	1170	
				f_{MX} = 20 MHz Note 3, V_{DD} = 3.0 V	Square wave input		280	1000	μA
					Resonator connection		450	1170	
				f_{MX} = 10 MHz Note 3, V_{DD} = 5.0 V	Square wave input		190	600	μA
					Resonator connection		260	670	
				f_{MX} = 10 MHz Note 3, V_{DD} = 3.0 V	Square wave input		190	600	μA
					Resonator connection		260	670	
			LS (Low-speed main) mode Note 6	f_{MX} = 8 MHz Note 3, V_{DD} = 3.0 V	Square wave input		95	330	μA
					Resonator connection		145	380	
				f_{MX} = 8 MHz Note 3 V_{DD} = 2.0 V	Square wave input		95	330	μA
					Resonator connection		145	380	
	I_{DD3} Note 5	STOP mode	T_A = –40°C				0.18	0.50	μA
			T_A = +25°C				0.23	0.50	
			T_A = +50°C				0.30	1.10	
			T_A = +70°C				0.46	1.90	
			T_A = +85°C				0.75	3.30	

Notes 1. Total current flowing into V_{DD}, including the input leakage current flowing when the level of the input pin is fixed to V_{DD} or V_{SS}. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.

2. During HALT instruction execution by flash memory.

3. When high-speed on-chip oscillator clock is stopped.

4. When high-speed system clock is stopped.

5. Not including the current flowing into the 12-bit interval timer and watchdog timer.

6. Relationship between operation voltage width, operation frequency of CPU and operation mode is as follows.

HS (High speed main) mode: V_{DD} = 2.7 V to 5.5 V @1 MHz to 24 MHz
V_{DD} = 2.4 V to 5.5 V @1 MHz to 16 MHz
LS (Low speed main) mode: V_{DD} = 1.8 V to 5.5 V @1 MHz to 8 MHz

Remarks 1. f_{MX}: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)

2. f_{IH}: high-speed on-chip oscillator clock frequency

3. Except STOP mode, temperature condition of the TYP. value is T_A = 25°C.

(3) Peripheral functions (Common to all products)

(T_A = –40 to +85°C, 1.8 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Low-speed onchip oscillator operating current	I_{FIL} Note 1				0.20		μA
12-bit interval timer operating current	I_{TMKA} Notes 1, 2, 3				0.02		μA
Watchdog timer operating current	I_{WDT} Notes 1, 2, 4	f_{IL} = 15 kHz			0.22		μA
A/D converter operating current	I_{ADC} Notes 1, 5	When conversion at maximum speed	Normal mode, AV_{REFP} = V_{DD} = 5.0 V		1.30	1.70	mA
			Low voltage mode, AV_{REFP} = V_{DD} = 3.0 V		0.50	0.70	mA
A/D converter reference voltage operating current	I_{ADREF} Note 1				75.0		μA
Temperature sensor operating current	I_{TMPS} Note 1				75.0		μA
LVD operating current	I_{LVD} Notes 1, 6				0.08		μA
Self-programming operating current	I_{FSP} Notes 1, 8				2.00	12.20	mA
BGO operating current	I_{BGO} Notes 1, 7				2.00	12.20	mA
SNOOZE operating current	I_{SNOZ} Note 1	ADC operation	The mode is performed Note 9		0.50	0.60	mA
			The A/D conversion operations are performed, Low voltage mode, AV_{REFP} = V_{DD} = 3.0 V		1.20	1.44	mA
		CSI/UART operation			0.70	0.84	mA

Notes 1. Current flowing to the V_{DD}.

2. When high speed on-chip oscillator and high-speed system clock are stopped.

3. Current flowing only to the 12-bit interval timer (excluding the operating current of the low-speed on-chip oscillator). The current value of the RL78 microcontrollers is the sum of I_{DD1}, I_{DD2} or I_{DD3}, and I_{FIL} and I_{TMKA} when the 12-bit interval timer operates.

4. Current flowing only to the watchdog timer (including the operating current of the low-speed on-chip oscillator). The current value of the RL78 microcontrollers is the sum of I_{DD1}, I_{DD2} or I_{DD3} and I_{WDT} when the watchdog timer operates.

5. Current flowing only to the A/D converter. The current value of the RL78 microcontrollers is the sum of I_{DD1} or I_{DD2} and I_{ADC} when the A/D converter operates in an operation mode or the HALT mode.

6. Current flowing only to the LVD circuit. The current value of the RL78 microcontrollers is the sum of I_{DD1}, I_{DD2} or I_{DD3} and I_{LVD} when the LVD circuit operates.

7. Current flowing only during data flash rewrite.

8. Current flowing only during self programming.

9. For shift time to the SNOOZE mode, see **17.3.3 SNOOZE mode**.

Remarks 1. f_{IL}: Low-speed on-chip oscillator clock frequency

2. Temperature condition of the TYP. value is T_A = 25°C

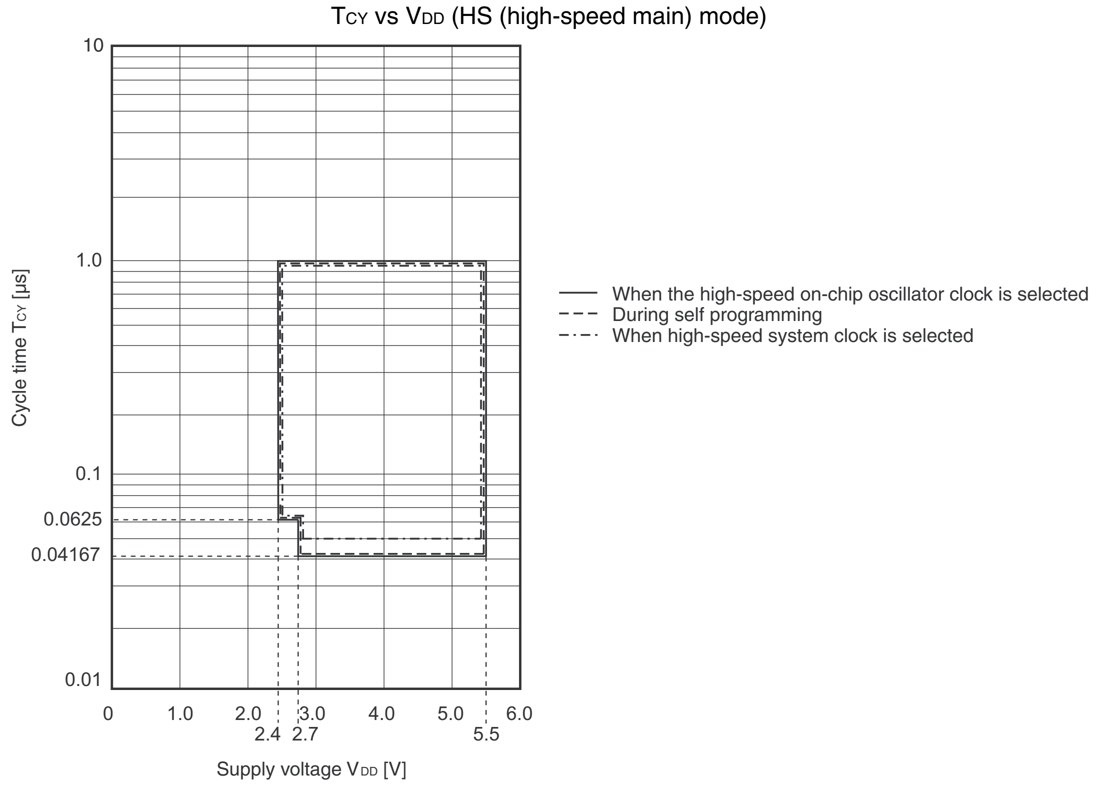
2.4 AC Characteristics

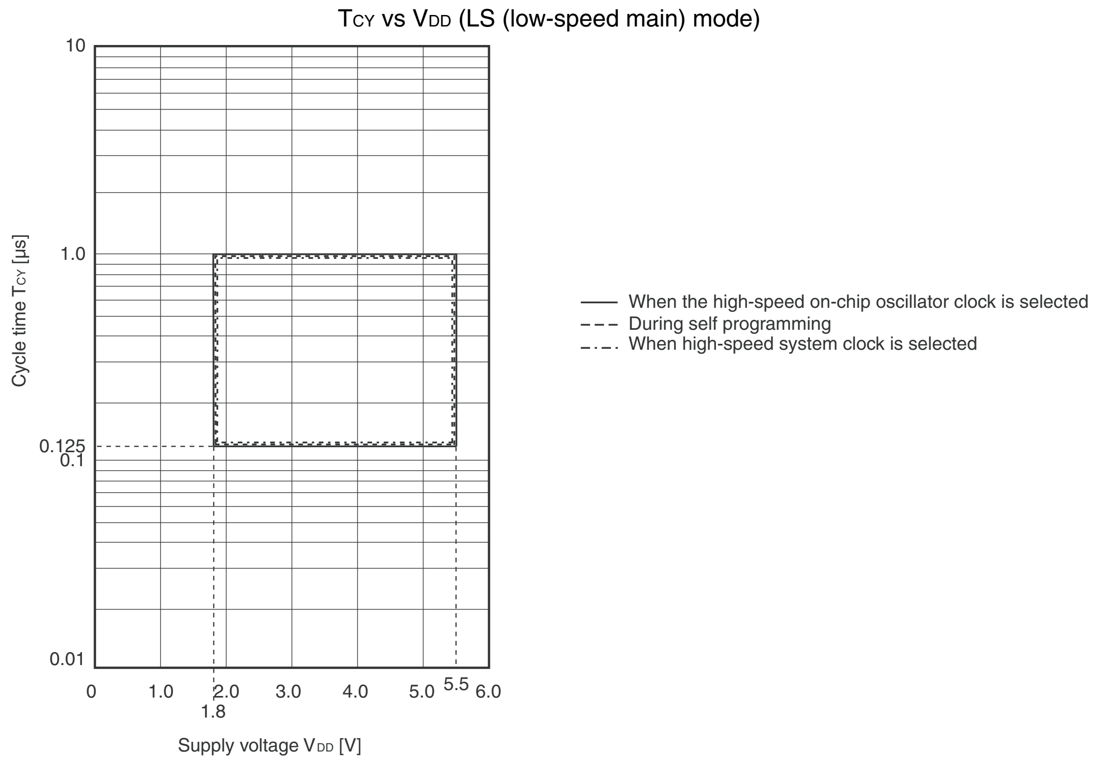
(T_A = –40 to +85°C, 1.8 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Items	Symbol	Conditions			MIN.	TYP.	MAX.	Unit
Instruction cycle (minimum instruction execution time)	T_{CY}	Main system clock (f_{MAIN}) operation	HS (High-speed main) mode	2.7 V ≤ V_{DD} ≤ 5.5 V	0.04167		1	μs
				2.4 V ≤ V_{DD} < 2.7 V	0.0625		1	μs
			LS (Low-speed main) mode	1.8 V ≤ V_{DD} ≤ 5.5 V	0.125		1	μs
		During self programming	HS (High-speed main) mode	2.7 V ≤ V_{DD} ≤ 5.5 V	0.04167		1	μs
				2.4 V ≤ V_{DD} < 2.7 V	0.0625		1	μs
			LS (Low-speed main) mode	1.8 V ≤ V_{DD} ≤ 5.5 V	0.125		1	μs
External main system clock frequency	f_{EX}	2.7 V ≤ V_{DD} ≤ 5.5 V			1.0		20.0	MHz
		2.4 V ≤ V_{DD} < 2.7 V			1.0		16.0	MHz
		1.8 V ≤ V_{DD} < 2.4 V			1.0		8.0	MHz
External main system clock input high-level width, low-level width	t_{EXH}, t_{EXL}	2.7 V ≤ V_{DD} ≤ 5.5 V			24			ns
		2.4 V ≤ V_{DD} < 2.7 V			30			ns
		1.8 V ≤ V_{DD} < 2.4 V			60			ns
TI00 to TI07 input high-level width, low-level width	t_{TIH}, t_{TIL}				1/f_{MCK} + 10			ns
TO00 to TO07 output frequency	f_{TO}	4.0 V ≤ V_{DD} ≤ 5.5 V					12	MHz
		2.7 V ≤ V_{DD} < 4.0 V					8	MHz
		1.8 V ≤ V_{DD} < 2.7 V					4	MHz
PCLBUZ0, or PCLBUZ1 output frequency	f_{PCL}	4.0 V ≤ V_{DD} ≤ 5.5 V					16	MHz
		2.7 V ≤ V_{DD} < 4.0 V					8	MHz
		1.8 V ≤ V_{DD} < 2.7 V					4	MHz
INTP0 to INTP5 input high-level width, low-level width	t_{INTH}, t_{INTL}				1			μs
KR0 to KR9 input available width	t_{KR}				250			ns
$\overline{\text{RESET}}$ low-level width	t_{RSL}				10			μs

Remark f_{MCK}: Timer array unit operation clock frequency
(Operation clock to be set by the timer clock select register 0 (TPS0) and the CKS0n bit of timer mode register 0n (TMR0n). n: Channel number (n = 0 to 7))

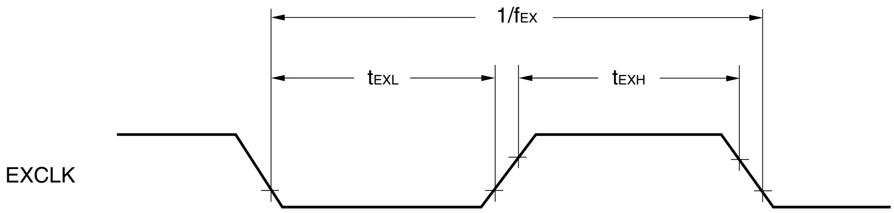
Minimum Instruction Execution Time during Main System Clock Operation



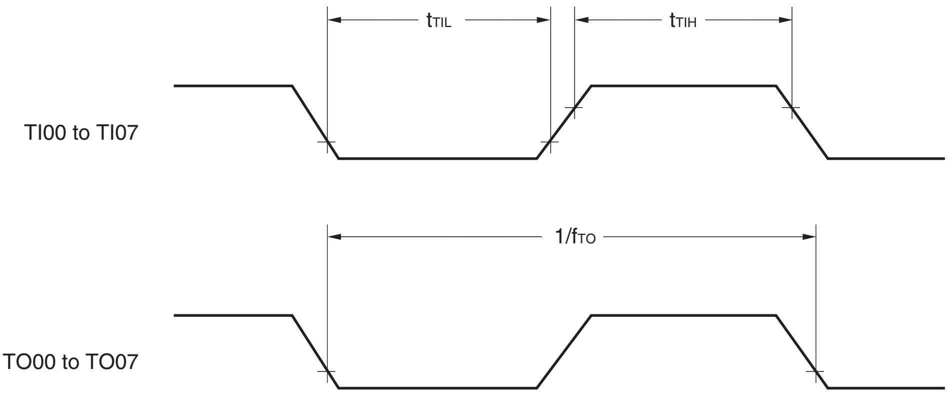


AC Timing Test Point

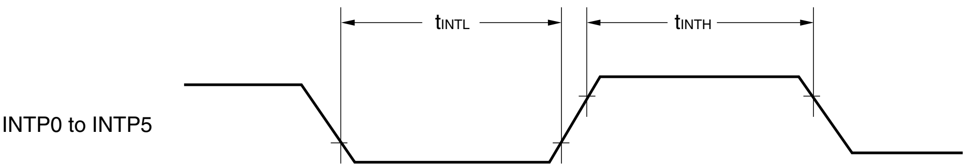
External Main System Clock Timing



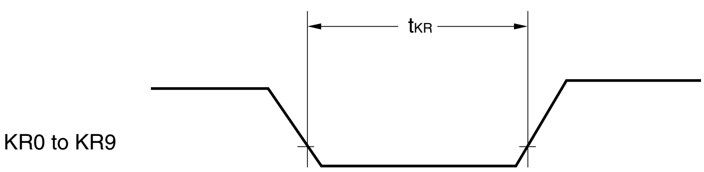
TI/TO Timing



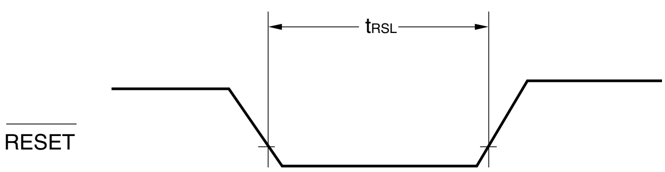
Interrupt Request Input Timing



Key Interrupt Input Timing



$\overline{\text{RESET}}$ Input Timing



2.5 Peripheral Functions Characteristics

AC Timing Test Point

2.5.1 Serial array unit

(1) During communication at same potential (UART mode)
(T_A = –40 to +85°C, 1.8 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

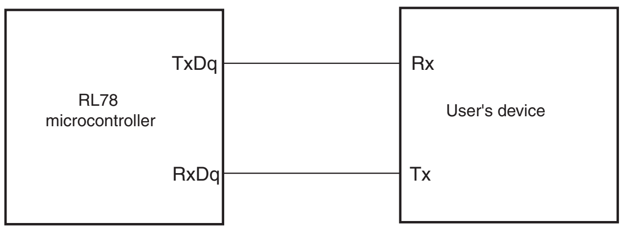
Parameter	Symbol	Conditions	HS (high-speed main) Mode		LS (low-speed main) Mode		Unit
			MIN.	MAX.	MIN.	MAX.	
Transfer rate Note 1				$f_{MCK}/6$		$f_{MCK}/6$	bps
		Theoretical value of the maximum transfer rate $f_{CLK} = f_{MCK}$ Note2		4.0		1.3	Mbps

Notes 1. Transfer rate in the SNOOZE mode is 4800 bps only.

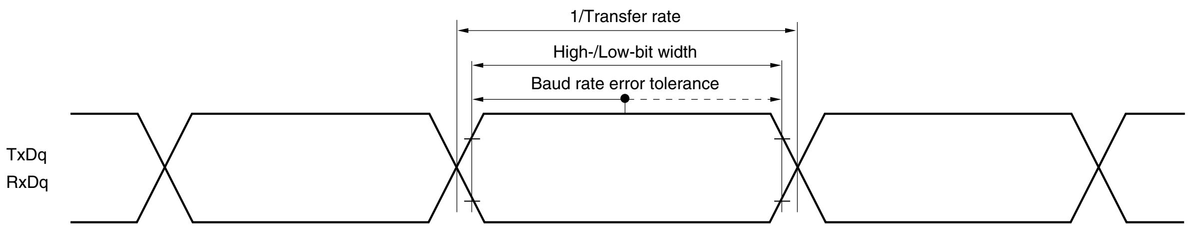
2. The maximum operating frequencies of the CPU/peripheral hardware clock (f_{CLK}) are:
HS (high-speed main) mode: 24 MHz (2.7 V ≤ V_{DD} ≤ 5.5 V)
16 MHz (2.4 V ≤ V_{DD} ≤ 5.5 V)
LS (low-speed main) mode: 8 MHz (1.8 V ≤ V_{DD} ≤ 5.5 V)

Caution Select the normal input buffer for the RxDq pin and the normal output mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg).

UART mode connection diagram (during communication at same potential)



UART mode bit width (during communication at same potential) (reference)



Remarks 1. q: UART number (q = 0 to 2), g: PIM, POM number (g = 0, 1)

2. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the serial clock select register m (SPSm) and the CKSmn bit of serial mode register mn (SMRmn).
m: Unit number, n: Channel number (mn = 00 to 03, 10, 11))

(2) During communication at same potential (CSI mode) (master mode, SCK00... internal clock output, corresponding CSI00 only)

(T_A = –40 to +85°C, 2.7 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions	HS (high-speed main) Mode		LS (low-speed main) Mode		Unit
			MIN.	MAX.	MIN.	MAX.	
SCK00 cycle time	t_{KCY1}	t_{KCY1} ≥ 2/f_{CLK}	83.3		250		ns
SCK00 high-/low-level width	t_{KH1}, t_{KL1}	4.0 V ≤ V_{DD} ≤ 5.5 V	t_{KCY1}/2–7		t_{KCY1}/2–50		ns
		2.7 V ≤ V_{DD} ≤ 5.5 V	t_{KCY1}/2–10		t_{KCY1}/2–50		ns
SI00 setup time (to SCK00↑) Note 1	t_{SIK1}	4.0 V ≤ V_{DD} ≤ 5.5 V	23		110		ns
		2.7 V ≤ V_{DD} ≤ 5.5 V	33		110		ns
SI00 hold time (from SCK00↑) Note2	t_{KSI1}		10		10		ns
Delay time from SCK00↓ to SO00 output Note 3	t_{KSO1}	C = 20 pF Note 4		10		10	ns

Notes 1. When DAP00 = 0 and CKP00 = 0, or DAP00 = 1 and CKP00 = 1. The SI00 setup time becomes "to SCK00↓" when DAP00 = 0 and CKP00 = 1, or DAP00 = 1 and CKP00 = 0.

2. When DAP00 = 0 and CKP00 = 0, or DAP00 = 1 and CKP00 = 1. The SI00 hold time becomes "from SCK00↓" when DAP00 = 0 and CKP00 = 1, or DAP00 = 1 and CKP00 = 0.

3. When DAP00 = 0 and CKP00 = 0, or DAP00 = 1 and CKP00 = 1. The delay time to SO00 output becomes "from SCK00↑" when DAP00 = 0 and CKP00 = 1, or DAP00 = 1 and CKP00 = 0.

4. C is the load capacitance of the SCK00 and SO00 output lines.

Caution Select the normal input buffer for the SI00 pin and the normal output mode for the SO00 and SCK00 pins by using port input mode register 1 (PIM1) and port output mode register 1 (POM1).

Remarks 1. This specification is valid only when CSI00's peripheral I/O redirect function is not used.

2. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the serial clock select register 0 (SPS0) and the CKS00 bit of serial mode register 00 (SMR00).)

(3) During communication at same potential (CSI mode) (master mode, SCKp... internal clock output)
(T_A = –40 to +85°C, 1.8 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions		HS (high-speed main) Mode		LS (low-speed main) Mode		Unit
				MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	t_{KCY1}	t_{KCY1} ≥ 4/f_{CLK}	2.7 V ≤ V_{DD} ≤ 5.5 V	167		500		ns
			2.4 V ≤ V_{DD} ≤ 5.5 V	250		500		ns
			1.8 V ≤ V_{DD} ≤ 5.5 V	–		500		ns
SCKp high-/low-level width	t_{KH1}, t_{KL1}	4.0 V ≤ V_{DD} ≤ 5.5 V		t_{KCY1}/2–12		t_{KCY1}/2–50		ns
		2.7 V ≤ V_{DD} ≤ 5.5 V		t_{KCY1}/2–18		t_{KCY1}/2–50		ns
		2.4 V ≤ V_{DD} ≤ 5.5 V		t_{KCY1}/2–38		t_{KCY1}/2–50		ns
		1.8 V ≤ V_{DD} ≤ 5.5 V		–		t_{KCY1}/2–50		ns
SIp setup time (to SCKp↑) Note 1	t_{SIK1}	4.0 V ≤ V_{DD} ≤ 5.5 V		44		110		ns
		2.7 V ≤ V_{DD} ≤ 5.5 V		44		110		ns
		2.4 V ≤ V_{DD} ≤ 5.5 V		75		110		ns
		1.8 V ≤ V_{DD} ≤ 5.5 V		–		110		ns
SIp hold time (from SCKp↑) Note 2	t_{KSI1}			19		19		ns
Delay time from SCKp↓ to SOp output Note 3	t_{KSO1}	C = 30 pF Note4			25		25	ns

Notes 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes “to SCKp↓” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes “from SCKp↓” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes “from SCKp↑” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

4. C is the load capacitance of the SCKp and SOp output lines.

Caution Select the normal input buffer for the SIp pin and the normal output mode for the SOp and SCKp pins by using port input mode register 1 (PIM1) and port output mode registers 0, 1, 4 (POM0, POM1, POM4).

Remarks 1. p: CSI number (p = 00, 01, 11, 20), m: Unit number (m = 0, 1), n: Channel number (n = 0, 1, 3: “1, 3” is only for the R5F102 products)

2. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the serial clock select register m (SPSm) and the CKSmn bit of serial mode register mn (SMRmn). m: Unit number (m = 0, 1), n: Channel number (n = 0, 1, 3: “1, 3” is only for the R5F102 products.))

(4) During communication at same potential (CSI mode) (slave mode, SCKp... external clock input)
(T_A = –40 to +85°C, 1.8 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions		HS (high-speed main) Mode		LS (low-speed main) Mode		Unit
				MIN.	MAX.	MIN.	MAX.	
SCKp cycle time Note4	t_{KCY2}	4.0 V ≤ V_{DD} ≤ 5.5 V	20 MHz < f_{MCK}	8/f_{MCK}		–		ns
			f_{MCK} ≤ 20 MHz	6/f_{MCK}		6/f_{MCK}		ns
		2.7 V ≤ V_{DD} ≤ 5.5 V	16 MHz < f_{MCK}	8/f_{MCK}		–		ns
			f_{MCK} ≤ 16 MHz	6/f_{MCK}		6/f_{MCK}		ns
		2.4 V ≤ V_{DD} ≤ 5.5 V		6/f_{MCK} and 500		6/f_{MCK} and 500		ns
		1.8 V ≤ V_{DD} ≤ 5.5 V		–		6/f_{MCK} and 750		ns
SCKp high-/low-level width	t_{KH2}, t_{KL2}	4.0 V ≤ V_{DD} ≤ 5.5 V		t_{KCY2}/2–7		t_{KCY2}/2–7		ns
		2.7 V ≤ V_{DD} ≤ 5.5 V		t_{KCY2}/2–8		t_{KCY2}/2–8		ns
		2.4 V ≤ V_{DD} ≤ 5.5 V		t_{KCY2}/2–18		t_{KCY2}/2–18		ns
		1.8 V ≤ V_{DD} ≤ 5.5 V		–		t_{KCY2}/2–18		ns
SIp setup time (to SCKp↑) Note 1	t_{SIK2}	2.7 V ≤ V_{DD} ≤ 5.5 V		1/f_{MCK} + 20		1/f_{MCK} + 30		ns
		2.4 V ≤ V_{DD} ≤ 5.5 V		1/f_{MCK} + 30		1/f_{MCK} + 30		ns
		1.8 V ≤ V_{DD} ≤ 5.5 V		–		1/f_{MCK} + 30		ns
SIp hold time (from SCKp↑) Note 2	t_{KSI2}			1/f_{MCK} + 31		1/f_{MCK} + 31		ns
Delay time from SCKp↓ to SOp output Note 3	t_{KSO2}	C = 30 pF Note4	2.7 V ≤ V_{DD} ≤ 5.5 V		2/f_{MCK} + 44		2/f_{MCK} + 110	ns
			2.4 V ≤ V_{DD} ≤ 5.5 V		2/f_{MCK} + 75		2/f_{MCK} + 110	ns
			1.8 V ≤ V_{DD} ≤ 5.5 V		–		2/f_{MCK} + 110	ns

Notes 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes “to SCKp↓” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes “from SCKp↓” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

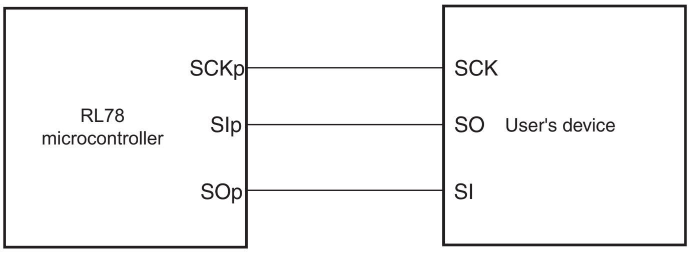
3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes “from SCKp↑” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

4. C is the load capacitance of the SOp output lines.

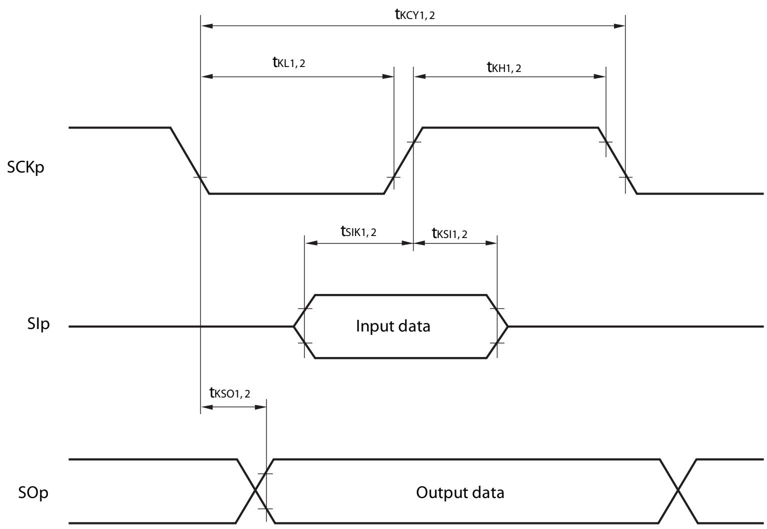
5. Transfer rate in the SNOOZE mode: MAX. 1 Mbps

Caution Select the normal input buffer for the SIp and SCKp pins and the normal output mode for the SOp pin by using port input mode register 1 (PIM1) and port output mode registers 0, 1, 4 (POM0, POM1, POM4).

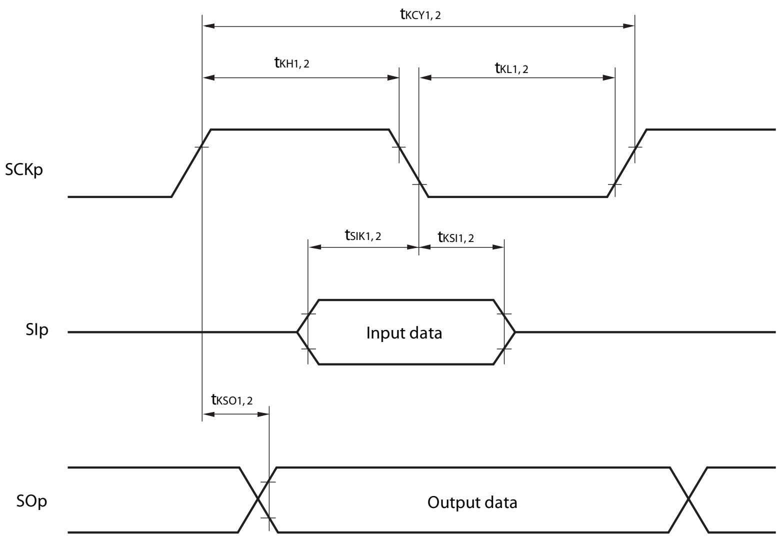
CSI mode connection diagram (during communication at same potential)



CSI mode serial transfer timing (during communication at same potential)
(When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



CSI mode serial transfer timing (during communication at same potential)
(When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



(**Remarks** are listed on the next page.)

Remarks 1. p: CSI number (p = 00, 01, 11, 20), m: Unit number (m = 0, 1), n: Channel number (n = 0, 1, 3: "1, 3" is only for the R5F102 products.)

2. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the serial clock select register m (SPSm) and the CKSmn bit of serial mode register mn (SMRmn). m: Unit number (m = 0, 1), n: Channel number (n = 0, 1, 3: "1, 3" is only for the R5F102 products.))

(5) During communication at same potential (simplified I²C mode)
(T_A = –40 to +85°C, 1.8 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions	HS (high-speed main) Mode LS (low-speed main) Mode		Unit
			MIN.	MAX.	
SCLr clock frequency	f_{SCL}	1.8 V ≤ V_{DD} ≤ 5.5 V, C_b = 100 pF, R_b = 3 kΩ		400 Note 1	kHz
		1.8 V ≤ V_{DD} < 2.7 V, C_b = 100 pF, R_b = 5 kΩ		300 Note 1	kHz
Hold time when SCLr = "L"	t_{LOW}	1.8 V ≤ V_{DD} ≤ 5.5 V, C_b = 100 pF, R_b = 3 kΩ	1150		ns
		1.8 V ≤ V_{DD} < 2.7 V, C_b = 100 pF, R_b = 5 kΩ	1550		ns
Hold time when SCLr = "H"	t_{HIGH}	1.8 V ≤ V_{DD} ≤ 5.5 V, C_b = 100 pF, R_b = 3 kΩ	1150		ns
		1.8 V ≤ V_{DD} < 2.7 V, C_b = 100 pF, R_b = 5 kΩ	1550		ns
Data setup time (reception)	$t_{SU:DAT}$	1.8 V ≤ V_{DD} ≤ 5.5 V, C_b = 100 pF, R_b = 3 kΩ	1/f_{MCK} + 145 Note 2		ns
		1.8 V ≤ V_{DD} < 2.7 V, C_b = 100 pF, R_b = 5 kΩ	1/f_{MCK} + 230 Note 2		ns
Data hold time (transmission)	$t_{HD:DAT}$	1.8 V ≤ V_{DD} ≤ 5.5 V, C_b = 100 pF, R_b = 3 kΩ	0	355	ns
		1.8 V ≤ V_{DD} < 2.7 V, C_b = 100 pF, R_b = 5 kΩ	0	405	ns

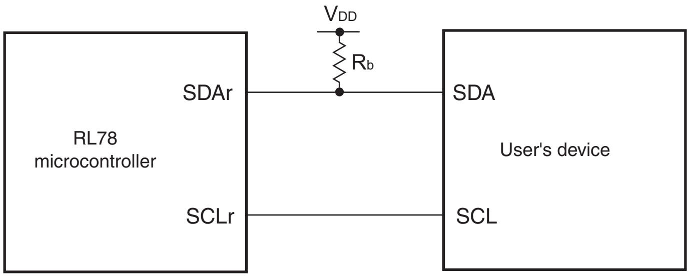
Notes 1. The value must also be equal to or less than f_{MCK}/4.

2. Set $t_{SU:DAT}$ so that it will not exceed the hold time when SCLr = "L" or SCLr = "H".

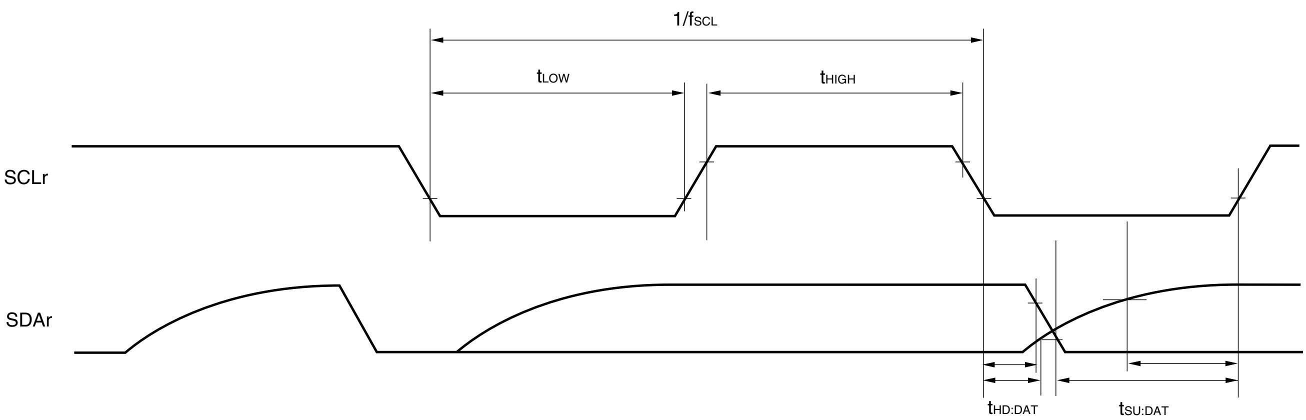
Caution Select the N-ch open drain output (V_{DD} tolerance) mode for SDAr by using port output mode register h (POMh).

(**Remarks** are listed on the next page.)

Simplified I²C mode connection diagram (during communication at same potential)



Simplified I²C mode serial transfer timing (during communication at same potential)



Remarks 1. R_b [Ω]:Communication line (SDAr) pull-up resistance
C_b [F]: Communication line (SCLr, SDAr) load capacitance

2. r: IIC number (r = 00, 01, 11, 20), h: = POM number (h = 0, 1, 4, 5)

3. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the serial clock select register m (SPSm) and the CKSmn bit of serial mode register mn (SMRmn). m: Unit number (m = 0, 1), n: Channel number (0, 1, 3))

4. Simplified I²C mode is supported only by the R5F102 products.

(6) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode)
(T_A = –40 to +85°C, 1.8 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

<table>
<tr><th rowspan="2">Parameter</th><th rowspan="2">Symbol</th><th rowspan="2" colspan="3">Conditions</th><th colspan="2">HS (high-speed main) Mode</th><th colspan="2">LS (low-speed main) Mode</th><th rowspan="2">Unit</th></tr>
<tr><th>MIN.</th><th>MAX.</th><th>MIN.</th><th>MAX.</th></tr>
<tr><td rowspan="12">Transfer rate Note4</td><td rowspan="12"></td><td rowspan="6">Reception</td><td colspan="2">4.0 V ≤ V_{DD} ≤ 5.5 V,
2.7 V ≤ V_b ≤ 4.0 V</td><td></td><td>f_{MCK}/6 Note1</td><td></td><td>f_{MCK}/6 Note1</td><td>bps</td></tr>
<tr><td></td><td>Theoretical value of the maximum transfer rate
f_{MCK} = f_{CLK} Note3</td><td></td><td>4.0</td><td></td><td>1.3</td><td>Mbps</td></tr>
<tr><td colspan="2">2.7 V ≤ V_{DD} < 4.0 V,
2.3 V ≤ V_b ≤ 2.7 V</td><td></td><td>f_{MCK}/6 Note1</td><td></td><td>f_{MCK}/6 Note1</td><td>bps</td></tr>
<tr><td></td><td>Theoretical value of the maximum transfer rate
f_{MCK} = f_{CLK} Note3</td><td></td><td>4.0</td><td></td><td>1.3</td><td>Mbps</td></tr>
<tr><td colspan="2">1.8 V ≤ V_{DD} < 3.3 V,
1.6 V ≤ V_b ≤ 2.0 V</td><td></td><td>f_{MCK}/6 Notes1, 2</td><td></td><td>f_{MCK}/6 Notes1, 2</td><td>bps</td></tr>
<tr><td></td><td>Theoretical value of the maximum transfer rate
f_{MCK} = f_{CLK} Note3</td><td></td><td>4.0</td><td></td><td>1.3</td><td>Mbps</td></tr>
<tr><td rowspan="6">Transmission</td><td colspan="2">4.0 V ≤ V_{DD} ≤ 5.5 V,
2.7 V ≤ V_b ≤ 4.0 V</td><td></td><td>**Note4**</td><td></td><td>**Note4**</td><td>bps</td></tr>
<tr><td></td><td>Theoretical value of the maximum transfer rate
C_b = 50 pF, R_b = 1.4 kΩ, V_b = 2.7 V</td><td></td><td>2.8 Note5</td><td></td><td>2.8 Note5</td><td>Mbps</td></tr>
<tr><td colspan="2">2.7 V ≤ V_{DD} < 4.0 V,
2.3 V ≤ V_b ≤ 2.7 V,</td><td></td><td>**Note6**</td><td></td><td>**Note6**</td><td>bps</td></tr>
<tr><td></td><td>Theoretical value of the maximum transfer rate
C_b = 50 pF, R_b = 2.7 kΩ, V_b = 2.3 V</td><td></td><td>1.2 Note7</td><td></td><td>1.2 Note7</td><td>Mbps</td></tr>
<tr><td colspan="2">1.8 V ≤ V_{DD} < 3.3 V,
1.6 V ≤ V_b ≤ 2.0 V</td><td></td><td>**Notes 2, 8**</td><td></td><td>**Notes 2, 8**</td><td>bps</td></tr>
<tr><td></td><td>Theoretical value of the maximum transfer rate
C_b = 50 pF, R_b = 5.5 kΩ, V_b = 1.6 V</td><td></td><td>0.43 Note9</td><td></td><td>0.43 Note9</td><td>Mbps</td></tr>
</table>

Notes 1. Transfer rate in the SNOOZE mode is 4800 bps only.

2. Use it with V_{DD} ≥ V_b.

3. The maximum operating frequencies of the CPU/peripheral hardware clock (f_{CLK}) are:
HS (high-speed main) mode: 24 MHz (2.7 V ≤ V_{DD} ≤ 5.5 V)
16 MHz (2.4 V ≤ V_{DD} ≤ 5.5 V)
LS (low-speed main) mode: 8 MHz (1.8 V ≤ V_{DD} ≤ 5.5 V)

4. The smaller maximum transfer rate derived by using f_{MCK}/6 or the following expression is the valid maximum transfer rate.
Expression for calculating the transfer rate when 4.0 V ≤ V_{DD} ≤ 5.5 V and 2.7 V ≤ V_b ≤ 4.0 V

$$\text{Maximum transfer rate} = \frac{1}{\{-C_b \times R_b \times \ln(1 - \frac{2.2}{V_b})\} \times 3} \text{ [bps]}$$

$$\text{Baud rate error (theoretical value)} = \frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{2.2}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 \text{ [\%]}$$

* This value is the theoretical value of the relative difference between the transmission and reception sides.

5. This value as an example is calculated when the conditions described in the “Conditions” column are met. Refer to **Note 4** above to calculate the maximum transfer rate under conditions of the customer.

6. The smaller maximum transfer rate derived by using $f_{MCK}/6$ or the following expression is the valid maximum transfer rate.
Expression for calculating the transfer rate when 2.7 V ≤ V_{DD} < 4.0 V and 2.3 V ≤ V_b ≤ 2.7 V

$$\text{Maximum transfer rate} = \frac{1}{\{-C_b \times R_b \times \ln(1 - \frac{2.0}{V_b})\} \times 3} \text{ [bps]}$$

$$\text{Baud rate error (theoretical value)} = \frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{2.0}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 \text{ [\%]}$$

* This value is the theoretical value of the relative difference between the transmission and reception sides.

7. This value as an example is calculated when the conditions described in the “Conditions” column are met. Refer to **Note 6** above to calculate the maximum transfer rate under conditions of the customer.

8. The smaller maximum transfer rate derived by using $f_{MCK}/6$ or the following expression is the valid maximum transfer rate.
Expression for calculating the transfer rate when 1.8 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V

$$\text{Maximum transfer rate} = \frac{1}{\{-C_b \times R_b \times \ln(1 - \frac{1.5}{V_b})\} \times 3} \text{ [bps]}$$

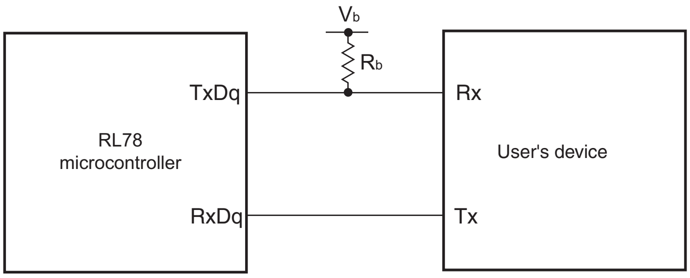
$$\text{Baud rate error (theoretical value)} = \frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{1.5}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 \text{ [\%]}$$

* This value is the theoretical value of the relative difference between the transmission and reception sides.

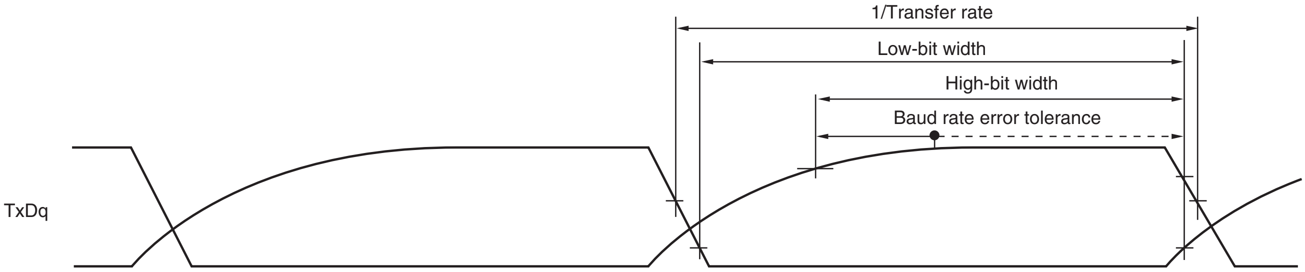
9. This value as an example is calculated when the conditions described in the “Conditions” column are met. Refer to **Note 8** above to calculate the maximum transfer rate under conditions of the customer.

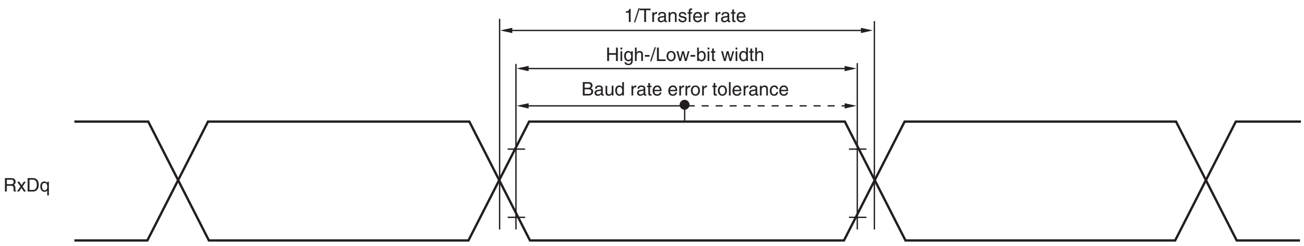
Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (V_{DD} tolerance) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). **For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.**

UART mode connection diagram (during communication at different potential)



UART mode bit width (during communication at different potential) (reference)





Remarks 1. R_b[Ω]: Communication line (TxDq) pull-up resistance, C_b[F]: Communication line (TxDq) load capacitance, V_b[V]: Communication line voltage

2. q: UART number (q = 0 to 2), g: PIM and POM number (g = 0, 1)

3. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the serial clock select register m (SPSm) and the CKSmn bit of serial mode register mn (SMRmn).
m: Unit number, n: Channel number (mn = 00 to 03, 10, 11))

4. UART0 of the 20- and 24-pin products supports communication at different potential only when the peripheral I/O redirection function is not used.

(7) Communication at different potential (2.5 V, 3 V) (CSI mode) (master mode, SCK00... internal clock output, corresponding CSI00 only)

(T_A = –40 to +85°C, 2.7 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions		HS (high-speed main) Mode		LS (low-speed main) Mode		Unit
				MIN.	MAX.	MIN.	MAX.	
SCK00 cycle time	t_{KCY1}	t_{KCY1} ≥ 2/f_{CLK}	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 20 pF, R_b = 1.4 kΩ	200		1150		ns
			2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 20 pF, R_b = 2.7 kΩ	300		1150		ns
SCK00 high-level width	t_{KH1}	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 20 pF, R_b = 1.4 kΩ		t_{KCY1}/2 – 50		t_{KCY1}/2– 50		ns
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 20 pF, R_b = 2.7 kΩ		t_{KCY1}/2 – 120		t_{KCY1}/2 – 120		ns
SCK00 low-level width	t_{KL1}	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 20 pF, R_b = 1.4 kΩ		t_{KCY1}/2 – 7		t_{KCY1}/2 – 50		ns
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 20 pF, R_b = 2.7 kΩ		t_{KCY1}/2 – 10		t_{KCY1}/2 – 50		ns
SI00 setup time (to SCK00↑) Note 1	t_{SIK1}	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 20 pF, R_b = 1.4 kΩ		58		479		ns
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 20 pF, R_b = 2.7 kΩ		121		479		ns
SI00 hold time (from SCK00↑) Note 1	t_{KSI1}	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 20 pF, R_b = 1.4 kΩ		10		10		ns
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 20 pF, R_b = 2.7 kΩ		10		10		ns
Delay time from SCK00↓ to SO00 output Note 1	t_{KSO1}	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 20 pF, R_b = 1.4 kΩ			60		60	ns
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 20 pF, R_b = 2.7 kΩ			130		130	ns
SI00 setup time (to SCK00↓) Note 2	t_{SIK1}	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 20 pF, R_b = 1.4 kΩ		23		110		ns
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 20 pF, R_b = 2.7 kΩ		33		110		ns
SI00 hold time (from SCK00↓) Note 2	t_{KSI1}	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 20 pF, R_b = 1.4 kΩ		10		10		ns
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 20 pF, R_b = 2.7 kΩ		10		10		ns
Delay time from SCK00↑ to SO00 output Note 2	t_{KSO1}	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 20 pF, R_b = 1.4 kΩ			10		10	ns
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 20 pF, R_b = 2.7 kΩ			10		10	ns

(**Notes**, **Caution**, and **Remarks** are listed on the next page.)

Notes 1. When DAP00 = 0 and CKP00 = 0, or DAP00 = 1 and CKP00 = 1

2. When DAP00 = 0 and CKP00 = 1, or DAP00 = 1 and CKP00 = 0.

Caution Select the TTL input buffer for the SI00 pin and the N-ch open drain output (V_{DD} tolerance) mode for the SO00 pin and SCK00 pin by using port input mode register 1 (PIM1) and port output mode register 1 (POM1). **For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.**

Remarks 1. R_b [Ω]:Communication line (SCK00, SO00) pull-up resistance, C_b [F]: Communication line (SCK00, SO00) load capacitance, V_b [V]: Communication line voltage

2. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the serial clock select register 0 (SPS0) and the CKS00 bit of serial mode register 00 (SMR00).)

(8) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output) (1/3)

(T_A = –40 to +85°C, 1.8 V ≤ V_{DD} ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions		HS (high-speed main) Mode		LS (low-speed main) Mode		Unit
				MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	t_{KCY1}	t_{KCY1} ≥ 4/f_{CLK}	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 30 pF, R_b = 1.4 kΩ	300		1150		ns
			2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ	500		1150		ns
			1.8 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note, C_b = 30 pF, R_b = 5.5 kΩ	1150		1150		ns
SCKp high-level width	t_{KH1}	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 30 pF, R_b = 1.4 kΩ		t_{KCY1}/2 –75		t_{KCY1}/2–75		ns
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ		t_{KCY1}/2 –170		t_{KCY1}/2–170		ns
		1.8 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note, C_b = 30 pF, R_b = 5.5 kΩ		t_{KCY1}/2 –458		t_{KCY1}/2–458		ns
SCKp low-level width	t_{KL1}	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 30 pF, R_b = 1.4 kΩ		t_{KCY1}/2 –12		t_{KCY1}/2–50		ns
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ		t_{KCY1}/2 –18		t_{KCY1}/2–50		ns
		1.8 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note, C_b = 30 pF, R_b = 5.5 kΩ		t_{KCY1}/2 –50		t_{KCY1}/2–50		ns

Note Use it with V_{DD} ≥ V_b.

Cautions 1. Select the TTL input buffer for the SIp pin and the N-ch open drain output (V_{DD} tolerance) mode for the SOp pin and SCKp pin by using port input mode register 1 (PIM1) and port output mode register 1 (POM1). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

2. CSI01 and CSI11 cannot communicate at different potential.

Remarks 1. R_b [Ω]: Communication line (SCKp, SOp) pull-up resistance, C_b [F]: Communication line (SCKp, SOp) load capacitance, V_b [V]: Communication line voltage

2. p: CSI number (p = 00, 20)

(8) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output) (2/3)

(T_A = –40 to +85°C, 1.8 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions	HS (high-speed main) Mode		LS (low-speed main) Mode		Unit
			MIN.	MAX.	MIN.	MAX.	
SIp setup time (to SCKp↑) Note 1	t_{SIK1}	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 30 pF, R_b = 1.4 kΩ	81		479		ns
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ	177		479		ns
		1.8 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 2, C_b = 30 pF, R_b = 5.5 kΩ	479		479		ns
SIp hold time (from SCKp↑) Note 1	t_{KSI1}	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 30 pF, R_b = 1.4 kΩ	19		19		ns
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ	19		19		ns
		1.8 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 2, C_b = 30 pF, R_b = 5.5 kΩ	19		19		ns
Delay time from SCKp↓ to SOp output Note 1	t_{KSO1}	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 30 pF, R_b = 1.4 kΩ		100		100	ns
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ		195		195	ns
		1.8 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 2, C_b = 30 pF, R_b = 5.5 kΩ		483		483	ns

Notes 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.

2. Use it with V_{DD} ≥ V_b.

(**Cautions** and **Remarks** are listed on the next page.)

(8) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output) (3/3)

(T_A = –40 to +85°C, 1.8 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions	HS (high-speed main) Mode		LS (low-speed main) Mode		Unit
			MIN.	MAX.	MIN.	MAX.	
SIp setup time (to SCKp↓) Note 1	t_{SIK1}	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 30 pF, R_b = 1.4 kΩ	44		110		ns
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ	44		110		ns
		1.8 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 2, C_b = 30 pF, R_b = 5.5 kΩ	110		110		ns
SIp hold time (from SCKp↓) Note 1	t_{KSI1}	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 30 pF, R_b = 1.4 kΩ	19		19		ns
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ	19		19		ns
		1.8 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 2, C_b = 30 pF, R_b = 5.5 kΩ	19		19		ns
Delay time from SCKp↑ to SOp output Note 1	t_{KSO1}	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 30 pF, R_b = 1.4 kΩ		25		25	ns
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ		25		25	ns
		1.8 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 2, C_b = 30 pF, R_b = 5.5 kΩ		25		25	ns

Notes 1. When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

2. Use it with V_{DD} ≥ V_b.

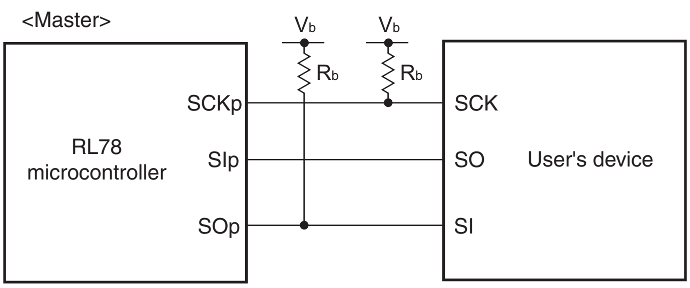
Cautions 1. Select the TTL input buffer for the SIp pin and the N-ch open drain output (V_{DD} tolerance) mode for the SOp pin and SCKp pin by using port input mode register 1 (PIM1) and port output mode register 1 (POM1). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

2. CSI01 and CSI11 cannot communicate at different potential.

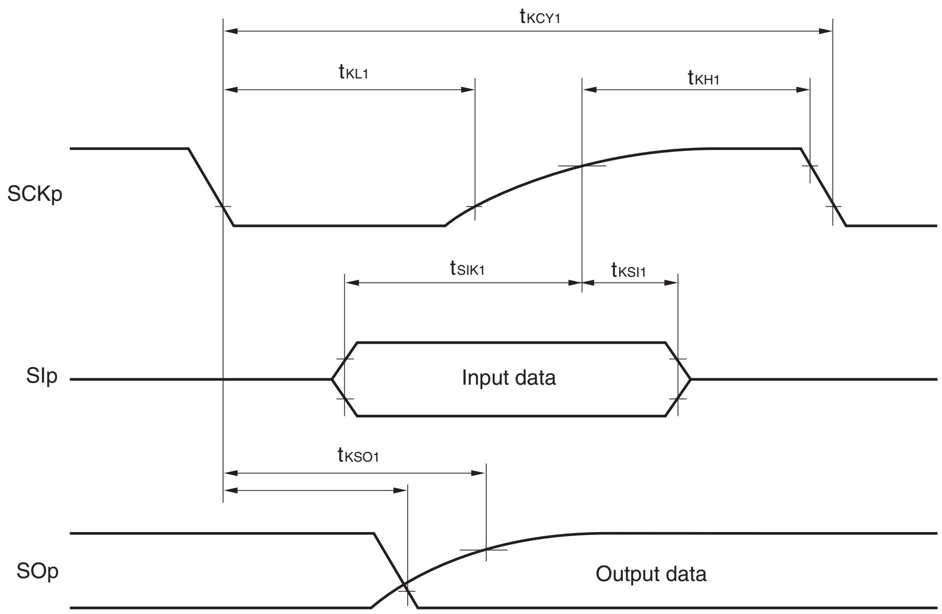
Remarks 1. R_b [Ω]: Communication line (SCKp, SOp) pull-up resistance, C_b [F]: Communication line (SCKp, SOp) load capacitance, V_b [V]: Communication line voltage

2. p: CSI number (p = 00, 20), m: Unit number (m = 0, 1), n: Channel number (n = 0)

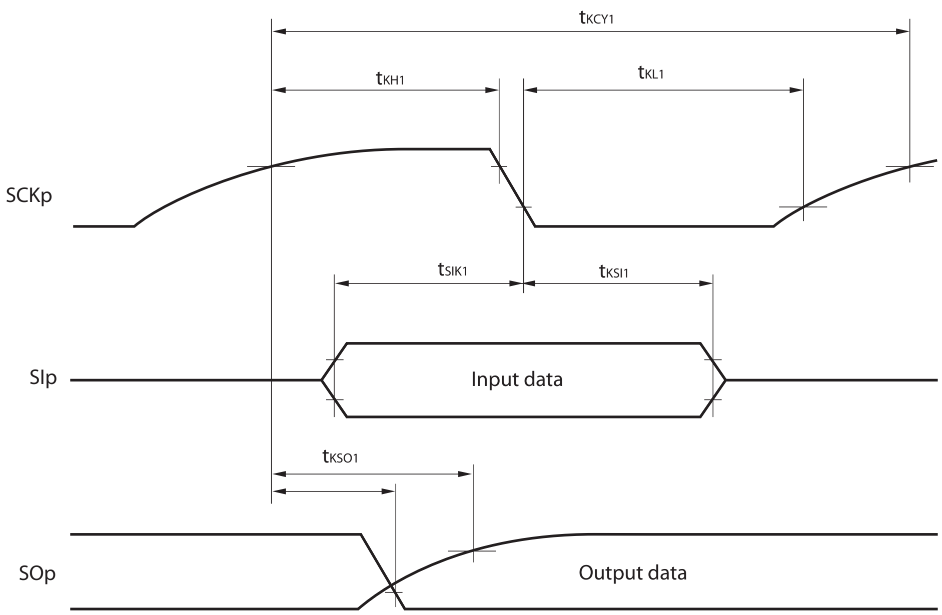
CSI mode connection diagram (during communication at different potential)



CSI mode serial transfer timing (master mode) (during communication at different potential)
(When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1)



CSI mode serial transfer timing (master mode) (during communication at different potential)
(When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



(9) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (slave mode, SCKp... external clock input)
(T_A = –40 to +85°C, 1.8 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions		HS (high-speed main) Mode		LS (low-speed main) Mode		Unit
				MIN.	MAX.	MIN.	MAX.	
SCKp cycle time Note 1	t_{KCY2}	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V	20 MHz < f_{MCK} ≤ 24 MHz	12/f_{MCK}		–		ns
			8 MHz < f_{MCK} ≤ 20 MHz	10/f_{MCK}		–		ns
			4 MHz < f_{MCK} ≤ 8 MHz	8/f_{MCK}		16/f_{MCK}		ns
			f_{MCK} ≤ 4 MHz	6/f_{MCK}		10/f_{MCK}		ns
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V	20 MHz < f_{MCK} ≤ 24 MHz	16/f_{MCK}		–		ns
			16 MHz < f_{MCK} ≤ 20 MHz	14/f_{MCK}		–		ns
			8 MHz < f_{MCK} ≤ 16 MHz	12/f_{MCK}		–		ns
			4 MHz < f_{MCK} ≤ 8 MHz	8/f_{MCK}		16/f_{MCK}		ns
			f_{MCK} ≤ 4 MHz	6/f_{MCK}		10/f_{MCK}		ns
		1.8 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 2	20 MHz < f_{MCK} ≤ 24 MHz	36/f_{MCK}		–		ns
			16 MHz < f_{MCK} ≤ 20 MHz	32/f_{MCK}		–		ns
			8 MHz < f_{MCK} ≤ 16 MHz	26/f_{MCK}		–		ns
			4 MHz < f_{MCK} ≤ 8 MHz	16/f_{MCK}		16/f_{MCK}		ns
			f_{MCK} ≤ 4 MHz	10/f_{MCK}		10/f_{MCK}		ns
SCKp high-/low-level width	t_{KH2}, t_{KL2}	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V		t_{KCY2}/2 – 12		t_{KCY2}/2 – 50		ns
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V		t_{KCY2}/2 – 18		t_{KCY2}/2 – 50		ns
		1.8 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 2		t_{KCY2}/2 – 50		t_{KCY2}/2 – 50		ns
SIp setup time (to SCKp↑) Note 3	t_{SIK2}	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_{DD} ≤ 4.0 V		1/f_{MCK} + 20		1/f_{MCK} + 30		ns
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V		1/f_{MCK} + 20		1/f_{MCK} + 30		ns
		1.8 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_{DD} ≤ 2.0 V Note 2		1/f_{MCK} + 30		1/f_{MCK} + 30		ns
SIp hold time (from SCKp↑) Note 4	t_{KSI2}			1/f_{MCK} + 31		1/f_{MCK} + 31		ns
Delay time from SCKp↓ to SOp output Note 5	t_{KSO2}	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 30 pF, R_b = 1.4 kΩ			2/f_{MCK} + 120		2/f_{MCK} + 573	ns
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ			2/f_{MCK} + 214		2/f_{MCK} + 573	ns
		1.8 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 2, C_b = 30 pF, R_b = 5.5 kΩ			2/f_{MCK} + 573		2/f_{MCK} + 573	ns

Notes 1. Transfer rate in the SNOOZE mode: MAX. 1 Mbps

2. Use it with V_{DD} ≥ V_b.

3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes “to SCKp↓” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

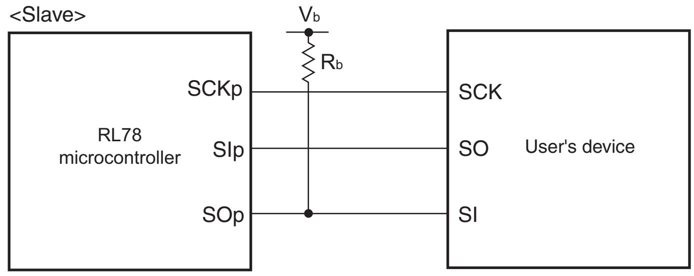
4. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes “from SCKp↓” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

5. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes “from SCKp↑” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Cautions 1. Select the TTL input buffer for the SIp and SCKp pins and the N-ch open drain output (V_{DD} tolerance) mode for the SOp pin by using port input mode register 1 (PIM1) and port output mode register 1 (POM1). **For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.**

2. CSI01 and CSI11 cannot communicate at different potential.

CSI mode connection diagram (during communication at different potential)

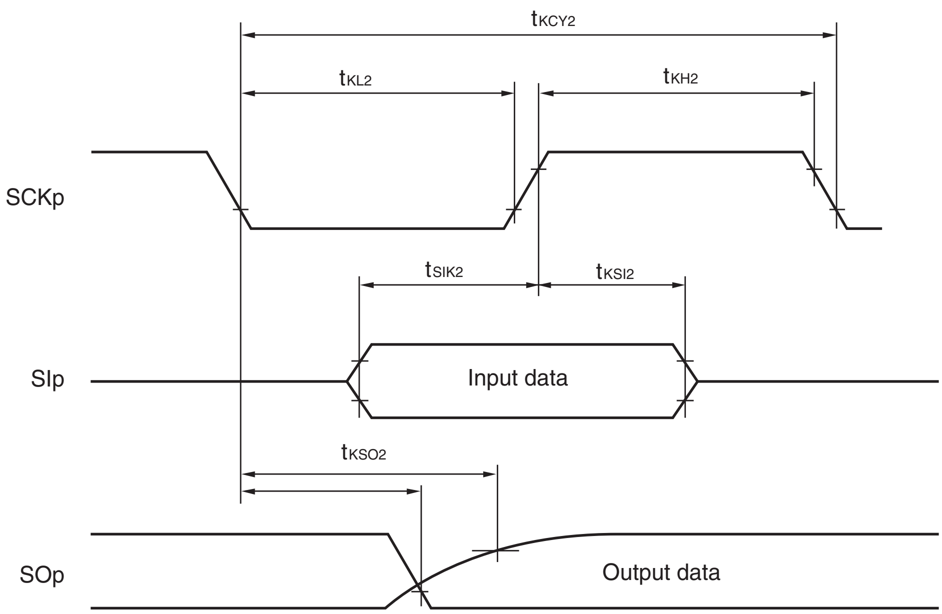


Remarks 1. R_b [Ω]: Communication line (SOp) pull-up resistance, C_b [F]: Communication line (SOp) load capacitance, V_b [V]: Communication line voltage

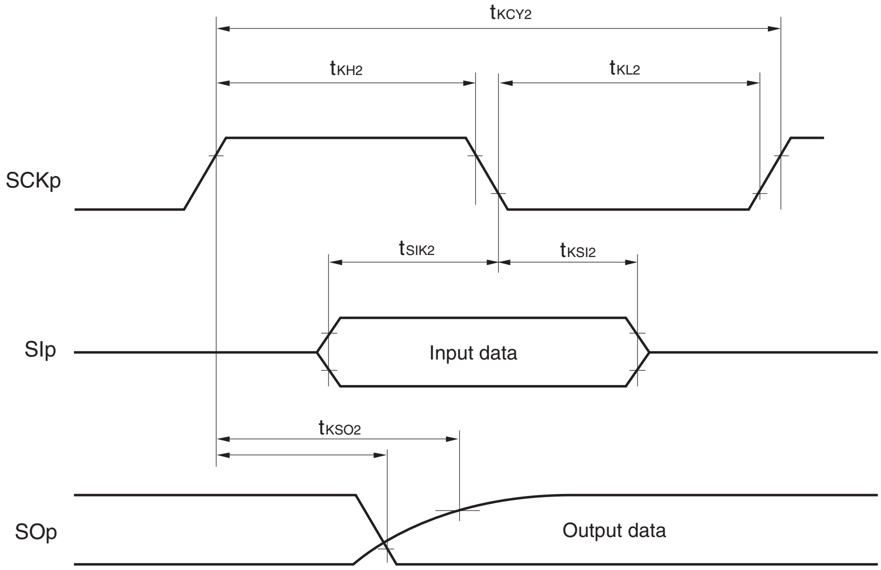
2. p: CSI number (p = 00, 20), m: Unit number (m = 0, 1), n: Channel number (n = 0)

3. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the serial clock select register m (SPSm) and the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00, 10))

CSI mode serial transfer timing (slave mode) (during communication at different potential)
(When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



CSI mode serial transfer timing (slave mode) (during communication at different potential)
(When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



Remark p: CSI number (p = 00, 20), m: Unit number (m = 0, 1), n: Channel number (n = 0)

(10) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified I²C mode)
(T_A = –40 to +85°C, 1.8 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

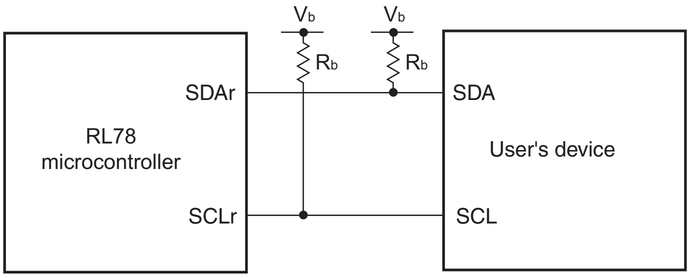
Parameter	Symbol	Conditions	HS (high-speed main) Mode		LS (low-speed main) Mode		Unit
			MIN.	MAX.	MIN.	MAX.	
SCLr clock frequency	f_{SCL}	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 100 pF, R_b = 2.8 kΩ		400 Note1		300 Note1	kHz
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 100 pF, R_b = 2.7 kΩ		400 Note1		300 Note1	kHz
		1.8 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V, Note2 C_b = 100 pF, R_b = 5.5 kΩ		300 Note1		300 Note1	kHz
Hold time when SCLr = "L"	t_{LOW}	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 100 pF, R_b = 2.8 kΩ	1150		1550		ns
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 100 pF, R_b = 2.7 kΩ	1150		1550		ns
		1.8 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V, Note2 C_b = 100 pF, R_b = 5.5 kΩ	1550		1550		ns
Hold time when SCLr = "H"	t_{HIGH}	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 100 pF, R_b = 2.8 kΩ	675		610		ns
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 100 pF, R_b = 2.7 kΩ	600		610		ns
		1.8 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V, Note2 C_b = 100 pF, R_b = 5.5 kΩ	610		610		ns
Data setup time (reception)	$t_{SU:DAT}$	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 100 pF, R_b = 2.8 kΩ	1/f_{MCK} + 190 Note3		1/f_{MCK} + 190 Note3		ns
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 100 pF, R_b = 2.7 kΩ	1/f_{MCK} + 190 Note3		1/f_{MCK} + 190 Note3		ns
		1.8 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V, Note2 C_b = 100 pF, R_b = 5.5 kΩ	1/f_{MCK} + 190 Note3		1/f_{MCK} + 190 Note3		ns
Data hold time (transmission)	$t_{HD:DAT}$	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 100 pF, R_b = 2.8 kΩ	0	355	0	355	ns
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 100 pF, R_b = 2.7 kΩ	0	355	0	355	ns
		1.8 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V, Note2 C_b = 100 pF, R_b = 5.5 kΩ	0	405	0	405	ns

Notes 1. The value must also be equal to or less than f_{MCK}/4.
2. Use it with V_{DD} ≥ V_b.
3. Set $t_{SU:DAT}$ so that it will not exceed the hold time when SCLr = "L" or SCLr = "H".

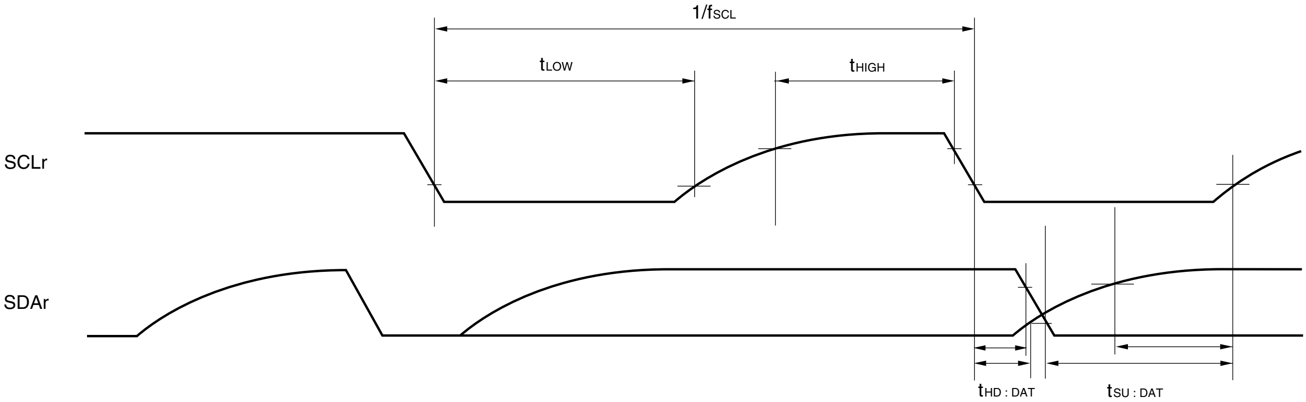
Cautions 1. Select the TTL input buffer and the N-ch open drain output (V_{DD} tolerance) mode for the SDAr pin and the N-ch open drain output (V_{DD} tolerance) mode for the SCLr pin by using port input mode register 1 (PIM1) and port output mode register 1 (POM1). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.
2. IIC01 and IIC11 cannot communicate at different potential.

(**Remarks** are listed on the next page.)

Simplified I²C mode connection diagram (during communication at different potential)



Simplified I²C mode serial transfer timing (during communication at different potential)



Remarks 1. R_b [Ω]: Communication line (SDAr, SCLr) pull-up resistance, C_b [F]: Communication line (SDAr, SCLr) load capacitance, V_b [V]: Communication line voltage

2. r: IIC Number (r = 00, 20)

3. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the serial clock select register m (SPSm) and the CKSmn bit of serial mode register mn (SMRmn).
m: Unit number (m = 0,1), n: Channel number (n = 0))

4. Simplified I²C mode is supported only by the R5F102 products.

2.5.2 Serial interface IICA

(T_A = –40 to +85°C, 1.8 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions	HS (high-speed main) mode LS (low-speed main) mode				Unit
			Standard Mode		Fast Mode		
			MIN.	MAX.	MIN.	MAX.	
SCLA0 clock frequency	f_{SCL}	Fast mode: f_{CLK} ≥ 3.5 MHz			0	400	kHz
		Normal mode: f_{CLK} ≥ 1 MHz	0	100			kHz
Setup time of restart condition	$t_{SU:STA}$		4.7		0.6		μs
Hold time[Note 1]	$t_{HD:STA}$		4.0		0.6		μs
Hold time when SCLA0 = "L"	t_{LOW}		4.7		1.3		μs
Hold time when SCLA0 = "H"	t_{HIGH}		4.0		0.6		μs
Data setup time (reception)	$t_{SU:DAT}$		250		100		ns
Data hold time (transmission)[Note 2]	$t_{HD:DAT}$		0	3.45	0	0.9	μs
Setup time of stop condition	$t_{SU:STO}$		4.0		0.6		μs
Bus-free time	t_{BUF}		4.7		1.3		μs

Notes 1. The first clock pulse is generated after this period when the start/restart condition is detected.

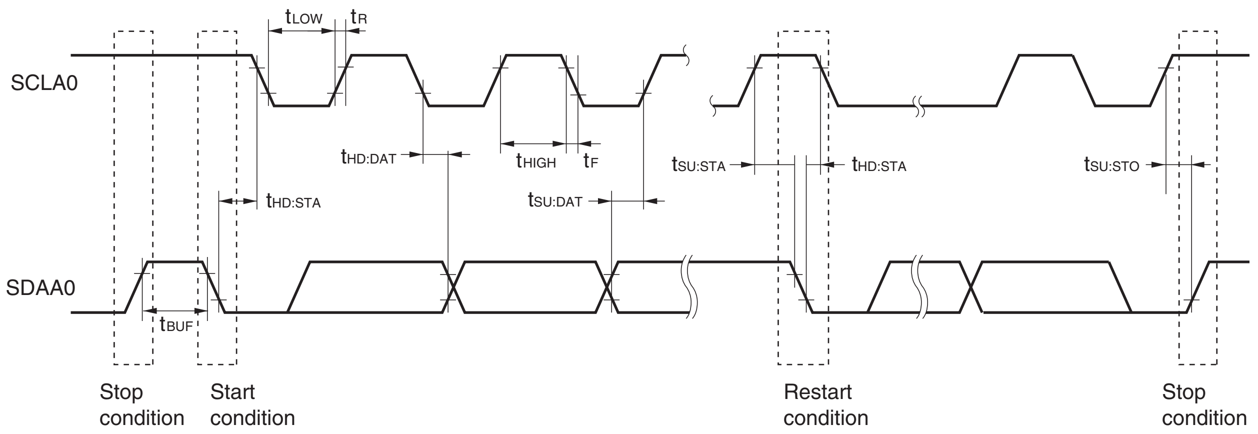
<R> **2.** The maximum value (MAX.) of $t_{HD:DAT}$ is during normal transfer and a wait state is inserted in the ACK (acknowledge) timing.

Caution Only in the 30-pin products, the values in the above table are applied even when bit 2 (PIOR2) in the peripheral I/O redirection register (PIOR) is 1. At this time, the pin characteristics (I_{OH1}, I_{OL1}, V_{OH1}, V_{OL1}) must satisfy the values in the redirect destination.

Remark The maximum value of C_b (communication line capacitance) and the value of R_b (communication line pull-up resistor) at that time in each mode are as follows.

Normal mode: C_b = 400 pF, Rb = 2.7 kΩ
Fast mode: C_b = 320 pF, Rb = 1.1 kΩ

IICA serial transfer timing



2.6 Analog Characteristics

2.6.1 A/D converter characteristics

Classification of A/D converter characteristics

Input channel	Reference Voltage		
	Reference voltage (+) = AV_{REFP} Reference voltage (–) = AV_{REFM}	Reference voltage (+) = V_{DD} Reference voltage (–) = V_{SS}	Reference voltage (+) = V_{BGR} Reference voltage (–) = AV_{REFM}
ANI0 to ANI3	Refer to **28.6.1 (1)**.	Refer to **28.6.1 (3)**.	Refer to **28.6.1 (4)**.
ANI16 to ANI22	Refer to **28.6.1 (2)**.		
Internal reference voltage Temperature sensor output voltage	Refer to **28.6.1 (1)**.		–

(1) When reference voltage (+) = AV_{REFP}/ANI0 (ADREFP1 = 0, ADREFP0 = 1), reference voltage (–) = AV_{REFM}/ANI1 (ADREFM = 1), target pin: ANI2, ANI3, internal reference voltage, and temperature sensor output voltage

(T_A = –40 to +85°C, 1.8 V ≤ AV_{REFP} ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V, Reference voltage (+) = AV_{REFP}, Reference voltage (–) = AV_{REFM} = 0 V)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error[Note 1]	AINL	10-bit resolution			1.2	±3.5	LSB
		AV_{REFP} = V_{DD} [Note 3]			1.2	±7.0 [Note 4]	LSB
Conversion time	t_{CONV}	10-bit resolution Target pin: ANI2, ANI3	3.6 V ≤ V_{DD} ≤ 5.5 V	2.125		39	μs
			2.7 V ≤ V_{DD} ≤ 5.5 V	3.1875		39	μs
			1.8 V ≤ V_{DD} ≤ 5.5 V	17		39	μs
				57		95	μs
		10-bit resolution Target pin: Internal reference voltage, and temperature sensor output voltage (HS (high-speed main) mode)	3.6 V ≤ V_{DD} ≤ 5.5 V	2.375		39	μs
			2.7 V ≤ V_{DD} ≤ 5.5 V	3.5625		39	μs
			2.4 V ≤ V_{DD} ≤ 5.5 V	17		39	μs
Zero-scale error[Notes 1, 2]	EZS	10-bit resolution				±0.25	%FSR
		AV_{REFP} = V_{DD} [Note 3]				±0.50 [Note 4]	%FSR
Full-scale error[Notes 1, 2]	EFS	10-bit resolution				±0.25	%FSR
		AV_{REFP} = V_{DD} [Note 3]				±0.50 [Note 4]	%FSR
Integral linearity error[Note 1]	ILE	10-bit resolution				±2.5	LSB
		AV_{REFP} = V_{DD} [Note 3]				±5.0 [Note 4]	LSB
Differential linearity error [Note 1]	DLE	10-bit resolution				±1.5	LSB
		AV_{REFP} = V_{DD} [Note 3]				±2.0 [Note 4]	LSB
Analog input voltage	V_{AIN}	ANI2, ANI3		0		AV_{REFP}	V
		Internal reference voltage (2.4 V ≤ V_{DD} ≤ 5.5 V, HS (high-speed main) mode)		V_{BGR} [Note 5]			V
		Temperature sensor output voltage (2.4 V ≤ V_{DD} ≤ 5.5 V, HS (high-speed main) mode)		V_{TMPS25} [Note 5]			V

(**Notes** are listed on the next page.)

Notes 1. Excludes quantization error (±1/2 LSB).

2. This value is indicated as a ratio (%FSR) to the full-scale value.

3. When $AV_{REFP} < V_{DD}$, the MAX. values are as follows.

Overall error: Add ±1.0 LSB to the MAX. value when $AV_{REFP} = V_{DD}$.

Zero-scale error/Full-scale error: Add ±0.05%FSR to the MAX. value when $AV_{REFP} = V_{DD}$.

Integral linearity error/ Differential linearity error: Add ±0.5 LSB to the MAX. value when $AV_{REFP} = V_{DD}$.

4. Values when the conversion time is set to 57 μs (min.) and 95 μs (max.).

5. Refer to **28.6.2 Temperature sensor/internal reference voltage characteristics**.

(2) When reference voltage (+) = AV_{REFP}/ANI0 (ADREFP1 = 0, ADREFP0 = 1), reference voltage (–) = AV_{REFM}/ANI1 (ADREFM = 1), target pin: ANI16 to ANI22

(T_A = –40 to +85°C, 1.8 V ≤ AV_{REFP} ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V, Reference voltage (+) = AV_{REFP}, Reference voltage (–) = AV_{REFM} = 0 V)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	R_{ES}			8		10	bit
Overall error [Note 1]	AINL	10-bit resolution			1.2	±5.0	LSB
		$AV_{REFP} = V_{DD}$ [Note 3]			1.2	±8.5 [Note 4]	LSB
Conversion time	t_{CONV}	10-bit resolution Target ANI pin: ANI16 to ANI22	3.6 V ≤ V_{DD} ≤ 5.5 V	2.125		39	μs
			2.7 V ≤ V_{DD} ≤ 5.5 V	3.1875		39	μs
			1.8 V ≤ V_{DD} ≤ 5.5 V	17		39	μs
				57		95	μs
Zero-scale error [Notes 1, 2]	EZS	10-bit resolution				±0.35	%FSR
		$AV_{REFP} = V_{DD}$ [Note 3]				±0.60 [Note 4]	%FSR
Full-scale error [Notes 1, 2]	EFS	10-bit resolution				±0.35	%FSR
		$AV_{REFP} = V_{DD}$ [Note 3]				±0.60 [Note 4]	%FSR
Integral linearity error [Note 1]	ILE	10-bit resolution				±3.5	LSB
		$AV_{REFP} = V_{DD}$ [Note 3]				±6.0 [Note 4]	LSB
Differential linearity error [Note 1]	DLE	10-bit resolution				±2.0	LSB
		$AV_{REFP} = V_{DD}$ [Note 3]				±2.5 [Note 4]	LSB
Analog input voltage	V_{AIN}	ANI16 to ANI22		0		AV_{REFP} and V_{DD}	V

Notes 1. Excludes quantization error (±1/2 LSB).

2. This value is indicated as a ratio (%FSR) to the full-scale value.

3. When $AV_{REFP} \leq V_{DD}$, the MAX. values are as follows.

Overall error: Add ±4.0 LSB to the MAX. value when $AV_{REFP} = V_{DD}$.

Zero-scale error/Full-scale error: Add ±0.20%FSR to the MAX. value when $AV_{REFP} = V_{DD}$.

Integral linearity error/ Differential linearity error: Add ±2.0 LSB to the MAX. value when $AV_{REFP} = V_{DD}$.

4. When the conversion time is set to 57 μs (min.) and 95 μs (max.).

(3) When reference voltage (+) = V_{DD} (ADREFP1 = 0, ADREFP0 = 0), reference voltage (–) = V_{SS} (ADREFM = 0), target pin: ANI0 to ANI3, ANI16 to ANI22, internal reference voltage, and temperature sensor output voltage

(T_A = –40 to +85°C, 1.8 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V, Reference voltage (+) = V_{DD}, Reference voltage (–) = V_{SS})

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	R_{ES}			8		10	bit
Overall error[Note 1]	AINL	10-bit resolution			1.2	±7.0	LSB
					1.2	±10.5 [Note 3]	LSB
Conversion time	t_{CONV}	10-bit resolution Target pin: ANI0 to ANI3, ANI16 to ANI22	3.6 V ≤ V_{DD} ≤ 5.5 V	2.125		39	μs
			2.7 V ≤ V_{DD} ≤ 5.5 V	3.1875		39	μs
			1.8 V ≤ V_{DD} ≤ 5.5 V	17		39	μs
				57		95	μs
Conversion time	t_{CONV}	10-bit resolution Target pin: internal reference voltage, and temperature sensor output voltage (HS (high-speed main) mode)	3.6 V ≤ V_{DD} ≤ 5.5 V	2.375		39	μs
			2.7 V ≤ V_{DD} ≤ 5.5 V	3.5625		39	μs
			2.4 V ≤ V_{DD} ≤ 5.5 V	17		39	μs
Zero-scale error[Notes 1, 2]	EZS	10-bit resolution				±0.60	%FSR
						±0.85 [Note 3]	%FSR
Full-scale error[Notes 1, 2]	EFS	10-bit resolution				±0.60	%FSR
						±0.85 [Note 3]	%FSR
Integral linearity error[Note 1]	ILE	10-bit resolution				±4.0	LSB
						±6.5 [Note 3]	LSB
Differential linearity error[Note 1]	DLE	10-bit resolution				±2.0	LSB
						±2.5 [Note 3]	LSB
Analog input voltage	V_{AIN}	ANI0 to ANI3, ANI16 to ANI22		0		V_{DD}	V
		Internal reference voltage (2.4 V ≤ V_{DD} ≤ 5.5 V, HS (high-speed main) mode)		V_{BGR} [Note 4]			V
		Temperature sensor output voltage (2.4 V ≤ V_{DD} ≤ 5.5 V, HS (high-speed main) mode)		V_{TMPS25} [Note 4]			V

Notes 1. Excludes quantization error (±1/2 LSB).

2. This value is indicated as a ratio (%FSR) to the full-scale value.

3. When the conversion time is set to 57 μs (min.) and 95 μs (max.).

4. Refer to **28.6.2 Temperature sensor/internal reference voltage characteristics**.

(4) When reference voltage (+) = Internal reference voltage (ADREFP1 = 1, ADREFP0 = 0), reference voltage (–) = AV_{REFM} (ADREFM = 1), target pin: ANI0, ANI2, ANI3, and ANI16 to ANI22

(T_A = –40 to +85°C, 2.4 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V, Reference voltage (+) = V_{BGR} [Note 3], Reference voltage (–) = AV_{REFM} [Note 4] = 0 V, HS (high-speed main) mode)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Resolution	R_{ES}			8		bit
Conversion time	t_{CONV}	8-bit resolution	17		39	μs
Zero-scale error [Notes 1, 2]	EZS	8-bit resolution			±0.60	%FSR
Integral linearity error [Note 1]	ILE	8-bit resolution			±2.0	LSB
Differential linearity error [Note 1]	DLE	8-bit resolution			±1.0	LSB
Analog input voltage	V_{AIN}		0		V_{BGR} [Note 3]	V

Notes 1. Excludes quantization error (±1/2 LSB).

2. This value is indicated as a ratio (%FSR) to the full-scale value.

3. Refer to **28.6.2 Temperature sensor/internal reference voltage characteristics**.

4. When reference voltage (–) = V_{SS}, the MAX. values are as follows.
Zero-scale error: Add ±0.35%FSR to the MAX. value when reference voltage (–) = AV_{REFM}.
Integral linearity error: Add ±0.5 LSB to the MAX. value when reference voltage (–) = AV_{REFM}.
Differential linearity error: Add ±0.2 LSB to the MAX. value when reference voltage (–) = AV_{REFM}.

2.6.2 Temperature sensor/internal reference voltage characteristics

(T_A = –40 to +85°C, 2.4 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V, HS (high-speed main) mode

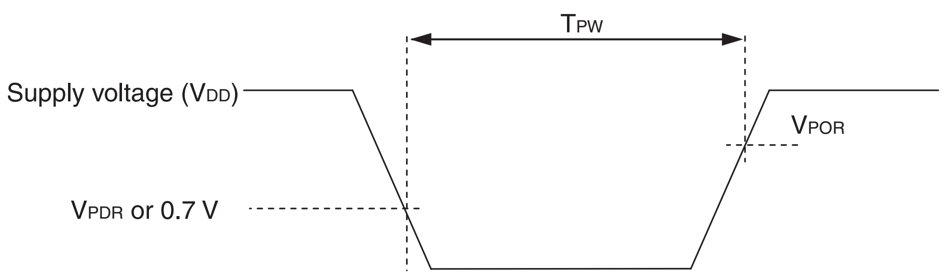
Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Temperature sensor output voltage	V_{TMPS25}	Setting ADS register = 80H, T_A = +25°C		1.05		V
Internal reference voltage	V_{BGR}	Setting ADS register = 81H	1.38	1.45	1.50	V
Temperature coefficient	F_{VTMPS}	Temperature sensor output voltage that depends on the temperature		–3.6		mV/°C
Operation stabilization wait time	t_{AMP}		5			μs

2.6.3 POR circuit characteristics

(T_A = –40 to +85°C, V_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Detection voltage	V_{POR}	Power supply rise time	1.47	1.51	1.55	V
	V_{PDR}	Power supply fall time	1.46	1.50	1.54	V
Minimum pulse width Note	T_{PW}		300			μs

Note Minimum time required for a POR reset when V_{DD} exceeds below V_{PDR}. This is also the minimum time required for a POR reset from when V_{DD} exceeds below 0.7 V to when V_{DD} exceeds V_{POR} while STOP mode is entered or the main system clock is stopped through setting bit 0 (HIOSTOP) and bit 7 (MSTOP) in the clock operation status control register (CSC).



2.6.4 LVD circuit characteristics

LVD Detection Voltage of Reset Mode and Interrupt Mode
(T_A = –40 to +85°C, $V_{PDR} \leq V_{DD} \leq$ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Detection supply voltage	V_{LVD0}	Power supply rise time	3.98	4.06	4.14	V
		Power supply fall time	3.90	3.98	4.06	V
	V_{LVD1}	Power supply rise time	3.68	3.75	3.82	V
		Power supply fall time	3.60	3.67	3.74	V
	V_{LVD2}	Power supply rise time	3.07	3.13	3.19	V
		Power supply fall time	3.00	3.06	3.12	V
	V_{LVD3}	Power supply rise time	2.96	3.02	3.08	V
		Power supply fall time	2.90	2.96	3.02	V
	V_{LVD4}	Power supply rise time	2.86	2.92	2.97	V
		Power supply fall time	2.80	2.86	2.91	V
	V_{LVD5}	Power supply rise time	2.76	2.81	2.87	V
		Power supply fall time	2.70	2.75	2.81	V
	V_{LVD6}	Power supply rise time	2.66	2.71	2.76	V
		Power supply fall time	2.60	2.65	2.70	V
	V_{LVD7}	Power supply rise time	2.56	2.61	2.66	V
		Power supply fall time	2.50	2.55	2.60	V
	V_{LVD8}	Power supply rise time	2.45	2.50	2.55	V
		Power supply fall time	2.40	2.45	2.50	V
	V_{LVD9}	Power supply rise time	2.05	2.09	2.13	V
		Power supply fall time	2.00	2.04	2.08	V
	V_{LVD10}	Power supply rise time	1.94	1.98	2.02	V
		Power supply fall time	1.90	1.94	1.98	V
	V_{LVD11}	Power supply rise time	1.84	1.88	1.91	V
		Power supply fall time	1.80	1.84	1.87	V
Minimum pulse width	t_{LW}		300			μs
Detection delay time					300	μs

LVD detection voltage of interrupt & reset mode
(T_A = –40 to +85°C, $V_{PDR} \leq V_{DD} \leq$ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions			MIN.	TYP.	MAX.	Unit
Interrupt and reset mode	V_{LVDB0}	V_{POC2}, V_{POC1}, V_{POC0} = 0, 0, 1, falling reset voltage			1.80	1.84	1.87	V
	V_{LVDB1}		LVIS1, LVIS0 = 1, 0	Rising reset release voltage	1.94	1.98	2.02	V
				Falling interrupt voltage	1.90	1.94	1.98	V
	V_{LVDB2}		LVIS1, LVIS0 = 0, 1	Rising reset release voltage	2.05	2.09	2.13	V
				Falling interrupt voltage	2.00	2.04	2.08	V
	V_{LVDB3}		LVIS1, LVIS0 = 0, 0	Rising reset release voltage	3.07	3.13	3.19	V
				Falling interrupt voltage	3.00	3.06	3.12	V
	V_{LVDC0}	V_{POC2}, V_{POC1}, V_{POC0} = 0, 1, 0, falling reset voltage			2.40	2.45	2.50	V
	V_{LVDC1}		LVIS1, LVIS0 = 1, 0	Rising reset release voltage	2.56	2.61	2.66	V
				Falling interrupt voltage	2.50	2.55	2.60	V
	V_{LVDC2}		LVIS1, LVIS0 = 0, 1	Rising reset release voltage	2.66	2.71	2.76	V
				Falling interrupt voltage	2.60	2.65	2.70	V
	V_{LVDC3}		LVIS1, LVIS0 = 0, 0	Rising reset release voltage	3.68	3.75	3.82	V
				Falling interrupt voltage	3.60	3.67	3.74	V
	V_{LVDD0}	V_{POC2}, V_{POC1}, V_{POC1} = 0, 1, 1, falling reset voltage			2.70	2.75	2.81	V
	V_{LVDD1}		LVIS1, LVIS0 = 1, 0	Rising reset release voltage	2.86	2.92	2.97	V
				Falling interrupt voltage	2.80	2.86	2.91	V
	V_{LVDD2}		LVIS1, LVIS0 = 0, 1	Rising reset release voltage	2.96	3.02	3.08	V
				Falling interrupt voltage	2.90	2.96	3.02	V
	V_{LVDD3}		LVIS1, LVIS0 = 0, 0	Rising reset release voltage	3.98	4.06	4.14	V
				Falling interrupt voltage	3.90	3.98	4.06	V

2.6.5 Power supply voltage rising slope characteristics

(T_A = –40 to +85°C, V_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Power supply voltage rising slope	S_{VDD}				54	V/ms

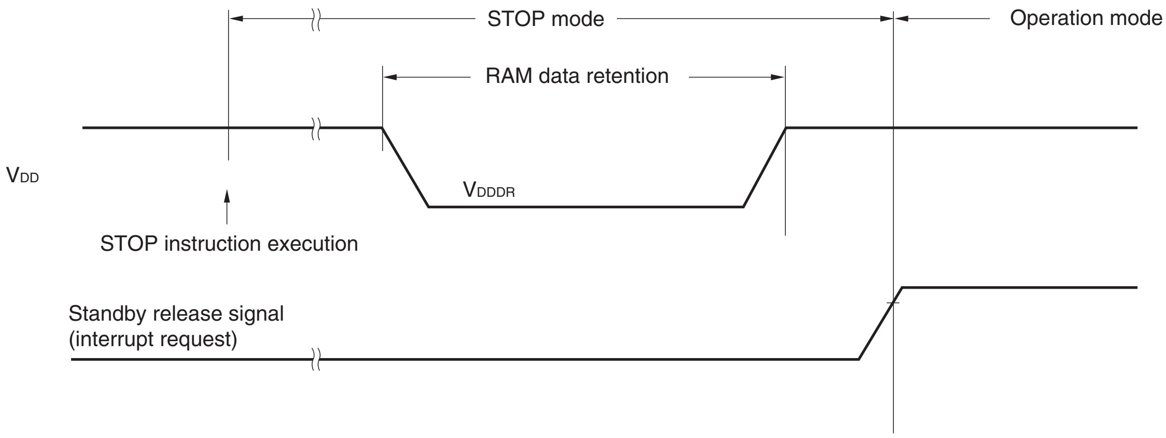
Caution Make sure to keep the internal reset state by the LVD circuit or an external reset until V_{DD} reaches the operating voltage range shown in 28.4 AC Characteristics.

<R> 2.7 Data Memory STOP Mode Low Supply Voltage Data Retention Characteristics

(T_A = –40 to +85°C, V_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Data retention supply voltage	V_{DDDR}		1.46 Note		5.5	V

<R> **Note** This depends on the POR detection voltage. For a falling voltage, data in RAM are retained until the voltage reaches the level that triggers a POR reset but not once it reaches the level at which a POR reset is generated.



2.8 Flash Memory Programming Characteristics

(T_A = –40 to +85°C, 1.8 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

<R>

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
System clock frequency	f_{CLK}		1		24	MHz
Code flash memory rewritable times Notes 1, 2, 3	C_{erwr}	Retained for 20 years T_A = 85°C	1,000			Times
Data flash memory rewritable times Notes 1, 2, 3		Retained for 1 year T_A = 25°C		1,000,000		
		Retained for 5 years T_A = 85°C	100,000			
		Retained for 20 years T_A = 85°C	10,000			

Notes 1. 1 erase + 1 write after the erase is regarded as 1 rewrite. The retaining years are until next rewrite after the rewrite.

2. When using flash memory programmer and Renesas Electronics self programming library

3. These are the characteristics of the flash memory and the results obtained from reliability testing by Renesas Electronics Corporation.

2.9 Dedicated Flash Memory Programmer Communication (UART)

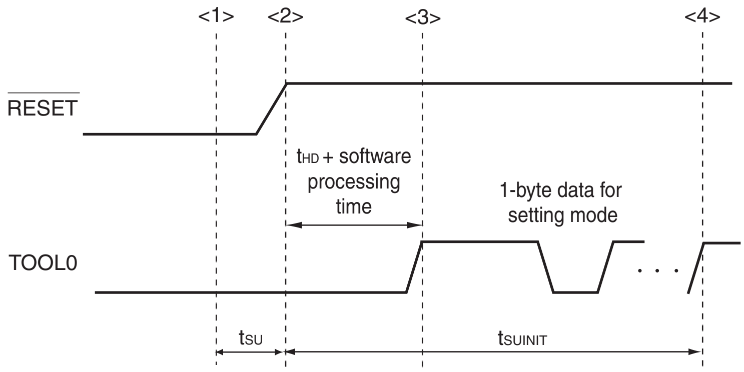
(T_A = –40 to +85°C, 1.8 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Transfer rate		During serial programming	115,200		1,000,000	bps

2.10 Timing of Entry to Flash Memory Programming Modes

(T_A = –40 to +85°C, 1.8 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Time to complete the communication for the initial setting after the external reset is released	t_{SUINIT}	POR and LVD reset are released before external reset release			100	ms
Time to release the external reset after the TOOL0 pin is set to the low level	t_{SU}	POR and LVD reset are released before external reset release	10			μs
Time to hold the TOOL0 pin at the low level after the external reset is released (excluding the processing time of the firmware to control the flash memory)	t_{HD}	POR and LVD reset are released before external reset release	1			ms



<1> The low level is input to the TOOL0 pin.

<2> The external reset is released (POR and LVD reset must be released before the external reset is released.).

<3> The TOOL0 pin is set to the high level.

<4> Setting of the flash memory programming mode by UART reception and complete the baud rate setting.

Remark t_{SUINIT}: Communication for the initial setting must be completed within 100 ms after the external reset is released during this period.

t_{SU}: Time to release the external reset after the TOOL0 pin is set to the low level

t_{HD}: Time to hold the TOOL0 pin at the low level after the external reset is released (excluding the processing time of the firmware to control the flash memory)

<R> 3. ELECTRICAL SPECIFICATIONS (G: INDUSTRIAL APPLICATIONS T_A = –40 to +105°C)

<R> This chapter describes the following electrical specifications.

Target products G: Industrial applications T_A = -40 to +105°C

<R> R5F102xxGxx

Cautions 1. The RL78 microcontrollers have an on-chip debug function, which is provided for development and evaluation. Do not use the on-chip debug function in products designated for mass production, because the guaranteed number of rewritable times of the flash memory may be exceeded when this function is used, and product reliability therefore cannot be guaranteed. Renesas Electronics is not liable for problems occurring when the on-chip debug function is used.

2. The pins mounted depend on the product. Refer to 2.1 Port Functions to 2.2.1 Functions for each product.

3. Please contact Renesas Electronics sales office for derating of operation under T_A = +85°C to +105°C. Derating is the systematic reduction of load for the sake of improved reliability.

Remark When the RL78 microcontroller is used in the range of T_A = -40 to +85 °C, see CHAPTER 28
<R> **ELECTRICAL SPECIFICATIONS (A: T_A = -40 to +85 °C).**

There are following differences between the products "G: Industrial applications (T_A = -40 to +105°C)" and the products "A: Consumer applications, and D: Industrial applications".

Parameter	Application	
	A: Consumer applications, D: Industrial applications	G: Industrial applications
Operating ambient temperature	T_A = -40 to +85°C	T_A = -40 to +105°C
Operating mode Operating voltage range	HS (high-speed main) mode: 2.7 V ≤ V_{DD} ≤ 5.5 V@1 MHz to 24 MHz 2.4 V ≤ V_{DD} ≤ 5.5 V@1 MHz to 16 MHz LS (low-speed main) mode: 1.8 V ≤ V_{DD} ≤ 5.5 V@1 MHz to 8 MHz	HS (high-speed main) mode only: 2.7 V ≤ V_{DD} ≤ 5.5 V@1 MHz to 24 MHz 2.4 V ≤ V_{DD} ≤ 5.5 V@1 MHz to 16 MHz
High-speed on-chip oscillator clock accuracy	R5F102 products, 1.8 V ≤ V_{DD} ≤ 5.5 V: ±1.0%@ T_A = -20 to +85°C ±1.5%@ T_A = -40 to -20°C R5F103 products, 1.8 V ≤ V_{DD} ≤ 5.5 V: ±5.0%@ T_A = -40 to +85°C	R5F102 products, 2.4 V ≤ V_{DD} ≤ 5.5 V: ±2.0%@ T_A = +85 to +105°C ±1.0%@ T_A = -20 to +85°C ±1.5%@ T_A = -40 to -20°C
Serial array unit	UART CSI: f_{CLK}/2 (supporting 12 Mbps), f_{CLK}/4 Simplified I^2C communication	UART CSI: f_{CLK}/4 Simplified I^2C communication
Voltage detector	Rise detection voltage: 1.88 V to 4.06 V (12 levels) Fall detection voltage: 1.84 V to 3.98 V (12 levels)	Rise detection voltage: 2.61 V to 4.06 V (8 levels) Fall detection voltage: 2.55 V to 3.98 V (8 levels)

Remark The electrical characteristics of the products G: Industrial applications (T_A = -40 to +105°C) are different from those of the products "A: Consumer applications, and D: Industrial applications". For details, refer to **29.1** to **29.10**.

3.1 Absolute Maximum Ratings

Absolute Maximum Ratings (T_A = 25°C)

Parameter	Symbols	Conditions		Ratings	Unit
Supply Voltage	V_{DD}			–0.5 to + 6.5	V
REGC terminal input voltage[Note1]	V_{IREGC}	REGC		–0.3 to +2.8 and –0.3 to V_{DD} + 0.3 [Note 2]	V
Input Voltage	V_{I1}	Other than P60, P61		–0.3 to V_{DD} + 0.3[Note 3]	V
	V_{I2}	P60, P61 (N-ch open drain)		–0.3 to 6.5	V
Output Voltage	V_O			–0.3 to V_{DD} + 0.3[Note 3]	V
Analog input voltage	V_{AI}	20, 24-pin products: ANI0 to ANI3, ANI16 to ANI22 30-pin products: ANI0 to ANI3, ANI16 to ANI19		–0.3 to V_{DD} + 0.3 and –0.3 to AVREF(+)+0.3 [Notes 3, 4]	V
Output current, high	I_{OH1}	Per pin	Other than P20 to P23	–40	mA
		Total of all pins	All the terminals other than P20 to P23	–170	mA
			20-, 24-pin products: P40 to P42 30-pin products: P00, P01, P40, P120	–70	mA
			20-, 24-pin products: P00 to P03[Note 5], P10 to P14 30-pin products: P10 to P17, P30, P31, P50, P51, P147	–100	mA
	I_{OH2}	Per pin	P20 to P23	–0.5	mA
		Total of all pins		–2	mA
Output current, low	I_{OL1}	Per pin	Other than P20 to P23	40	mA
		Total of all pins	All the terminals other than P20 to P23	170	mA
			20-, 24-pin products: P40 to P42 30-pin products: P00, P01, P40, P120	70	mA
			20-, 24-pin products: P00 to P03 [Note 5], P10 to P14, P60, P61 30-pin products: P10 to P17, P30, P31, P50, P51, P60, P61, P147	100	mA
	I_{OL2}	Per pin	P20 to P23	1	mA
		Total of all pins		5	mA
Operating ambient temperature	T_A			–40 to +105	°C
Storage temperature	T_{stg}			–65 to +150	°C

Notes 1. 30-pin product only.

2. Connect the REGC pin to V_{SS} via a capacitor (0.47 to 1 μF). This value determines the absolute maximum rating of the REGC pin. Do not use it with voltage applied.

3. Must be 6.5 V or lower.

4. Do not exceed $AV_{REF}(+)$ + 0.3 V in case of A/D conversion target pin.

5. 24-pin products only.

Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.

Remarks 1. Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

2. $AV_{REF}(+)$: + side reference voltage of the A/D converter.

3. V_{SS} : Reference voltage

3.2 Oscillator Characteristics

3.2.1 X1 oscillator characteristics

(T_A = –40 to +105°C, 2.4 V ≤ V_{DD} ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Resonator	Conditions	MIN.	TYP.	MAX.	Unit
X1 clock oscillation frequency (f_X)[Note]	Ceramic resonator / crystal oscillator	2.7 V ≤ V_{DD} ≤ 5.5 V	1.0		20.0	MHz
		2.4 V ≤ V_{DD} < 2.7 V	1.0		8.0	

Note Indicates only permissible oscillator frequency ranges. Refer to AC Characteristics for instruction execution time. Request evaluation by the manufacturer of the oscillator circuit mounted on a board to check the oscillator characteristics.

Caution Since the CPU is started by the high-speed on-chip oscillator clock after a reset release, check the X1 clock oscillation stabilization time using the oscillation stabilization time counter status register (OSTC) by the user. Determine the oscillation stabilization time of the OSTC register and the oscillation stabilization time select register (OSTS) after sufficiently evaluating the oscillation stabilization time with the resonator to be used.

Remark When using the X1 oscillator, refer to **5.4 System Clock Oscillator**.

3.2.2 On-chip oscillator characteristics

(T_A = –40 to +105°C, 2.4 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Oscillators	Parameters	Conditions		MIN.	TYP.	MAX.	Unit
High-speed on-chip oscillator clock frequency [Notes 1, 2]	f_{IH}			1		24	MHz
High-speed on-chip oscillator clock frequency accuracy		R5F102 products	T_A = –20 to +85°C	-1.0		+1.0	%
			T_A = –40 to –20°C	-1.5		+1.5	%
			T_A = +85 to +105°C	-2.0		+2.0	%
Low-speed on-chip oscillator clock frequency	f_{IL}				15		kHz
Low-speed on-chip oscillator clock frequency accuracy				-15		+15	%

Notes 1. High-speed on-chip oscillator frequency is selected by bits 0 to 3 of option byte (000C2H) and bits 0 to 2 of HOCODIV register.

2. This only indicates the oscillator characteristics. Refer to AC Characteristics for instruction execution time.

3.3 DC Characteristics

3.3.1 Pin characteristics

(T_A = –40 to +105°C, 2.4 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V) **(1/4)**

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current, high[Note 1]	I_{OH1}	20-, 24-pin products: Per pin for P00 to P03[Note 4], P10 to P14, P40 to P42 30-pin products: Per pin for P00, P01, P10 to P17, P30, P31, P40, P50, P51, P120, P147				–3.0 [Note 2]	mA
		20-, 24-pin products: Total of P40 to P42 30-pin products: Total of P00, P01, P40, P120 (When duty ≤ 70%[Note 3])	4.0 V ≤ V_{DD} ≤ 5.5 V			–9.0	mA
			2.7 V ≤ V_{DD} < 4.0 V			–6.0	mA
			2.4 V ≤ V_{DD} < 2.7 V			–4.5	mA
		20-, 24-pin products: Total of P00 to P03[Note 4], P10 to P14 30-pin products: Total of P10 to P17, P30, P31, P50, P51, P147 (When duty ≤ 70%[Note 3])	4.0 V ≤ V_{DD} ≤ 5.5 V			–27.0	mA
			2.7 V ≤ V_{DD} < 4.0 V			–18.0	mA
			2.4 V ≤ V_{DD} < 2.7 V			–10.0	mA
		Total of all pins (When duty ≤ 70%[Note 3])				–36.0	mA
	I_{OH2}	Per pin for P20 to P23				–0.1	mA
		Total of all pins				–0.4	mA

Notes 1. value of current at which the device operation is guaranteed even if the current flows from the V_{DD} pin to an output pin.

2. However, do not exceed the total current value.

3. The output current value under conditions where the duty factor ≤ 70%.

If duty factor > 70%: The output current value can be calculated with the following expression (where n represents the duty factor as a percentage).

- Total output current of pins = (I_{OH} × 0.7)/(n × 0.01)

<Example> Where n = 80% and I_{OH} = –10.0 mA

Total output current of pins = (–10.0 × 0.7)/(80 × 0.01) ≅ –8.7 mA

However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.

4. 24-pin products only.

Caution P10 to P12 and P41 for 20-pin products, P01, P10 to P12, and P41 for 24-pin products, and P00, P10 to P15, P17, and P50 for 30-pin products do not output high level in N-ch open-drain mode.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

(T_A = –40 to +105°C, 2.4 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V) **(2/4)**

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current, low[Note 1]	I_{OL1}	20-, 24-pin products: Per pin for P00 to P03[Note 4], P10 to P14, P40 to P42 30-pin products: Per pin for P00, P01, P10 to P17, P30, P31, P40, P50, P51, P120, P147				8.5 [Note 2]	mA
		Per pin for P60, P61				15.0 [Note 2]	mA
		20-, 24-pin products: Total of P40 to P42 30-pin products: Total of P00, P01, P40, P120 (When duty ≤ 70%[Note 3])	4.0 V ≤ V_{DD} ≤ 5.5 V			25.5	mA
			2.7 V ≤ V_{DD} < 4.0 V			9.0	mA
			2.4 V ≤ V_{DD} < 2.7 V			1.8	mA
		20-, 24-pin products: Total of P00 to P03[Note 4], P10 to P14, P60, P61 30-pin products: Total of P10 to P17, P30, P31, P50, P51, P60, P61, P147 (When duty ≤ 70%[Note 3])	4.0 V ≤ V_{DD} ≤ 5.5 V			40.0	mA
			2.7 V ≤ V_{DD} < 4.0 V			27.0	mA
			2.4 V ≤ V_{DD} < 2.7 V			5.4	mA
		Total of all pins (When duty ≤ 70%[Note 3])				65.5	mA
	I_{OL2}	Per pin for P20 to P23				0.4	mA
		Total of all pins				1.6	mA

Notes 1. Value of current at which the device operation is guaranteed even if the current flows from an output pin to the V_{SS} pin.

2. However, do not exceed the total current value.

3. The output current value under conditions where the duty factor ≤ 70%.

If duty factor > 70%: The output current value can be calculated with the following expression (where n represents the duty factor as a percentage).

- Total output current of pins = (I_{OL} × 0.7)/(n × 0.01)

<Example> Where n = 80% and I_{OL} = 10.0 mA

Total output current of pins = (10.0 × 0.7)/(80 × 0.01) ≅ 8.7 mA

However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.

4. 24-pin products only.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

(T_A = –40 to +105°C, 2.4 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V) **(3/4)**

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Input voltage, high	V_{IH1}	Normal input buffer 20-, 24-pin products: P00 to P03 [Note 2], P10 to P14, P40 to P42 30-pin products: P00, P01, P10 to P17, P30, P31, P40, P50, P51, P120, P147		0.8V_{DD}		V_{DD}	V
	V_{IH2}	TTL input buffer 20-, 24-pin products: P10, P11 30-pin products: P01, P10, P11, P13 to P17	4.0 V ≤ V_{DD} ≤ 5.5 V	2.2		V_{DD}	V
			3.3 V ≤ V_{DD} < 4.0 V	2.0		V_{DD}	V
			2.4 V ≤ V_{DD} < 3.3 V	1.5		V_{DD}	V
	V_{IH3}	Normal input buffer P20 to P23		0.7V_{DD}		V_{DD}	V
	V_{IH4}	P60, P61		0.7V_{DD}		6.0	V
	V_{IH5}	P121, P122, P125 [Note 1], P137, EXCLK, $\overline{\text{RESET}}$		0.8V_{DD}		V_{DD}	V
Input voltage, low	V_{IL1}	Normal input buffer 20-, 24-pin products: P00 to P03 [Note 2], P10 to P14, P40 to P42 30-pin products: P00, P01, P10 to P17, P30, P31, P40, P50, P51, P120, P147		0		0.2V_{DD}	V
	V_{IL2}	TTL input buffer 20-, 24-pin products: P10, P11 30-pin products: P01, P10, P11, P13 to P17	4.0 V ≤ V_{DD} ≤ 5.5 V	0		0.8	V
			3.3 V ≤ V_{DD} < 4.0 V	0		0.5	V
			2.4 V ≤ V_{DD} < 3.3 V	0		0.32	V
	V_{IL3}	P20 to P23		0		0.3V_{DD}	V
	V_{IL4}	P60, P61		0		0.3V_{DD}	V
	V_{IL5}	P121, P122, P125 [Note 1], P137, EXCLK, $\overline{\text{RESET}}$		0		0.2V_{DD}	V
Output voltage, high	V_{OH1}	20-, 24-pin products: P00 to P03 [Note 2], P10 to P14, P40 to P42 30-pin products: P00, P01, P10 to P17, P30, P31, P40, P50, P51, P120, P147	4.0 V ≤ V_{DD} ≤ 5.5 V, I_{OH1} = –3.0 mA	V_{DD}–0.7			V
			2.7 V ≤ V_{DD} ≤ 5.5 V, I_{OH1} = –2.0 mA	V_{DD}–0.6			V
			2.4 V ≤ V_{DD} ≤ 5.5 V, I_{OH1} = –1.5 mA	V_{DD}–0.5			V
	V_{OH2}	P20 to P23	I_{OH2} = –100 μA	V_{DD}–0.5			V

Notes 1. 20, 24-pin products only.

2. 24-pin products only.

Caution The maximum value of V_{IH} of pins P10 to P12 and P41 for 20-pin products, P01, P10 to P12, and P41 for 24-pin products, and P00, P10 to P15, P17, and P50 for 30-pin products is V_{DD} even in N-ch open-drain mode. High level is not output in the N-ch open-drain mode.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

(T_A = –40 to +105°C, 2.4 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V) **(4/4)**

Parameter	Symbol	Conditions			MIN.	TYP.	MAX.	Unit
Output voltage, low	V_{OL1}	20-, 24-pin products: P00 to P03[Note], P10 to P14, P40 to P42 30-pin products: P00, P01, P10 to P17, P30, P31, P40, P50, P51, P120, P147		4.0 V ≤ V_{DD} ≤ 5.5 V, I_{OL1} = 8.5 mA			0.7	V
				2.7 V ≤ V_{DD} ≤ 5.5 V, I_{OL1} = 3.0 mA			0.6	V
				2.7 V ≤ V_{DD} ≤ 5.5 V, I_{OL1} = 1.5 mA			0.4	V
				2.4 V ≤ V_{DD} ≤ 5.5 V, I_{OL1} = 0.6 mA			0.4	V
	V_{OL2}	P20 to P23		I_{OL2} = 400 μA			0.4	V
	V_{OL3}	P60, P61		4.0 V ≤ V_{DD} ≤ 5.5 V, I_{OL1} = 15.0 mA			2.0	V
				4.0 V ≤ V_{DD} ≤ 5.5 V, I_{OL1} = 5.0 mA			0.4	V
				2.7 V ≤ V_{DD} ≤ 5.5 V, I_{OL1} = 3.0 mA			0.4	V
				2.4 V ≤ V_{DD} ≤ 5.5 V, I_{OL1} = 2.0 mA			0.4	V
Input leakage current, high	I_{LIH1}	Other than P121, P122	V_I = V_{DD}				1	μA
	I_{LIH2}	P121, P122 (X1, X2/EXCLK)	V_I = V_{DD}	Input port or external clock input			1	μA
				When resonator connected			10	μA
Input leakage current, low	I_{LIL1}	Other than P121, P122	V_I = V_{SS}				–1	μA
	I_{LIL2}	P121, P122 (X1, X2/EXCLK)	V_I = V_{SS}	Input port or external clock input			–1	μA
				When resonator connected			–10	μA
On-chip pull-up resistance	R_U	20-, 24-pin products: P00 to P03[Note], P10 to P14, P40 to P42, P125, $\overline{\text{RESET}}$ 30-pin products: P00, P01, P10 to P17, P30, P31, P40, P50, P51, P120, P147		V_I = V_{SS}, input port	10	20	100	kΩ

Note 24-pin products only.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

3.3.2 Supply current characteristics

(1) 20-, 24-pin products

(T_A = –40 to +105°C, 2.4 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V) **(1/2)**

Parameter	Symbol	Conditions					MIN.	TYP.	MAX.	Unit
Supply current[Note 1]	I_{DD1}	Operating mode	HS (High-speed main) mode[Note 4]	f_{IH} = 24 MHz[Note 3]	Basic operation	V_{DD} = 5.0 V		1.5		mA
						V_{DD} = 3.0 V		1.5		
					Normal operation	V_{DD} = 5.0 V		3.3	5.3	mA
						V_{DD} = 3.0 V		3.3	5.3	
				f_{IH} = 16 MHz[Note 3]		V_{DD} = 5.0 V		2.5	3.9	mA
						V_{DD} = 3.0 V		2.5	3.9	
				f_{MX} = 20 MHz[Note 2], V_{DD} = 5.0 V		Square wave input		2.8	4.7	mA
						Resonator connection		3.0	4.8	
				f_{MX} = 20 MHz[Note 2], V_{DD} = 3.0 V		Square wave input		2.8	4.7	mA
						Resonator connection		3.0	4.8	
				f_{MX} = 10 MHz[Note 2], V_{DD} = 5.0 V		Square wave input		1.8	2.8	mA
						Resonator connection		1.8	2.8	
				f_{MX} = 10 MHz[Note 2], V_{DD} = 3.0 V		Square wave input		1.8	2.8	mA
						Resonator connection		1.8	2.8	

Notes 1. Total current flowing into V_{DD}, including the input leakage current flowing when the level of the input pin is fixed to V_{DD} or V_{SS}. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.

2. When high-speed on-chip oscillator clock is stopped.

3. When high-speed system clock is stopped

4. Relationship between operation voltage width, operation frequency of CPU and operation mode is as follows.

HS(High speed main) mode: V_{DD} = 2.7 V to 5.5 V @1 MHz to 24 MHz
V_{DD} = 2.4 V to 5.5 V @1 MHz to 16 MHz

Remarks 1. f_{MX}: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)

2. f_{IH}: high-speed on-chip oscillator clock frequency

3. Temperature condition of the TYP. value is T_A = 25°C.

(1) 20-, 24-pin products

(T_A = −40 to +105°C, 2.4 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V) **(2/2)**

Parameter	Symbol	Conditions				MIN.	TYP.	MAX.	Unit
Supply current[Note 1]	I_{DD2} [Note 2]	HALT mode	HS (High-speed main) mode[Note 6]	f_{IH} = 24 MHz[Note 4]	V_{DD} = 5.0 V		440	2230	μA
					V_{DD} = 3.0 V		440	2230	
				f_{IH} = 16 MHz[Note 4]	V_{DD} = 5.0 V		400	1650	μA
					V_{DD} = 3.0 V		400	1650	
				f_{MX} = 20 MHz[Note 3], V_{DD} = 5.0 V	Square wave input		280	1900	μA
					Resonator connection		450	2000	
				f_{MX} = 20 MHz[Note 3], V_{DD} = 3.0 V	Square wave input		280	1900	μA
					Resonator connection		450	2000	
				f_{MX} = 10 MHz[Note 3], V_{DD} = 5.0 V	Square wave input		190	1010	μA
					Resonator connection		260	1090	
				f_{MX} = 10 MHz[Note 3], V_{DD} = 3.0 V	Square wave input		190	1010	μA
					Resonator connection		260	1090	
	I_{DD3} [Note 5]	STOP mode	T_A = −40°C				0.19	0.50	μA
			T_A = +25°C				0.24	0.50	
			T_A = +50°C				0.32	0.80	
			T_A = +70°C				0.48	1.20	
			T_A = +85°C				0.74	2.20	
			T_A = +105°C				1.50	10.20	

Notes 1. Total current flowing into V_{DD}, including the input leakage current flowing when the level of the input pin is fixed to V_{DD} or V_{SS}. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.

2. During HALT instruction execution by flash memory.

3. When high-speed on-chip oscillator clock is stopped.

4. When high-speed system clock is stopped.

5. Not including the current flowing into the 12-bit interval timer and watchdog timer.

6. Relationship between operation voltage width, operation frequency of CPU and operation mode is as follows.

HS (High speed main) mode: V_{DD} = 2.7 V to 5.5 V @1 MHz to 24 MHz
V_{DD} = 2.4 V to 5.5 V @1 MHz to 16 MHz

Remarks 1. f_{MX}: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)

2. f_{IH}: high-speed on-chip oscillator clock frequency

3. Except temperature condition of the TYP. value is T_A = 25°C, other than STOP mode

(2) 30-pin products

(T_A = −40 to +105°C, 2.4 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V) **(1/2)**

Parameter	Symbol	Conditions					MIN.	TYP.	MAX.	Unit
Supply current[Note 1]	I_{DD1}	Operating mode	HS (High-speed main) mode[Note 4]	f_{IH} = 24 MHz[Note 3]	Basic operation	V_{DD} = 5.0 V		1.5		mA
						V_{DD} = 3.0 V		1.5		
					Normal operation	V_{DD} = 5.0 V		3.7	5.8	mA
						V_{DD} = 3.0 V		3.7	5.8	
				f_{IH} = 16 MHz[Note 3]		V_{DD} = 5.0 V		2.7	4.2	mA
						V_{DD} = 3.0 V		2.7	4.2	
				f_{MX} = 20 MHz[Note 2], V_{DD} = 5.0 V		Square wave input		3.0	4.9	mA
						Resonator connection		3.2	5.0	
				f_{MX} = 20 MHz[Note 2], V_{DD} = 3.0 V		Square wave input		3.0	4.9	mA
						Resonator connection		3.2	5.0	
				f_{MX} = 10 MHz[Note 2], V_{DD} = 5.0 V		Square wave input		1.9	2.9	mA
						Resonator connection		1.9	2.9	
				f_{MX} = 10 MHz[Note 2], V_{DD} = 3.0 V		Square wave input		1.9	2.9	mA
						Resonator connection		1.9	2.9	

Notes 1. Total current flowing into V_{DD}, including the input leakage current flowing when the level of the input pin is fixed to V_{DD} or V_{SS}. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.

2. When high-speed on-chip oscillator clock is stopped.

3. When high-speed system clock is stopped

4. Relationship between operation voltage width, operation frequency of CPU and operation mode is as follows.

HS(High speed main) mode: V_{DD} = 2.7 V to 5.5 V @1 MHz to 24 MHz
V_{DD} = 2.4 V to 5.5 V @1 MHz to 16 MHz

Remarks 1. f_{MX}: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)

2. f_{IH}: high-speed on-chip oscillator clock frequency

3. Temperature condition of the TYP. value is T_A = 25°C.

(2) 30-pin products

(T_A = –40 to +105°C, 2.4 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V) **(2/2)**

Parameter	Symbol	Conditions				MIN.	TYP.	MAX.	Unit
Supply current Note 1	I_{DD2} Note 2	HALT mode	HS (High-speed main) mode Note 6	f_{IH} = 24 MHz Note 4	V_{DD} = 5.0 V		440	2300	μA
					V_{DD} = 3.0 V		440	2300	
				f_{IH} = 16 MHz Note 4	V_{DD} = 5.0 V		400	1700	μA
					V_{DD} = 3.0 V		400	1700	
				f_{MX} = 20 MHz Note 3, V_{DD} = 5.0 V	Square wave input		280	1900	μA
					Resonator connection		450	2000	
				f_{MX} = 20 MHz Note 3, V_{DD} = 3.0 V	Square wave input		280	1900	μA
					Resonator connection		450	2000	
				f_{MX} = 10 MHz Note 3, V_{DD} = 5.0 V	Square wave input		190	1020	μA
					Resonator connection		260	1100	
				f_{MX} = 10 MHz Note 3, V_{DD} = 3.0 V	Square wave input		190	1020	μA
					Resonator connection		260	1100	
	I_{DD3} Note 5	STOP mode	T_A = –40°C				0.18	0.50	μA
			T_A = +25°C				0.23	0.50	
			T_A = +50°C				0.30	1.10	
			T_A = +70°C				0.46	1.90	
			T_A = +85°C				0.75	3.30	
			T_A = +105°C				2.94	15.30	

Notes 1. Total current flowing into V_{DD}, including the input leakage current flowing when the level of the input pin is fixed to V_{DD} or V_{SS}. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.

2. During HALT instruction execution by flash memory.

3. When high-speed on-chip oscillator clock is stopped.

4. When high-speed system clock is stopped.

5. Not including the current flowing into the 12-bit interval timer and watchdog timer.

6. Relationship between operation voltage width, operation frequency of CPU and operation mode is as follows.

HS (High speed main) mode: V_{DD} = 2.7 V to 5.5 V @1 MHz to 24 MHz
V_{DD} = 2.4 V to 5.5 V @1 MHz to 16 MHz

Remarks 1. f_{MX}: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)

2. f_{IH}: high-speed on-chip oscillator clock frequency

3. Except STOP mode, temperature condition of the TYP. value is T_A = 25°C.

(3) Peripheral functions (Common to all products)

(T_A = –40 to +105°C, 2.4 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

<table>
<tr><th>Parameter</th><th>Symbol</th><th colspan="2">Conditions</th><th>MIN.</th><th>TYP.</th><th>MAX.</th><th>Unit</th></tr>
<tr><td>Low-speed onchip oscillator operating current</td><td>I_{FIL} Note 1</td><td colspan="2"></td><td></td><td>0.20</td><td></td><td>μA</td></tr>
<tr><td>12-bit interval timer operating current</td><td>I_{TMKA} Notes 1, 2, 3</td><td colspan="2"></td><td></td><td>0.02</td><td></td><td>μA</td></tr>
<tr><td>Watchdog timer operating current</td><td>I_{WDT} Notes 1, 2, 4</td><td colspan="2">f_{IL} = 15 kHz</td><td></td><td>0.22</td><td></td><td>μA</td></tr>
<tr><td rowspan="2">A/D converter operating current</td><td rowspan="2">I_{ADC} Notes 1, 5</td><td rowspan="2">When conversion at maximum speed</td><td>Normal mode, AV_{REFP} = V_{DD} = 5.0 V</td><td></td><td>1.30</td><td>1.70</td><td>mA</td></tr>
<tr><td>Low voltage mode, AV_{REFP} = V_{DD} = 3.0 V</td><td></td><td>0.50</td><td>0.70</td><td>mA</td></tr>
<tr><td>A/D converter reference voltage operating current</td><td>I_{ADREF} Note 1</td><td colspan="2"></td><td></td><td>75.0</td><td></td><td>μA</td></tr>
<tr><td>Temperature sensor operating current</td><td>I_{TMPS} Note 1</td><td colspan="2"></td><td></td><td>75.0</td><td></td><td>μA</td></tr>
<tr><td>LVD operating current</td><td>I_{LVD} Notes 1, 6</td><td colspan="2"></td><td></td><td>0.08</td><td></td><td>μA</td></tr>
<tr><td>Self-programming operating current</td><td>I_{FSP} Notes 1, 8</td><td colspan="2"></td><td></td><td>2.00</td><td>12.20</td><td>mA</td></tr>
<tr><td>BGO operating current</td><td>I_{BGO} Notes 1, 7</td><td colspan="2"></td><td></td><td>2.00</td><td>12.20</td><td>mA</td></tr>
<tr><td rowspan="3">SNOOZE operating current</td><td rowspan="3">I_{SNOZ} Note 1</td><td rowspan="2">ADC operation</td><td>The mode is performed Note 9</td><td></td><td>0.50</td><td>1.10</td><td>mA</td></tr>
<tr><td>The A/D conversion operations are performed, Low voltage mode, AV_{REFP} = V_{DD} = 3.0 V</td><td></td><td>1.20</td><td>2.04</td><td>mA</td></tr>
<tr><td colspan="2">CSI/UART operation</td><td></td><td>0.70</td><td>1.54</td><td>mA</td></tr>
</table>

Notes 1. Current flowing to the V_{DD}.

2. When high speed on-chip oscillator and high-speed system clock are stopped.

3. Current flowing only to the 12-bit interval timer (excluding the operating current of the low-speed on-chip oscillator). The current value of the RL78 microcontrollers is the sum of I_{DD1}, I_{DD2} or I_{DD3}, and I_{FIL} and I_{TMKA} when the 12-bit interval timer operates.

4. Current flowing only to the watchdog timer (including the operating current of the low-speed on-chip oscillator). The current value of the RL78 microcontrollers is the sum of I_{DD1}, I_{DD2} or I_{DD3} and I_{WDT} when the watchdog timer operates.

5. Current flowing only to the A/D converter. The current value of the RL78 microcontrollers is the sum of I_{DD1} or I_{DD2} and I_{ADC} when the A/D converter operates in an operation mode or the HALT mode.

6. Current flowing only to the LVD circuit. The current value of the RL78 microcontrollers is the sum of I_{DD1}, I_{DD2} or I_{DD3} and I_{LVD} when the LVD circuit operates.

7. Current flowing only during data flash rewrite.

8. Current flowing only during self programming.

9. For shift time to the SNOOZE mode, see **17.3.3 SNOOZE mode**.

Remarks 1. f_{IL}: Low-speed on-chip oscillator clock frequency

2. Temperature condition of the TYP. value is T_A = 25°C

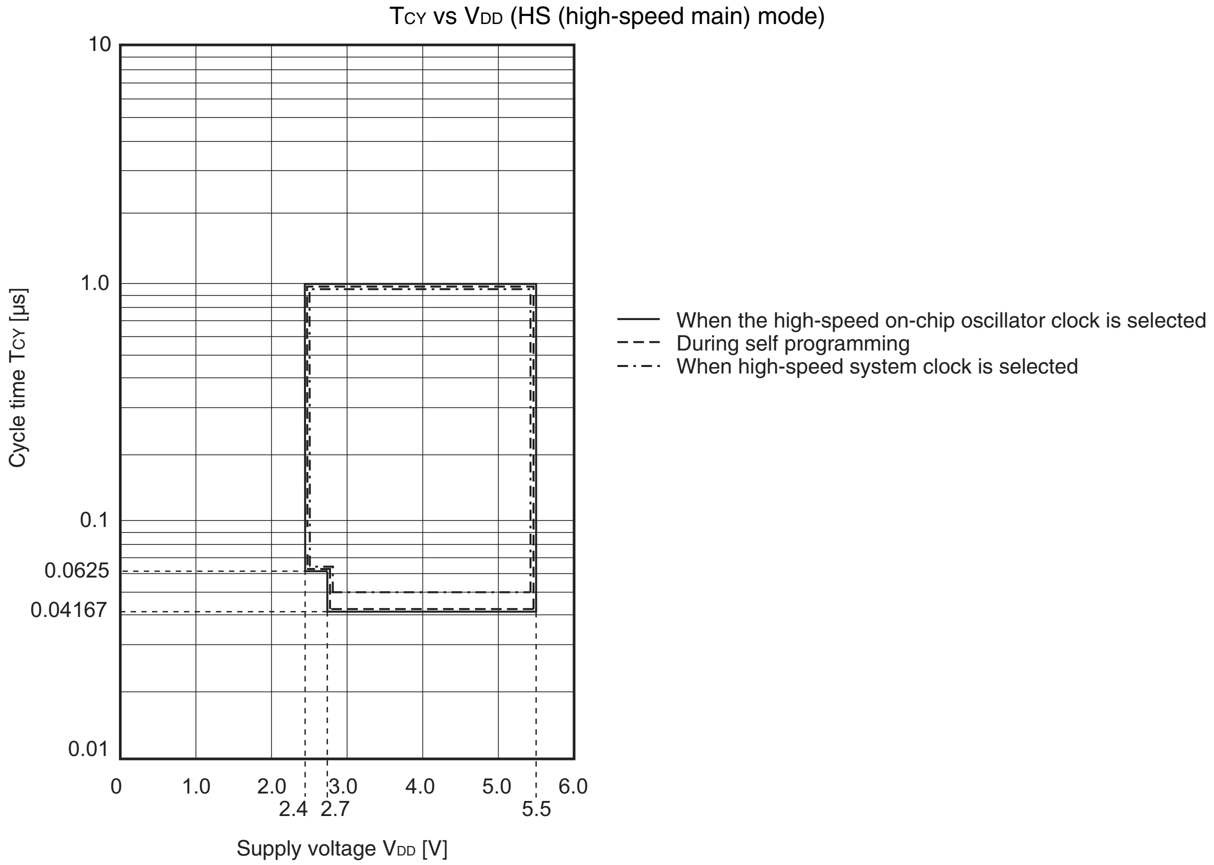
3.4 AC Characteristics

(T_A = –40 to +105°C, 2.4 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

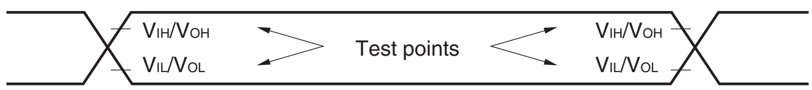
Items	Symbol	Conditions			MIN.	TYP.	MAX.	Unit
Instruction cycle (minimum instruction execution time)	T_{CY}	Main system clock (f_{MAIN}) operation	HS (High-speed main) mode	2.7 V ≤ V_{DD} ≤ 5.5 V	0.04167		1	μs
				2.4 V ≤ V_{DD} < 2.7 V	0.0625		1	μs
		During self programming	HS (High-speed main) mode	2.7 V ≤ V_{DD} ≤ 5.5 V	0.04167		1	μs
				2.4 V ≤ V_{DD} < 2.7 V	0.0625		1	μs
External main system clock frequency	f_{EX}	2.7 V ≤ V_{DD} ≤ 5.5 V			1.0		20.0	MHz
		2.4 V ≤ V_{DD} < 2.7 V			1.0		16.0	MHz
External main system clock input high-level width, low-level width	t_{EXH}, t_{EXL}	2.7 V ≤ V_{DD} ≤ 5.5 V			24			ns
		2.4 V ≤ V_{DD} < 2.7 V			30			ns
TI00 to TI07 input high-level width, low-level width	t_{TIH}, t_{TIL}				1/f_{MCK} + 10			ns
TO00 to TO07 output frequency	f_{TO}	4.0 V ≤ V_{DD} ≤ 5.5 V					12	MHz
		2.7 V ≤ V_{DD} < 4.0 V					8	MHz
		2.4 V ≤ V_{DD} < 2.7 V					4	MHz
PCLBUZ0, or PCLBUZ1 output frequency	f_{PCL}	4.0 V ≤ V_{DD} ≤ 5.5 V					16	MHz
		2.7 V ≤ V_{DD} < 4.0 V					8	MHz
		2.4 V ≤ V_{DD} < 2.7 V					4	MHz
INTP0 to INTP5 input high-level width, low-level width	t_{INTH}, t_{INTL}				1			μs
KR0 to KR9 input available width	t_{KR}				250			ns
$\overline{\text{RESET}}$ low-level width	t_{RSL}				10			μs

Remark f_{MCK}: Timer array unit operation clock frequency
(Operation clock to be set by the timer clock select register 0 (TPS0) and the CKS0n bit of timer mode register 0n (TMR0n). n: Channel number (n = 0 to 7))

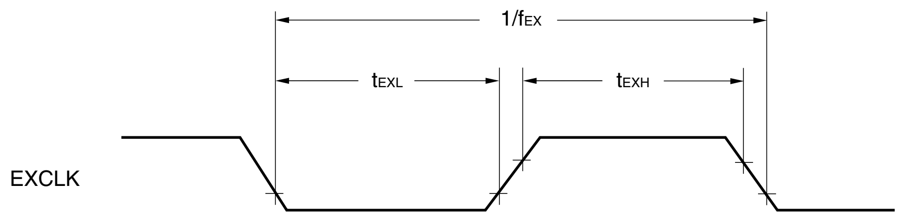
Minimum Instruction Execution Time during Main System Clock Operation



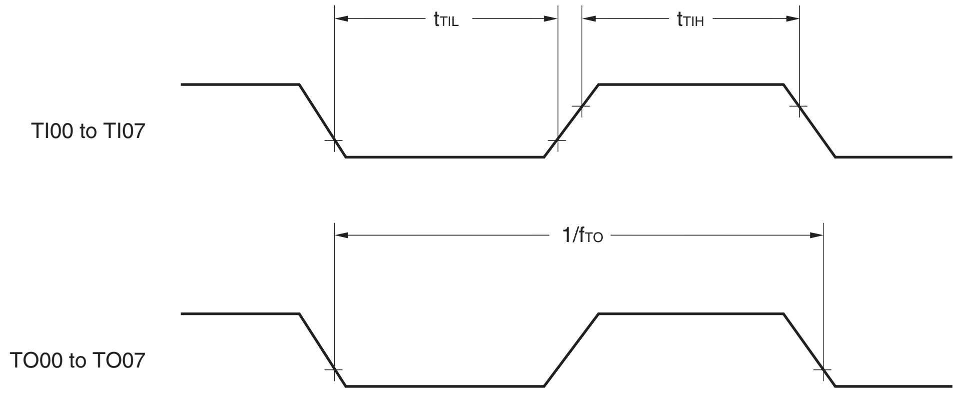
AC Timing Test Point



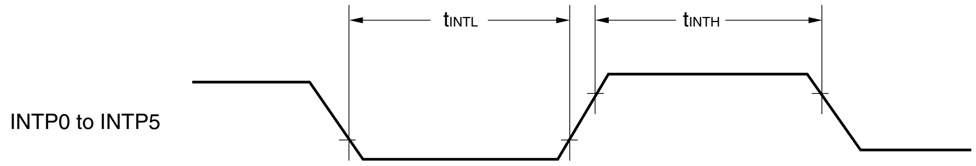
External Main System Clock Timing



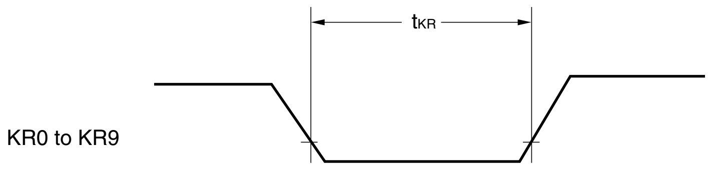
TI/TO Timing



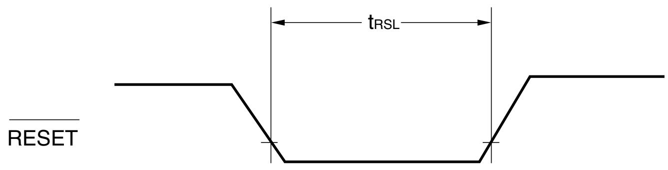
Interrupt Request Input Timing



Key Interrupt Input Timing

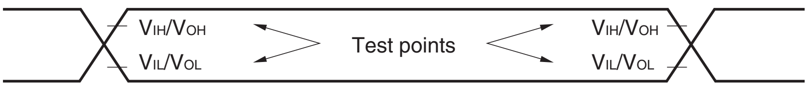


$\overline{\text{RESET}}$ Input Timing



3.5 Peripheral Functions Characteristics

AC Timing Test Point



3.5.1 Serial array unit

(1) During communication at same potential (UART mode)
(T_A = –40 to +105°C, 2.4 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

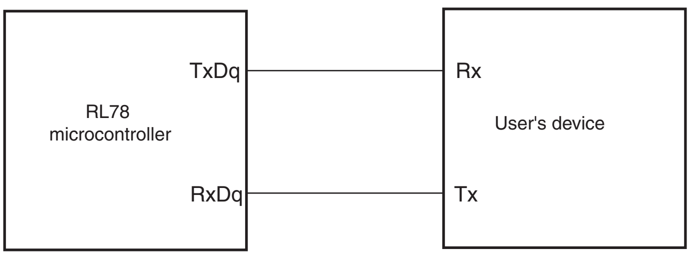
Parameter	Symbol	Conditions	HS (high-speed main) Mode		Unit
			MIN.	MAX.	
Transfer rate Note 1				f_{MCK}/12	bps
		Theoretical value of the maximum transfer rate $f_{CLK} = f_{MCK}$ Note2		2.0	Mbps

Notes 1. Transfer rate in the SNOOZE mode is 4800 bps only.

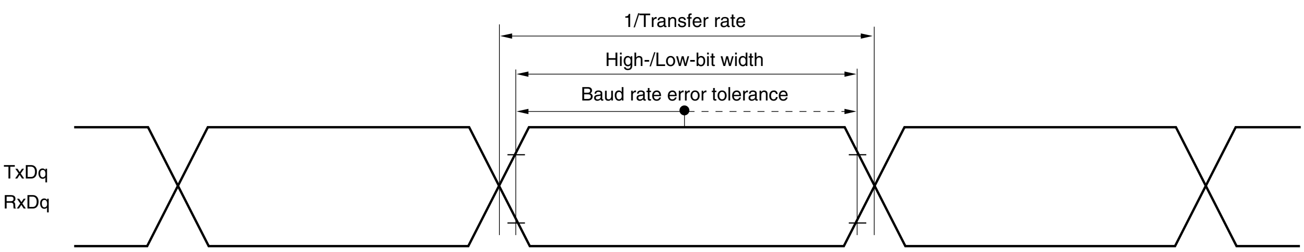
2. The maximum operating frequencies of the CPU/peripheral hardware clock (f_{CLK}) are:
HS (high-speed main) mode: 24 MHz (2.7 V ≤ V_{DD} ≤ 5.5 V)
16 MHz (2.4 V ≤ V_{DD} ≤ 5.5 V)

Caution Select the normal input buffer for the RxDq pin and the normal output mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg).

UART mode connection diagram (during communication at same potential)



UART mode bit width (during communication at same potential) (reference)



Remarks 1. q: UART number (q = 0 to 2), g: PIM, POM number (g = 0, 1)

2. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the serial clock select register m (SPSm) and the CKSmn bit of serial mode register mn (SMRmn).
m: Unit number, n: Channel number (mn = 00 to 03, 10, 11))

(2) During communication at same potential (CSI mode) (master mode, SCKp... internal clock output)
(T_A = –40 to +105°C, 2.4 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions		HS (high-speed main) Mode		Unit
				MIN.	MAX.	
SCKp cycle time	t_{KCY1}	t_{KCY1} ≥ 4/f_{CLK}	2.7 V ≤ V_{DD} ≤ 5.5 V	334		ns
			2.4 V ≤ V_{DD} ≤ 5.5 V	500		ns
SCKp high-/low-level width	t_{KH1}, t_{KL1}	4.0 V ≤ V_{DD} ≤ 5.5 V		t_{KCY1}/2–24		ns
		2.7 V ≤ V_{DD} ≤ 5.5 V		t_{KCY1}/2–36		ns
		2.4 V ≤ V_{DD} ≤ 5.5 V		t_{KCY1}/2–76		ns
SIp setup time (to SCKp↑) Note 1	t_{SIK1}	4.0 V ≤ V_{DD} ≤ 5.5 V		66		ns
		2.7 V ≤ V_{DD} ≤ 5.5 V		66		ns
		2.4 V ≤ V_{DD} ≤ 5.5 V		113		ns
SIp hold time (from SCKp↑) Note 2	t_{KSI1}			38		ns
Delay time from SCKp↓ to SOp output Note 3	t_{KSO1}	C = 30 pF Note4			50	ns

Notes 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

4. C is the load capacitance of the SCKp and SOp output lines.

Caution Select the normal input buffer for the SIp pin and the normal output mode for the SOp and SCKp pins by using port input mode register 1 (PIM1) and port output mode registers 0, 1, 4 (POM0, POM1, POM4).

Remarks 1. p: CSI number (p = 00, 01, 11, 20), m: Unit number (m = 0, 1), n: Channel number (n = 0, 1, 3)

2. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the serial clock select register m (SPSm) and the CKSmn bit of serial mode register mn (SMRmn). m: Unit number (m = 0, 1), n: Channel number (n = 0, 1, 3))

(3) During communication at same potential (CSI mode) (slave mode, SCKp... external clock input)
(T_A = –40 to +105°C, 2.4 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions		HS (high-speed main) Mode MIN.	HS (high-speed main) Mode MAX.	Unit
SCKp cycle time Note4	t_{KCY2}	4.0 V ≤ V_{DD} ≤ 5.5 V	20 MHz < f_{MCK}	16/f_{MCK}		ns
			f_{MCK} ≤ 20 MHz	12/f_{MCK}		ns
		2.7 V ≤ V_{DD} ≤ 5.5 V	16 MHz < f_{MCK}	16/f_{MCK}		ns
			f_{MCK} ≤ 16 MHz	12/f_{MCK}		ns
		2.4 V ≤ V_{DD} ≤ 5.5 V		12/f_{MCK} and 1000		ns
SCKp high-/low-level width	t_{KH2}, t_{KL2}	4.0 V ≤ V_{DD} ≤ 5.5 V		t_{KCY2}/2–14		ns
		2.7 V ≤ V_{DD} ≤ 5.5 V		t_{KCY2}/2–16		ns
		2.4 V ≤ V_{DD} ≤ 5.5 V		t_{KCY2}/2–36		ns
SIp setup time (to SCKp↑) Note 1	t_{SIK2}	2.7 V ≤ V_{DD} ≤ 5.5 V		1/f_{MCK} + 40		ns
		2.4 V ≤ V_{DD} ≤ 5.5 V		1/f_{MCK} + 60		ns
SIp hold time (from SCKp↑) Note 2	t_{KSI2}			1/f_{MCK} + 62		ns
Delay time from SCKp↓ to SOp output Note 3	t_{KSO2}	C = 30 pF Note4	2.7 V ≤ V_{DD} ≤ 5.5 V		2/f_{MCK} + 66	ns
			2.4 V ≤ V_{DD} ≤ 5.5 V		2/f_{MCK} + 113	ns

Notes 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

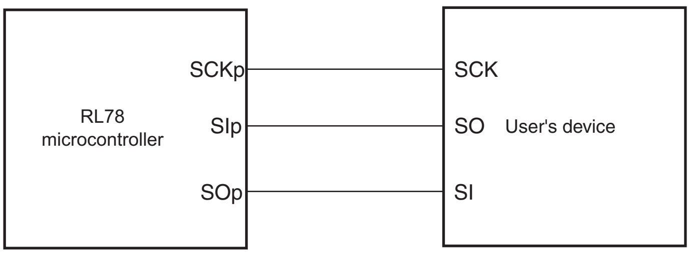
3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

4. C is the load capacitance of the SOp output lines.

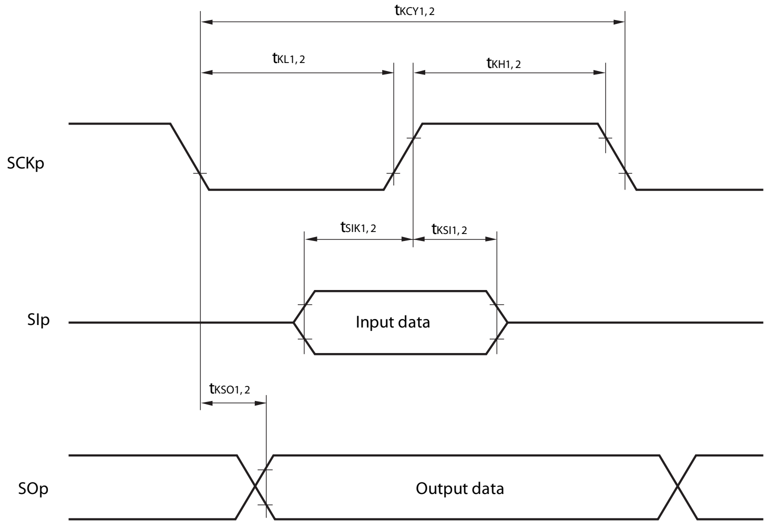
5. Transfer rate in the SNOOZE mode: MAX. 1 Mbps

Caution Select the normal input buffer for the SIp and SCKp pins and the normal output mode for the SOp pin by using port input mode register 1 (PIM1) and port output mode registers 0, 1, 4 (POM0, POM1, POM4).

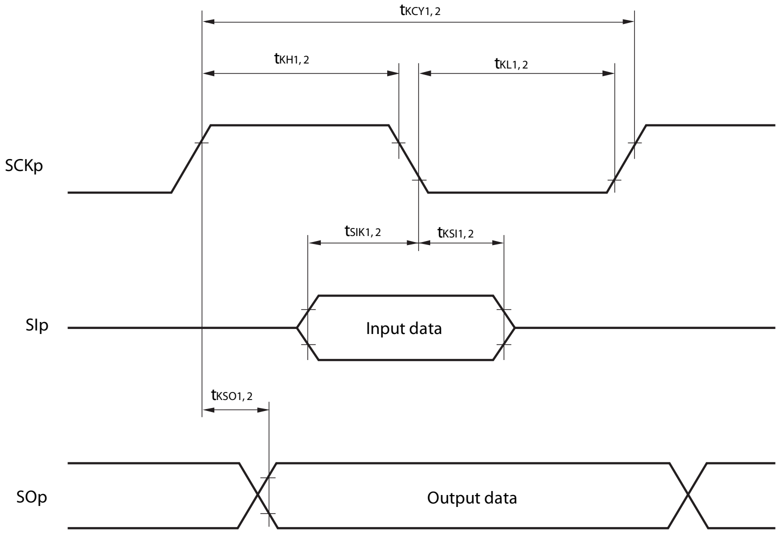
CSI mode connection diagram (during communication at same potential)



CSI mode serial transfer timing (during communication at same potential)
(When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



CSI mode serial transfer timing (during communication at same potential)
(When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



Remarks 1. p: CSI number (p = 00, 01, 11, 20), m: Unit number (m = 0, 1), n: Channel number (n = 0, 1, 3)

2. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the serial clock select register m (SPSm) and the CKSmn bit of serial mode register mn (SMRmn). m: Unit number (m = 0,1), n: Channel number (n = 0, 1, 3))

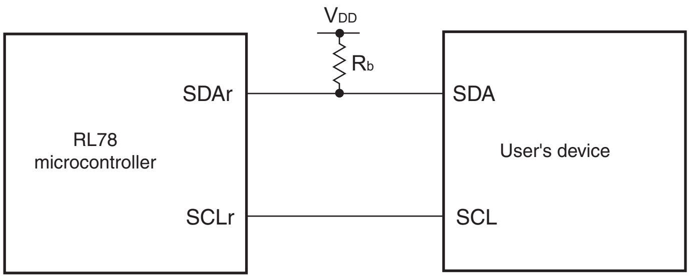
(4) During communication at same potential (simplified I²C mode)
(T_A = –40 to +105°C, 2.4 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions	HS (high-speed main) Mode		Unit
			MIN.	MAX.	
SCLr clock frequency	f_{SCL}	C_b = 100 pF, R_b = 3 kΩ		100 Note 1	kHz
Hold time when SCLr = “L”	t_{LOW}	C_b = 100 pF, R_b = 3 kΩ	4600		ns
Hold time when SCLr = “H”	t_{HIGH}	C_b = 100 pF, R_b = 3 kΩ	4600		ns
Data setup time (reception)	$t_{SU:DAT}$	C_b = 100 pF, R_b = 3 kΩ	1/f_{MCK} + 580 Note 2		ns
Data hold time (transmission)	$t_{HD:DAT}$	C_b = 100 pF, R_b = 3 kΩ	0	1420	ns

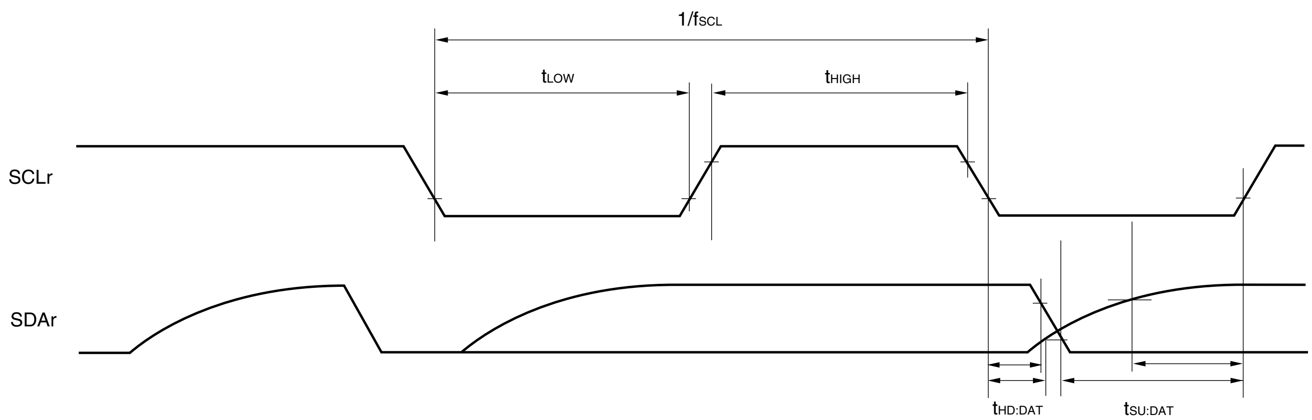
Notes 1. The value must also be equal to or less than f_{MCK}/4.
2. Set $t_{SU:DAT}$ so that it will not exceed the hold time when SCLr = "L" or SCLr = "H".

Caution Select the N-ch open drain output (V_{DD} tolerance) mode for SDAr by using port output mode register h (POMh).

Simplified I²C mode connection diagram (during communication at same potential)



Simplified I²C mode serial transfer timing (during communication at same potential)



Remarks 1. R_b [Ω]:Communication line (SDAr) pull-up resistance
C_b [F]: Communication line (SCLr, SDAr) load capacitance
2. r: IIC number (r = 00, 01, 11, 20), h: = POM number (h = 0, 1, 4, 5)
3. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the serial clock select register m (SPSm) and the CKSmn bit of serial mode register mn (SMRmn).
m: Unit number (m = 0, 1), n: Channel number (0, 1, 3))

(5) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode)
(T_A = –40 to +105°C, 2.4 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions			HS (high-speed main) Mode MIN.	HS (high-speed main) Mode MAX.	Unit
Transfer rate Note 4		Reception	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V			f_{MCK}/12 Note 1	bps
				Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK}$ Note 2		2.0	Mbps
			2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V			f_{MCK}/12 Note 1	bps
				Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK}$ Note 2		2.0	Mbps
			2.4 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V			f_{MCK}/12 Note 1	bps
				Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK}$ Note 2		2.0	Mbps
		Transmission	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V			**Note 3**	bps
				Theoretical value of the maximum transfer rate C_b = 50 pF, R_b = 1.4 kΩ, V_b = 2.7 V		2.0 Note 4	Mbps
			2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V,			**Note 5**	bps
				Theoretical value of the maximum transfer rate C_b = 50 pF, R_b = 2.7 kΩ, V_b = 2.3 V		1.2 Note 6	Mbps
			2.4 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V			**Notes 2, 7**	bps
				Theoretical value of the maximum transfer rate C_b = 50 pF, R_b = 5.5 kΩ, V_b = 1.6 V		0.43 Note 8	Mbps

Notes 1. Transfer rate in the SNOOZE mode is 4800 bps only.

2. The maximum operating frequencies of the CPU/peripheral hardware clock (f_{CLK}) are:
HS (high-speed main) mode: 24 MHz (2.7 V ≤ V_{DD} ≤ 5.5 V)
16 MHz (2.4 V ≤ V_{DD} ≤ 5.5 V)

3. The smaller maximum transfer rate derived by using f_{MCK}/12 or the following expression is the valid maximum transfer rate.
Expression for calculating the transfer rate when 4.0 V ≤ V_{DD} ≤ 5.5 V and 2.7 V ≤ V_b ≤ 4.0 V

$$\text{Maximum transfer rate} = \frac{1}{\{-C_b \times R_b \times \ln(1 - \frac{2.2}{V_b})\} \times 3} \text{ [bps]}$$

$$\text{Baud rate error (theoretical value)} = \frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln (1 - \frac{2.2}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100\ [\%]$$

* This value is the theoretical value of the relative difference between the transmission and reception sides.

4. This value as an example is calculated when the conditions described in the “Conditions” column are met. Refer to **Note 3** above to calculate the maximum transfer rate under conditions of the customer.

5. The smaller maximum transfer rate derived by using $f_{MCK}/12$ or the following expression is the valid maximum transfer rate.
Expression for calculating the transfer rate when 2.7 V ≤ V_{DD} < 4.0 V and 2.3 V ≤ V_b ≤ 2.7 V

$$\text{Maximum transfer rate} = \frac{1}{\{-C_b \times R_b \times \ln (1 - \frac{2.0}{V_b})\} \times 3}\ [\text{bps}]$$

$$\text{Baud rate error (theoretical value)} = \frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln (1 - \frac{2.0}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100\ [\%]$$

* This value is the theoretical value of the relative difference between the transmission and reception sides.

6. This value as an example is calculated when the conditions described in the “Conditions” column are met. Refer to **Note 5** above to calculate the maximum transfer rate under conditions of the customer.

7. The smaller maximum transfer rate derived by using $f_{MCK}/12$ or the following expression is the valid maximum transfer rate.
Expression for calculating the transfer rate when 2.4 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V

$$\text{Maximum transfer rate} = \frac{1}{\{-C_b \times R_b \times \ln (1 - \frac{1.5}{V_b})\} \times 3}\ [\text{bps}]$$

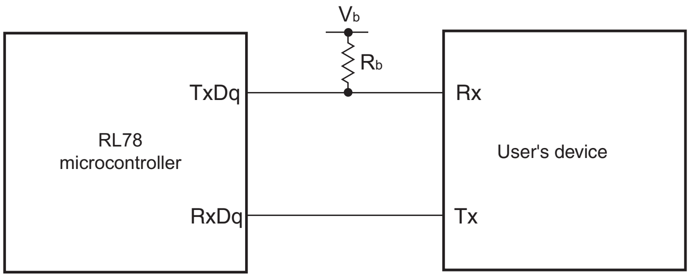
$$\text{Baud rate error (theoretical value)} = \frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln (1 - \frac{1.5}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100\ [\%]$$

* This value is the theoretical value of the relative difference between the transmission and reception sides.

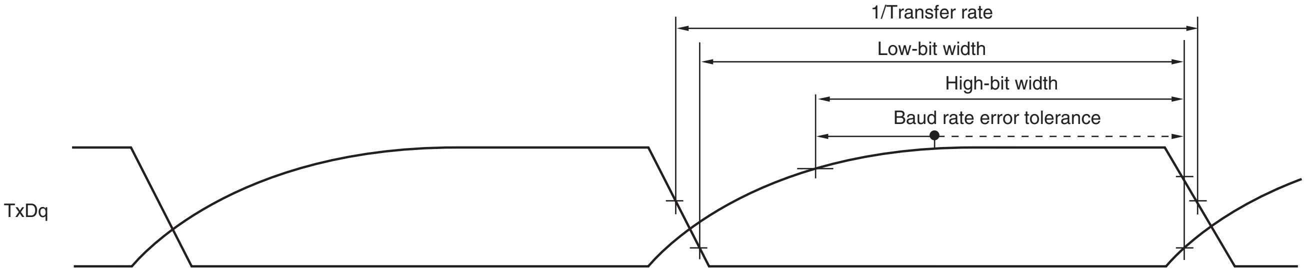
8. This value as an example is calculated when the conditions described in the “Conditions” column are met. Refer to **Note 7** above to calculate the maximum transfer rate under conditions of the customer.

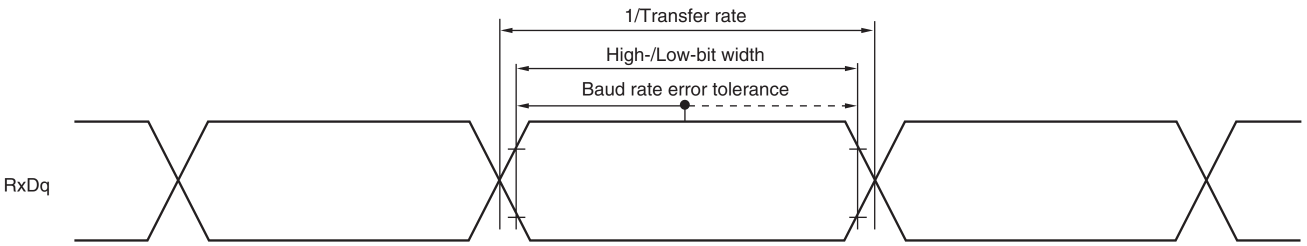
Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (V_{DD} tolerance) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). **For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.**

UART mode connection diagram (during communication at different potential)



UART mode bit width (during communication at different potential) (reference)





Remarks 1. R_b[Ω]: Communication line (TxDq) pull-up resistance, C_b[F]: Communication line (TxDq) load capacitance, V_b[V]: Communication line voltage

2. q: UART number (q = 0 to 2), g: PIM and POM number (g = 0, 1)

3. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the serial clock select register m (SPSm) and the CKSmn bit of serial mode register mn (SMRmn).
m: Unit number, n: Channel number (mn = 00 to 03, 10, 11))

4. UART0 of the 20- and 24-pin products supports communication at different potential only when the peripheral I/O redirection function is not used.

(6) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output) (1/3)

(T_A = –40 to +105°C, 2.4 V ≤ V_{DD} ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions		HS (high-speed main) Mode		Unit
				MIN.	MAX.	
SCKp cycle time	t_{KCY1}	t_{KCY1} ≥ 4/f_{CLK}	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 30 pF, R_b = 1.4 kΩ	600		ns
			2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ	1000		ns
			2.4 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V, C_b = 30 pF, R_b = 5.5 kΩ	2300		ns
SCKp high-level width	t_{KH1}	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 30 pF, R_b = 1.4 kΩ		t_{KCY1}/2 –150		ns
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ		t_{KCY1}/2 –340		ns
		2.4 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V, C_b = 30 pF, R_b = 5.5 kΩ		t_{KCY1}/2 –916		ns
SCKp low-level width	t_{KL1}	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 30 pF, R_b = 1.4 kΩ		t_{KCY1}/2 –24		ns
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ		t_{KCY1}/2 –36		ns
		2.4 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V, C_b = 30 pF, R_b = 5.5 kΩ		t_{KCY1}/2 –100		ns

Cautions 1. Select the TTL input buffer for the SIp pin and the N-ch open drain output (V_{DD} tolerance) mode for the SOp pin and SCKp pin by using port input mode register 1 (PIM1) and port output mode register 1 (POM1). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

2. CSI01 and CSI11 cannot communicate at different potential.

Remarks 1. R_b [Ω]: Communication line (SCKp, SOp) pull-up resistance, C_b [F]: Communication line (SCKp, SOp) load capacitance, V_b [V]: Communication line voltage

2. p: CSI number (p = 00, 20)

(6) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output) (2/3)

(T_A = –40 to +105°C, 2.4 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions	HS (high-speed main) Mode		Unit
			MIN.	MAX.	
SIp setup time (to SCKp↑) Note	t_{SIK1}	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 30 pF, R_b = 1.4 kΩ	162		ns
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ	354		ns
		2.4 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V, C_b = 30 pF, R_b = 5.5 kΩ	958		ns
SIp hold time (from SCKp↑) Note	t_{KSI1}	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 30 pF, R_b = 1.4 kΩ	38		ns
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ	38		ns
		2.4 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V, C_b = 30 pF, R_b = 5.5 kΩ	38		ns
Delay time from SCKp↓ to SOp output Note	t_{KSO1}	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 30 pF, R_b = 1.4 kΩ		200	ns
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ		390	ns
		2.4 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V, C_b = 30 pF, R_b = 5.5 kΩ		966	ns

Note When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.

(**Cautions** and **Remarks** are listed on the next page.)

(6) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output) (3/3)

(T_A = –40 to +105°C, 2.4 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions	HS (high-speed main) Mode		Unit
			MIN.	MAX.	
SIp setup time (to SCKp↓) Note	t_{SIK1}	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 30 pF, R_b = 1.4 kΩ	88		ns
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ	88		ns
		2.4 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V, C_b = 30 pF, R_b = 5.5 kΩ	220		ns
SIp hold time (from SCKp↓) Note	t_{KSI1}	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 30 pF, R_b = 1.4 kΩ	38		ns
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ	38		ns
		2.4 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V, C_b = 30 pF, R_b = 5.5 kΩ	38		ns
Delay time from SCKp↑ to SOp output Note	t_{KSO1}	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 30 pF, R_b = 1.4 kΩ		50	ns
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ		50	ns
		2.4 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V, C_b = 30 pF, R_b = 5.5 kΩ		50	ns

Note When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

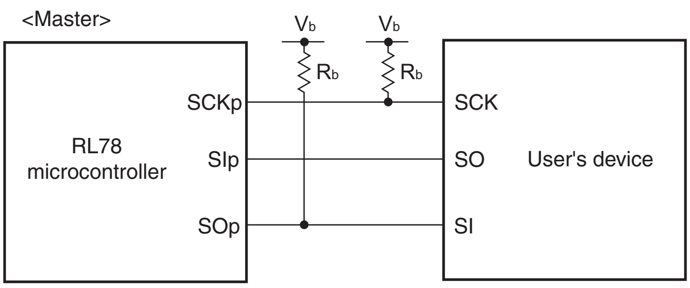
Cautions 1. Select the TTL input buffer for the SIp pin and the N-ch open drain output (V_{DD} tolerance) mode for the SOp pin and SCKp pin by using port input mode register 1 (PIM1) and port output mode register 1 (POM1). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

2. CSI01 and CSI11 cannot communicate at different potential.

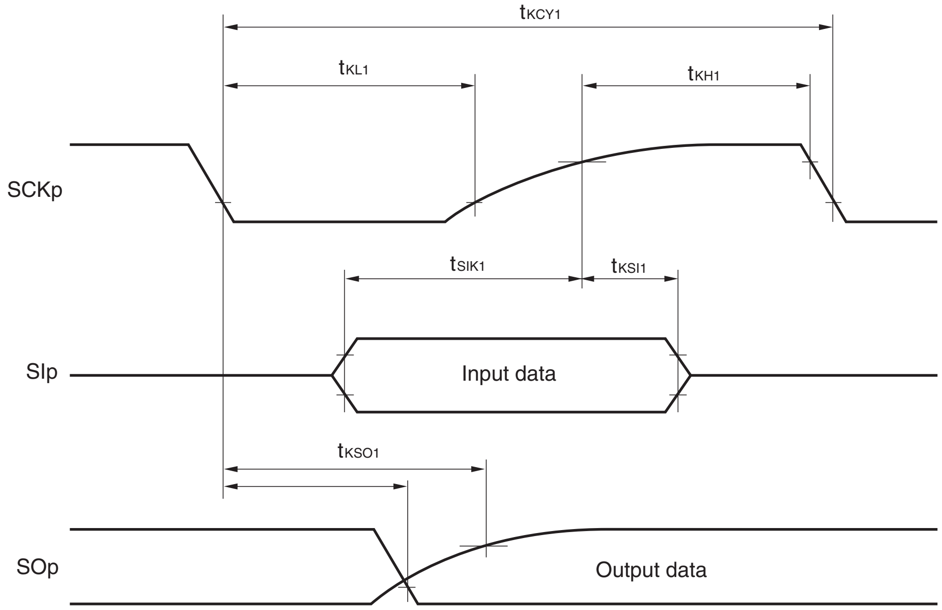
Remarks 1. R_b [Ω]: Communication line (SCKp, SOp) pull-up resistance, C_b [F]: Communication line (SCKp, SOp) load capacitance, V_b [V]: Communication line voltage

2. p: CSI number (p = 00, 20), m: Unit number (m = 0, 1), n: Channel number (n = 0)

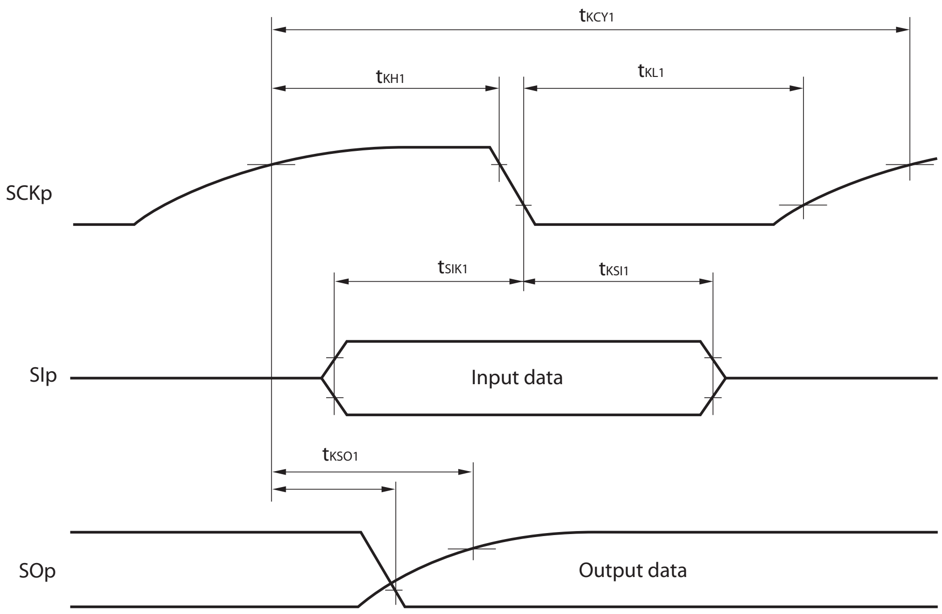
CSI mode connection diagram (during communication at different potential)



CSI mode serial transfer timing (master mode) (during communication at different potential)
(When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1)



CSI mode serial transfer timing (master mode) (during communication at different potential)
(When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



Remark p: CSI number (p = 00, 20), m: Unit number (m = 0, 1), n: Channel number (n = 0)

(7) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (slave mode, SCKp... external clock input)
(T_A = –40 to +105°C, 2.4 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions		HS (high-speed main) Mode MIN.	HS (high-speed main) Mode MAX.	Unit
SCKp cycle time Note 1	t_{KCY2}	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V	20 MHz < f_{MCK} ≤ 24 MHz	24/f_{MCK}		ns
			8 MHz < f_{MCK} ≤ 20 MHz	20/f_{MCK}		ns
			4 MHz < f_{MCK} ≤ 8 MHz	16/f_{MCK}		ns
			f_{MCK} ≤ 4 MHz	12/f_{MCK}		ns
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V	20 MHz < f_{MCK} ≤ 24 MHz	32/f_{MCK}		ns
			16 MHz < f_{MCK} ≤ 20 MHz	28/f_{MCK}		ns
			8 MHz < f_{MCK} ≤ 16 MHz	24/f_{MCK}		ns
			4 MHz < f_{MCK} ≤ 8 MHz	16/f_{MCK}		ns
			f_{MCK} ≤ 4 MHz	12/f_{MCK}		ns
		2.4 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V	20 MHz < f_{MCK} ≤ 24 MHz	72/f_{MCK}		ns
			16 MHz < f_{MCK} ≤ 20 MHz	64/f_{MCK}		ns
			8 MHz < f_{MCK} ≤ 16 MHz	52/f_{MCK}		ns
			4 MHz < f_{MCK} ≤ 8 MHz	32/f_{MCK}		ns
			f_{MCK} ≤ 4 MHz	20/f_{MCK}		ns
SCKp high-/low-level width	t_{KH2}, t_{KL2}	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V		t_{KCY2}/2 – 24		ns
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V		t_{KCY2}/2 – 36		ns
		2.4 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V		t_{KCY2}/2 – 100		ns
SIp setup time (to SCKp↑) Note 2	t_{SIK2}	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_{DD} ≤ 4.0 V		1/f_{MCK} + 40		ns
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V		1/f_{MCK} + 40		ns
		2.4 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_{DD} ≤ 2.0 V		1/f_{MCK} + 60		ns
SIp hold time (from SCKp↑) Note 3	t_{KSI2}			1/f_{MCK} + 62		ns
Delay time from SCKp↓ to SOp output Note 4	t_{KSO2}	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 30 pF, R_b = 1.4 kΩ			2/f_{MCK} + 240	ns
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ			2/f_{MCK} + 428	ns
		2.4 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V, C_b = 30 pF, R_b = 5.5 kΩ			2/f_{MCK} + 1146	ns

Notes 1. Transfer rate in the SNOOZE mode: MAX. 1 Mbps

2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

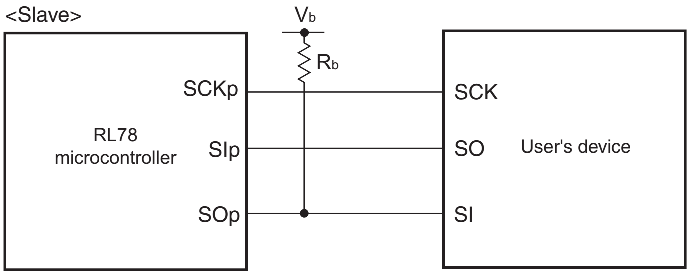
3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

4. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

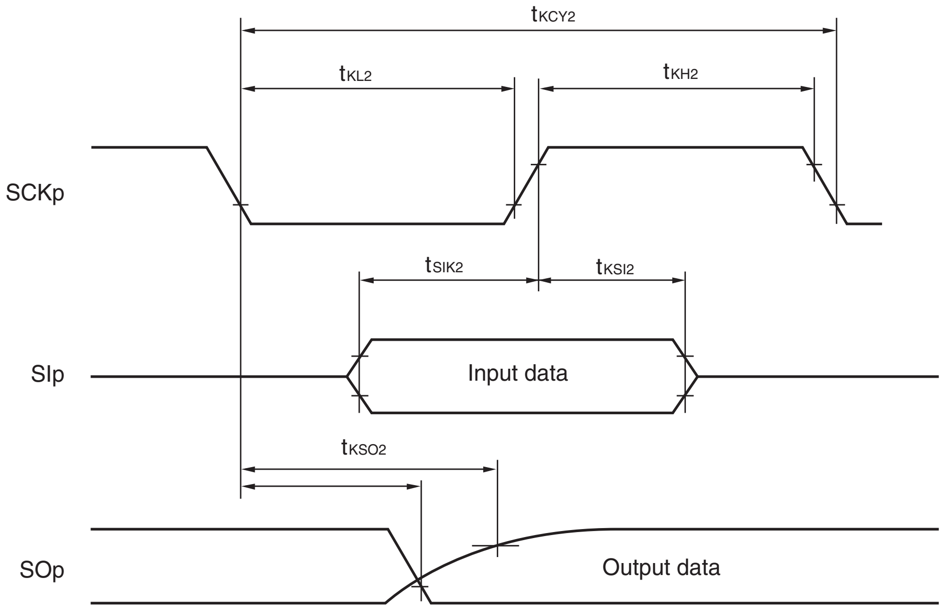
Cautions 1. Select the TTL input buffer for the SIp and SCKp pins and the N-ch open drain output (V_{DD} tolerance) mode for the SOp pin by using port input mode register 1 (PIM1) and port output mode register 1 (POM1). **For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.**

2. CSI01 and CSI11 cannot communicate at different potential.

CSI mode connection diagram (during communication at different potential)



CSI mode serial transfer timing (slave mode) (during communication at different potential)
(When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)

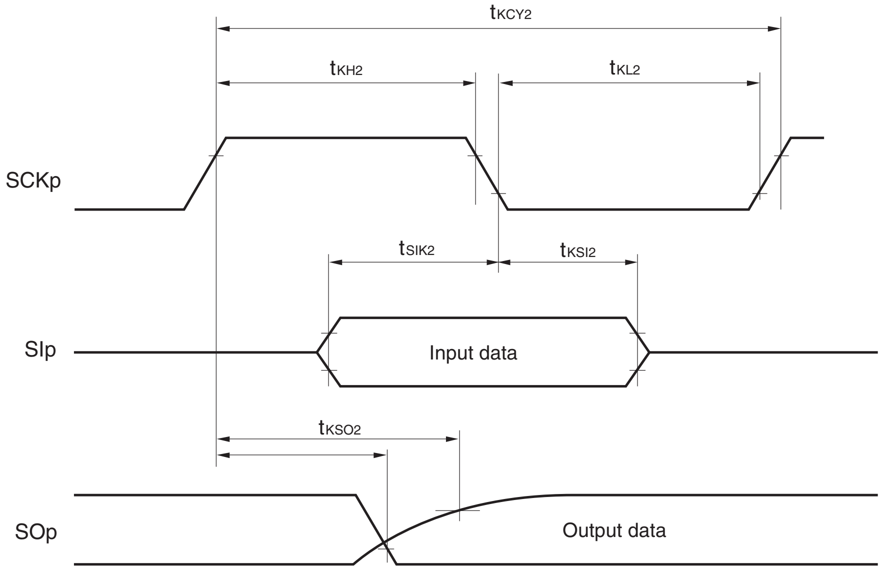


Remarks 1. R_b [Ω]: Communication line (SOp) pull-up resistance, C_b [F]: Communication line (SOp) load capacitance, V_b [V]: Communication line voltage

2. p: CSI number (p = 00, 20), m: Unit number (m = 0, 1), n: Channel number (n = 0)

3. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the serial clock select register m (SPSm) and the CKSmn bit of serial mode register mn (SMRmn))

CSI mode serial transfer timing (slave mode) (during communication at different potential)
(When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



Remark p: CSI number (p = 00, 20), m: Unit number (m = 0, 1), n: Channel number (n = 0)

(8) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified I²C mode)
(T_A = –40 to +105°C, 2.4 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions	HS (high-speed main) Mode		Unit
			MIN.	MAX.	
SCLr clock frequency	f_{SCL}	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 100 pF, R_b = 2.8 kΩ		100 Note1	kHz
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 100 pF, R_b = 2.7 kΩ		100 Note1	kHz
		2.4 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V, C_b = 100 pF, R_b = 5.5 kΩ		100 Note1	kHz
Hold time when SCLr = "L"	t_{LOW}	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 100 pF, R_b = 2.8 kΩ	4600		ns
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 100 pF, R_b = 2.7 kΩ	4600		ns
		2.4 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V, C_b = 100 pF, R_b = 5.5 kΩ	4650		ns
Hold time when SCLr = "H"	t_{HIGH}	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 100 pF, R_b = 2.8 kΩ	2700		ns
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 100 pF, R_b = 2.7 kΩ	2400		ns
		2.4 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V, C_b = 100 pF, R_b = 5.5 kΩ	1830		ns
Data setup time (reception)	$t_{SU:DAT}$	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 100 pF, R_b = 2.8 kΩ	$1/f_{MCK}$ + 760 Note3		ns
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 100 pF, R_b = 2.7 kΩ	$1/f_{MCK}$ + 760 Note3		ns
		2.4 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V, C_b = 100 pF, R_b = 5.5 kΩ	$1/f_{MCK}$ + 570 Note3		ns
Data hold time (transmission)	$t_{HD:DAT}$	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 100 pF, R_b = 2.8 kΩ	0	1420	ns
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 100 pF, R_b = 2.7 kΩ	0	1420	ns
		2.4 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V, C_b = 100 pF, R_b = 5.5 kΩ	0	1215	ns

Notes 1. The value must also be equal to or less than $f_{MCK}/4$.

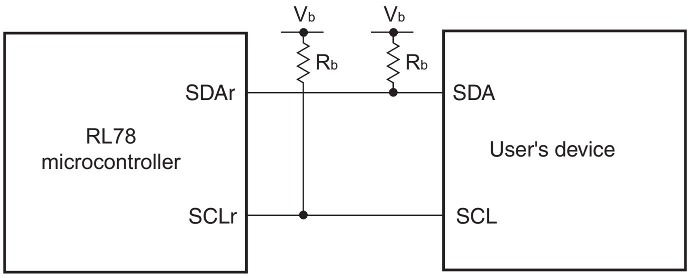
2. Set $t_{SU:DAT}$ so that it will not exceed the hold time when SCLr = "L" or SCLr = "H".

Cautions 1. Select the TTL input buffer and the N-ch open drain output (V_{DD} tolerance) mode for the SDAr pin and the N-ch open drain output (V_{DD} tolerance) mode for the SCLr pin by using port input mode register 1 (PIM1) and port output mode register 1 (POM1). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

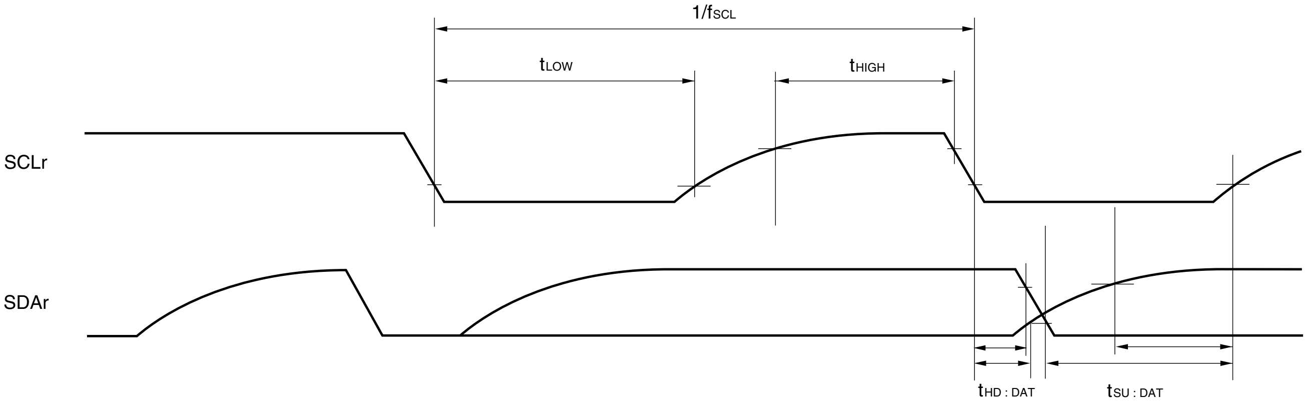
2. IIC01 and IIC11 cannot communicate at different potential.

(**Remarks** are listed on the next page.)

Simplified I²C mode connection diagram (during communication at different potential)



Simplified I²C mode serial transfer timing (during communication at different potential)



Remarks 1. R_b [Ω]: Communication line (SDAr, SCLr) pull-up resistance, C_b [F]: Communication line (SDAr, SCLr) load capacitance, V_b [V]: Communication line voltage

2. r: IIC Number (r = 00, 20)

3. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the serial clock select register m (SPSm) and the CKSmn bit of serial mode register mn (SMRmn).
m: Unit number (m = 0,1), n: Channel number (n = 0))

3.5.2 Serial interface IICA

(T_A = –40 to +105°C, 2.4 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions	HS (high-speed main) mode				Unit
			Standard Mode		Fast Mode		
			MIN.	MAX.	MIN.	MAX.	
SCLA0 clock frequency	f_{SCL}	Fast mode: f_{CLK} ≥ 3.5 MHz			0	400	kHz
		Normal mode: f_{CLK} ≥ 1 MHz	0	100			kHz
Setup time of restart condition	$t_{SU:STA}$		4.7		0.6		μs
Hold time[Note 1]	$t_{HD:STA}$		4.0		0.6		μs
Hold time when SCLA0 = "L"	t_{LOW}		4.7		1.3		μs
Hold time when SCLA0 = "H"	t_{HIGH}		4.0		0.6		μs
Data setup time (reception)	$t_{SU:DAT}$		250		100		ns
Data hold time (transmission)[Note 2]	$t_{HD:DAT}$		0	3.45	0	0.9	μs
Setup time of stop condition	$t_{SU:STO}$		4.0		0.6		μs
Bus-free time	t_{BUF}		4.7		1.3		μs

Notes 1. The first clock pulse is generated after this period when the start/restart condition is detected.

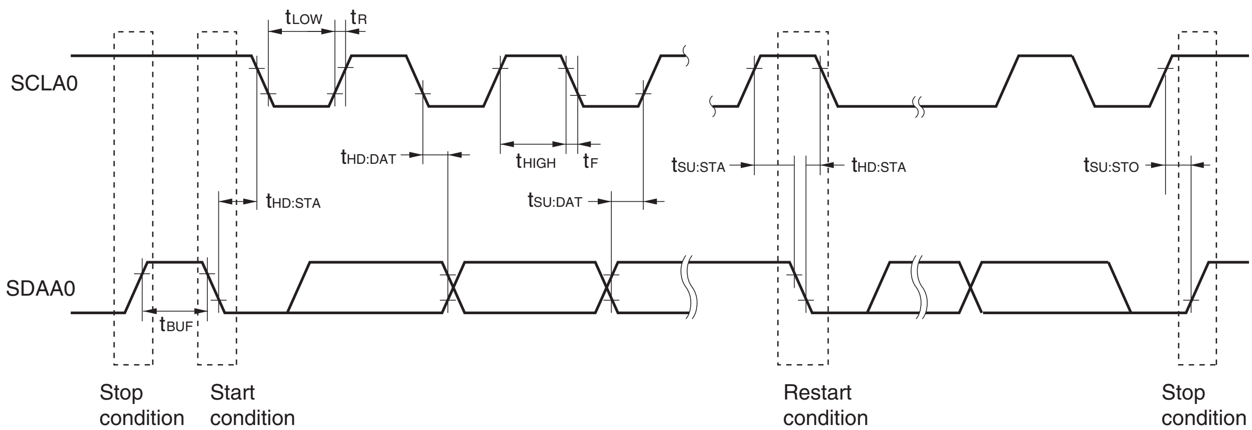
<R> **2.** The maximum value (MAX.) of $t_{HD:DAT}$ is during normal transfer and a wait state is inserted in the ACK (acknowledge) timing.

Caution Only in the 30-pin products, the values in the above table are applied even when bit 2 (PIOR2) in the peripheral I/O redirection register (PIOR) is 1. At this time, the pin characteristics (I_{OH1}, I_{OL1}, V_{OH1}, V_{OL1}) must satisfy the values in the redirect destination.

Remark The maximum value of C_b (communication line capacitance) and the value of R_b (communication line pull-up resistor) at that time in each mode are as follows.

Normal mode: C_b = 400 pF, Rb = 2.7 kΩ
Fast mode: C_b = 320 pF, Rb = 1.1 kΩ

IICA serial transfer timing



3.6 Analog Characteristics

3.6.1 A/D converter characteristics

Classification of A/D converter characteristics

Input channel	Reference Voltage		
	Reference voltage (+) = AV_{REFP} Reference voltage (–) = AV_{REFM}	Reference voltage (+) = V_{DD} Reference voltage (–) = V_{SS}	Reference voltage (+) = V_{BGR} Reference voltage (–) = AV_{REFM}
ANI0 to ANI3	Refer to **29.6.1 (1)**.	Refer to **29.6.1 (3)**.	Refer to **29.6.1 (4)**.
ANI16 to ANI22	Refer to **29.6.1 (2)**.		
Internal reference voltage Temperature sensor output voltage	Refer to **29.6.1 (1)**.		–

(1) When reference voltage (+) = AV_{REFP}/ANI0 (ADREFP1 = 0, ADREFP0 = 1), reference voltage (–) = AV_{REFM}/ANI1 (ADREFM = 1), target pin: ANI2, ANI3, internal reference voltage, and temperature sensor output voltage

(T_A = –40 to +105°C, 2.4 V ≤ AV_{REFP} ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V, Reference voltage (+) = AV_{REFP}, Reference voltage (–) = AV_{REFM} = 0 V)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error[Note 1]	AINL	10-bit resolution AV_{REFP} = V_{DD} [Note 3]			1.2	±3.5	LSB
Conversion time	t_{CONV}	10-bit resolution Target pin: ANI2, ANI3	3.6 V ≤ V_{DD} ≤ 5.5 V	2.125		39	μs
			2.7 V ≤ V_{DD} ≤ 5.5 V	3.1875		39	μs
			2.4 V ≤ V_{DD} ≤ 5.5 V	17		39	μs
		10-bit resolution Target pin: Internal reference voltage, and temperature sensor output voltage (HS (high-speed main) mode)	3.6 V ≤ V_{DD} ≤ 5.5 V	2.375		39	μs
			2.7 V ≤ V_{DD} ≤ 5.5 V	3.5625		39	μs
			2.4 V ≤ V_{DD} ≤ 5.5 V	17		39	μs
Zero-scale error[Notes 1, 2]	EZS	10-bit resolution AV_{REFP} = V_{DD} [Note 3]				±0.25	%FSR
Full-scale error[Notes 1, 2]	EFS	10-bit resolution AV_{REFP} = V_{DD} [Note 3]				±0.25	%FSR
Integral linearity error[Note 1]	ILE	10-bit resolution AV_{REFP} = V_{DD} [Note 3]				±2.5	LSB
Differential linearity error [Note 1]	DLE	10-bit resolution AV_{REFP} = V_{DD} [Note 3]				±1.5	LSB
Analog input voltage	V_{AIN}	ANI2, ANI3		0		AV_{REFP}	V
		Internal reference voltage (HS (high-speed main) mode)		V_{BGR} [Note 4]			V
		Temperature sensor output voltage (HS (high-speed main) mode)		V_{TMPS25} [Note 4]			V

(**Notes** are listed on the next page.)

Notes 1. Excludes quantization error (±1/2 LSB).

2. This value is indicated as a ratio (%FSR) to the full-scale value.

3. When AV_{REFP} < V_{DD}, the MAX. values are as follows.

Overall error: Add ±1.0 LSB to the MAX. value when AV_{REFP} = V_{DD}.

Zero-scale error/Full-scale error: Add ±0.05%FSR to the MAX. value when AV_{REFP} = V_{DD}.

Integral linearity error/ Differential linearity error: Add ±0.5 LSB to the MAX. value when AV_{REFP} = V_{DD}.

4. Refer to **29.6.2 Temperature sensor/internal reference voltage characteristics**.

(2) When reference voltage (+) = AV_{REFP}/ANI0 (ADREFP1 = 0, ADREFP0 = 1), reference voltage (–) = AV_{REFM}/ANI1 (ADREFM = 1), target pin: ANI16 to ANI22

(T_A = –40 to +105°C, 2.4 V ≤ AV_{REFP} ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V, Reference voltage (+) = AV_{REFP}, Reference voltage (–) = AV_{REFM} = 0 V)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	R_{ES}			8		10	bit
Overall error Note 1	AINL	10-bit resolution AV_{REFP} = V_{DD} Note 3			1.2	±5.0	LSB
Conversion time	t_{CONV}	10-bit resolution Target ANI pin: ANI16 to ANI22	3.6 V ≤ V_{DD} ≤ 5.5 V	2.125		39	μs
			2.7 V ≤ V_{DD} ≤ 5.5 V	3.1875		39	μs
			2.4 V ≤ V_{DD} ≤ 5.5 V	17		39	μs
Zero-scale error Notes 1, 2	EZS	10-bit resolution AV_{REFP} = V_{DD} Note 3				±0.35	%FSR
Full-scale error Notes 1, 2	EFS	10-bit resolution AV_{REFP} = V_{DD} Note 3				±0.35	%FSR
Integral linearity error Note 1	ILE	10-bit resolution AV_{REFP} = V_{DD} Note 3				±3.5	LSB
Differential linearity error Note 1	DLE	10-bit resolution AV_{REFP} = V_{DD} Note 3				±2.0	LSB
Analog input voltage	V_{AIN}	ANI16 to ANI22		0		AV_{REFP} and V_{DD}	V

Notes 1. Excludes quantization error (±1/2 LSB).

2. This value is indicated as a ratio (%FSR) to the full-scale value.

3. When AV_{REFP} ≤ V_{DD}, the MAX. values are as follows.

Overall error: Add ±4.0 LSB to the MAX. value when AV_{REFP} = V_{DD}.

Zero-scale error/Full-scale error: Add ±0.20%FSR to the MAX. value when AV_{REFP} = V_{DD}.

Integral linearity error/ Differential linearity error: Add ±2.0 LSB to the MAX. value when AV_{REFP} = V_{DD}.

(3) When reference voltage (+) = V_{DD} (ADREFP1 = 0, ADREFP0 = 0), reference voltage (–) = V_{SS} (ADREFM = 0), target pin: ANI0 to ANI3, ANI16 to ANI22, internal reference voltage, and temperature sensor output voltage

(T_A = –40 to +105°C, 2.4 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V, Reference voltage (+) = V_{DD}, Reference voltage (–) = V_{SS})

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	R_{ES}			8		10	bit
Overall error[Note 1]	AINL	10-bit resolution			1.2	±7.0	LSB
Conversion time	t_{CONV}	10-bit resolution Target pin: ANI0 to ANI3, ANI16 to ANI22	3.6 V ≤ V_{DD} ≤ 5.5 V	2.125		39	μs
			2.7 V ≤ V_{DD} ≤ 5.5 V	3.1875		39	μs
			2.4 V ≤ V_{DD} ≤ 5.5 V	17		39	μs
Conversion time	t_{CONV}	10-bit resolution Target pin: internal reference voltage, and temperature sensor output voltage (HS (high-speed main) mode)	3.6 V ≤ V_{DD} ≤ 5.5 V	2.375		39	μs
			2.7 V ≤ V_{DD} ≤ 5.5 V	3.5625		39	μs
			2.4 V ≤ V_{DD} ≤ 5.5 V	17		39	μs
Zero-scale error[Notes 1, 2]	EZS	10-bit resolution				±0.60	%FSR
Full-scale error[Notes 1, 2]	EFS	10-bit resolution				±0.60	%FSR
Integral linearity error[Note 1]	ILE	10-bit resolution				±4.0	LSB
Differential linearity error[Note 1]	DLE	10-bit resolution				±2.0	LSB
Analog input voltage	V_{AIN}	ANI0 to ANI3, ANI16 to ANI22		0		V_{DD}	V
		Internal reference voltage (HS (high-speed main) mode)			V_{BGR}[Note 3]		V
		Temperature sensor output voltage (HS (high-speed main) mode)			V_{TMPS25}[Note 3]		V

Notes 1. Excludes quantization error (±1/2 LSB).

2. This value is indicated as a ratio (%FSR) to the full-scale value.

3. Refer to **29.6.2 Temperature sensor/internal reference voltage characteristics**.

(4) When reference voltage (+) = Internal reference voltage (ADREFP1 = 1, ADREFP0 = 0), reference voltage (–) = AV_{REFM} (ADREFM = 1), target pin: ANI0, ANI2, ANI3, and ANI16 to ANI22

(T_A = –40 to +105°C, 2.4 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V, Reference voltage (+) = V_{BGR} Note 3, Reference voltage (–) = AV_{REFM} Note 4 = 0 V, HS (high-speed main) mode)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Resolution	R_{ES}			8		bit
Conversion time	t_{CONV}	8-bit resolution	17		39	μs
Zero-scale error Notes 1, 2	EZS	8-bit resolution			±0.60	%FSR
Integral linearity error Note 1	ILE	8-bit resolution			±2.0	LSB
Differential linearity error Note 1	DLE	8-bit resolution			±1.0	LSB
Analog input voltage	V_{AIN}		0		V_{BGR} Note 3	V

Notes 1. Excludes quantization error (±1/2 LSB).

2. This value is indicated as a ratio (%FSR) to the full-scale value.

3. Refer to **29.6.2 Temperature sensor/internal reference voltage characteristics**.

4. When reference voltage (–) = V_{SS}, the MAX. values are as follows.
Zero-scale error: Add ±0.35%FSR to the MAX. value when reference voltage (–) = AV_{REFM}.
Integral linearity error: Add ±0.5 LSB to the MAX. value when reference voltage (–) = AV_{REFM}.
Differential linearity error: Add ±0.2 LSB to the MAX. value when reference voltage (–) = AV_{REFM}.

3.6.2 Temperature sensor/internal reference voltage characteristics

(T_A = –40 to +105°C, 2.4 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V, HS (high-speed main) mode

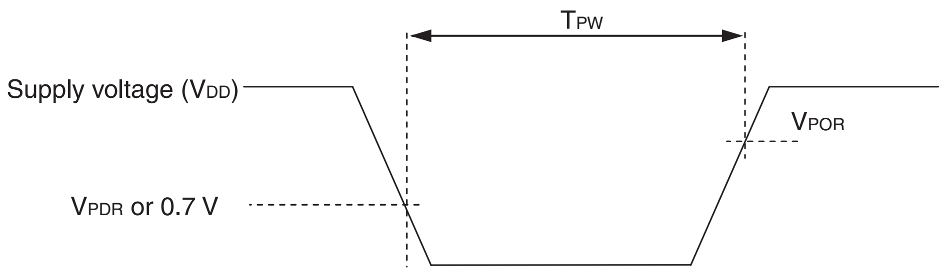
Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Temperature sensor output voltage	V_{TMPS25}	Setting ADS register = 80H, T_A = +25°C		1.05		V
Internal reference voltage	V_{BGR}	Setting ADS register = 81H	1.38	1.45	1.50	V
Temperature coefficient	F_{VTMPS}	Temperature sensor output voltage that depends on the temperature		–3.6		mV/°C
Operation stabilization wait time	t_{AMP}		5			μs

3.6.3 POR circuit characteristics

(T_A = –40 to +105°C, V_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Detection voltage	V_{POR}	Power supply rise time	1.45	1.51	1.57	V
	V_{PDR}	Power supply fall time	1.44	1.50	1.56	V
Minimum pulse width Note	T_{PW}		300			μs

Note Minimum time required for a POR reset when V_{DD} exceeds below V_{PDR}. This is also the minimum time required for a POR reset from when V_{DD} exceeds below 0.7 V to when V_{DD} exceeds V_{POR} while STOP mode is entered or the main system clock is stopped through setting bit 0 (HIOSTOP) and bit 7 (MSTOP) in the clock operation status control register (CSC).



3.6.4 LVD circuit characteristics

LVD Detection Voltage of Reset Mode and Interrupt Mode

(T_A = −40 to +105°C, $V_{PDR} \leq V_{DD} \leq 5.5$ V, V_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Detection supply voltage	V_{LVD0}	Power supply rise time	3.90	4.06	4.22	V
		Power supply fall time	3.83	3.98	4.13	V
	V_{LVD1}	Power supply rise time	3.60	3.75	3.90	V
		Power supply fall time	3.53	3.67	3.81	V
	V_{LVD2}	Power supply rise time	3.01	3.13	3.25	V
		Power supply fall time	2.94	3.06	3.18	V
	V_{LVD3}	Power supply rise time	2.90	3.02	3.14	V
		Power supply fall time	2.85	2.96	3.07	V
	V_{LVD4}	Power supply rise time	2.81	2.92	3.03	V
		Power supply fall time	2.75	2.86	2.97	V
	V_{LVD5}	Power supply rise time	2.70	2.81	2.92	V
		Power supply fall time	2.64	2.75	2.86	V
	V_{LVD6}	Power supply rise time	2.61	2.71	2.81	V
		Power supply fall time	2.55	2.65	2.75	V
	V_{LVD7}	Power supply rise time	2.51	2.61	2.71	V
		Power supply fall time	2.45	2.55	2.65	V
Minimum pulse width	t_{LW}		300			μs
Detection delay time					300	μs

LVD detection voltage of interrupt & reset mode
(T_A = –40 to +105°C, $V_{PDR} \leq V_{DD} \leq 5.5$ V, V_{SS} = 0 V)

Parameter	Symbol	Conditions			MIN.	TYP.	MAX.	Unit
Interrupt and reset mode	V_{LVDD0}	V_{POC2}, V_{POC1}, V_{POC1} = 0, 1, 1, falling reset voltage			2.64	2.75	2.86	V
	V_{LVDD1}		LVIS1, LVIS0 = 1, 0	Rising reset release voltage	2.81	2.92	3.03	V
				Falling interrupt voltage	2.75	2.86	2.97	V
	V_{LVDD2}		LVIS1, LVIS0 = 0, 1	Rising reset release voltage	2.90	3.02	3.14	V
				Falling interrupt voltage	2.85	2.96	3.07	V
	V_{LVDD3}		LVIS1, LVIS0 = 0, 0	Rising reset release voltage	3.90	4.06	4.22	V
				Falling interrupt voltage	3.83	3.98	4.13	V

3.6.5 Power supply voltage rising slope characteristics

(T_A = –40 to +105°C, V_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Power supply voltage rising slope	S_{VDD}				54	V/ms

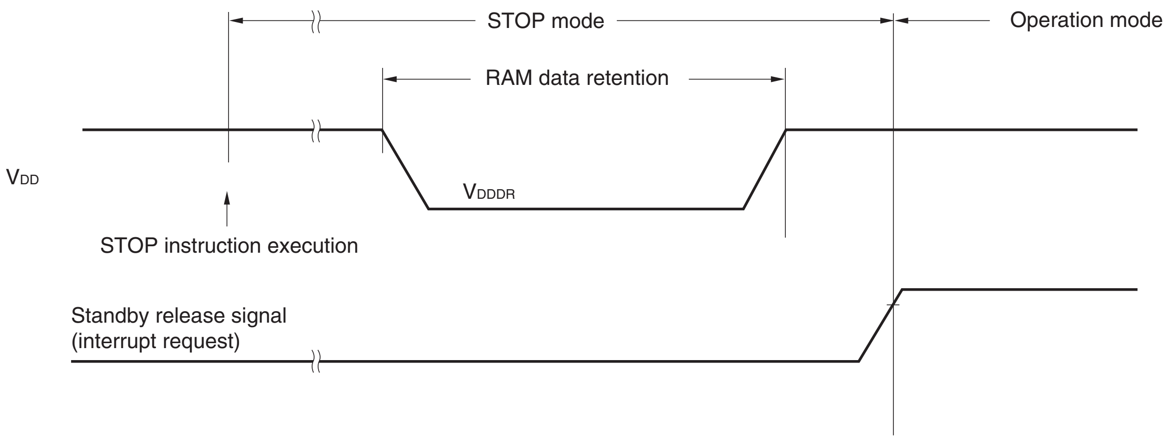
Caution Make sure to keep the internal reset state by the LVD circuit or an external reset until V_{DD} reaches the operating voltage range shown in 29.4 AC Characteristics.

<R> 3.7 RAM Data Retention Characteristics

(T_A = –40 to +105°C, V_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Data retention supply voltage	V_{DDDR}		1.44 Note		5.5	V

<R> Note This depends on the POR detection voltage. For a falling voltage, data in RAM are retained until the voltage reaches the level that triggers a POR reset but not once it reaches the level at which a POR reset is generated.



3.8 Flash Memory Programming Characteristics

(T_A = –40 to +105°C, 2.4 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
<R> System clock frequency	f_{CLK}		1		24	MHz
Code flash memory rewritable times Notes 1, 2, 3	C_{erwr}	Retained for 20 years T_A = 85°C Notes 4	1,000			Times
Data flash memory rewritable times Notes 1, 2, 3		Retained for 1 year T_A = 25°C Notes 4		1,000,000		
		Retained for 5 years T_A = 85°C Notes 4	100,000			
		Retained for 20 years T_A = 85°C Notes 4	10,000			

Notes 1. 1 erase + 1 write after the erase is regarded as 1 rewrite. The retaining years are until next rewrite after the rewrite.

2. When using flash memory programmer and Renesas Electronics self programming library

3. These are the characteristics of the flash memory and the results obtained from reliability testing by Renesas Electronics Corporation.

4. This temperature is the average value at which data are retained.

3.9 Dedicated Flash Memory Programmer Communication (UART)

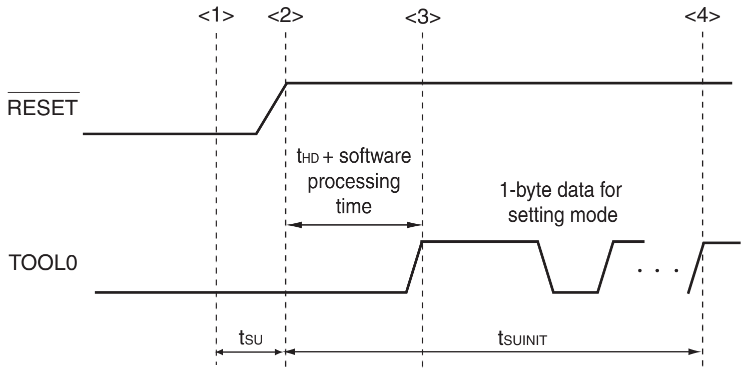
(T_A = –40 to +105°C, 2.4 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Transfer rate		During serial programming	115,200		1,000,000	bps

3.10 Timing of Entry to Flash Memory Programming Modes

(T_A = –40 to +105°C, 2.4 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Time to complete the communication for the initial setting after the external reset is released	t_{SUINIT}	POR and LVD reset are released before external release			100	ms
Time to release the external reset after the TOOL0 pin is set to the low level	t_{SU}	POR and LVD reset are released before external release	10			μs
Time to hold the TOOL0 pin at the low level after the external reset is released (excluding the processing time of the firmware to control the flash memory)	t_{HD}	POR and LVD reset are released before external release	1			ms



<1> The low level is input to the TOOL0 pin.

<2> The external reset is released (POR and LVD reset must be released before the external reset is released.).

<3> The TOOL0 pin is set to the high level.

<4> Setting of the flash memory programming mode by UART reception and complete the baud rate setting.

Remark t_{SUINIT}: Communication for the initial setting must be completed within 100 ms after the external reset is released during this period.

t_{SU}: Time to release the external reset after the TOOL0 pin is set to the low level

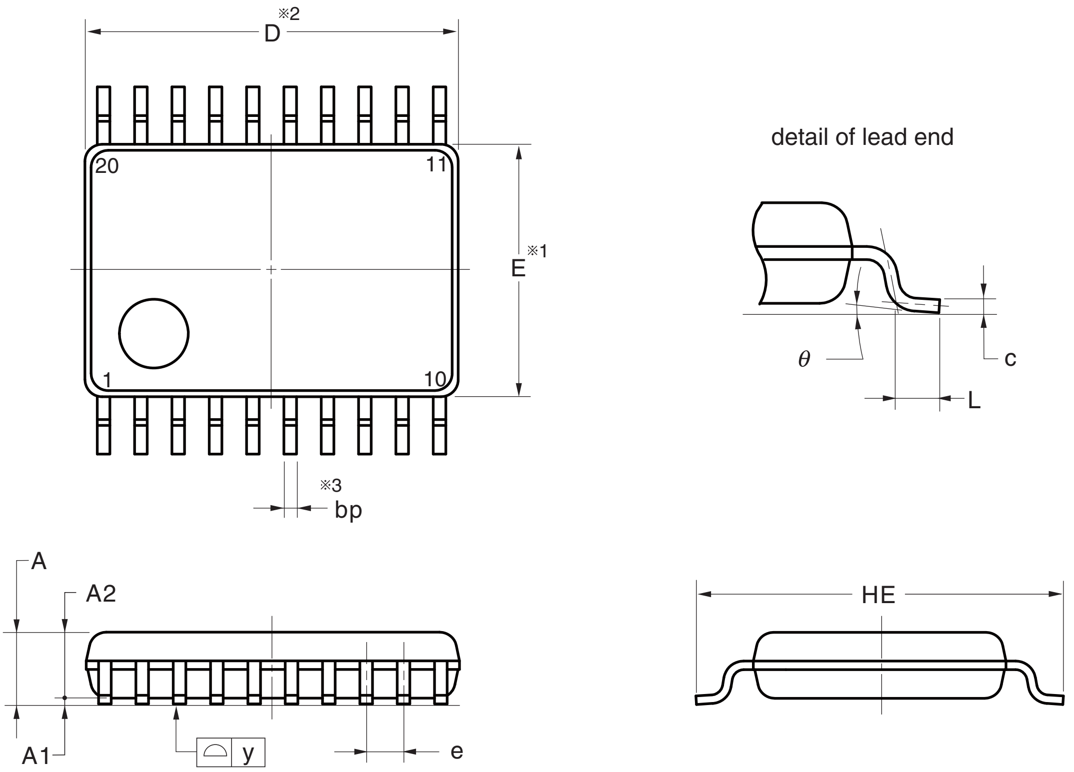
t_{HD}: Time to hold the TOOL0 pin at the low level after the external reset is released (excluding the processing time of the firmware to control the flash memory)

4. PACKAGE DRAWINGS

4.1 20-pin products

R5F1026AASP, R5F10269ASP, R5F10268ASP, R5F10267ASP, R5F10266ASP
R5F1036AASP, R5F10369ASP, R5F10368ASP, R5F10367ASP, R5F10366ASP
R5F1026ADSP, R5F10269DSP, R5F10268DSP, R5F10267DSP, R5F10266DSP
R5F1036ADSP, R5F10369DSP, R5F10368DSP, R5F10367DSP, R5F10366DSP
<R> R5F1026AGSP, R5F10269GSP, R5F10268GSP, R5F10267GSP, R5F10266GSP

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LSSOP20-4.4x6.5-0.65	PLSP0020JB-A	P20MA-65-NAA-1	0.1



(UNIT:mm)

ITEM	DIMENSIONS
D	6.50±0.10
E	4.40±0.10
HE	6.40±0.20
A	1.45 MAX.
A1	0.10±0.10
A2	1.15
e	0.65±0.12
bp	$0.22^{+0.10}_{-0.05}$
c	$0.15^{+0.05}_{-0.02}$
L	0.50±0.20
y	0.10
θ	0° to 10°

NOTE

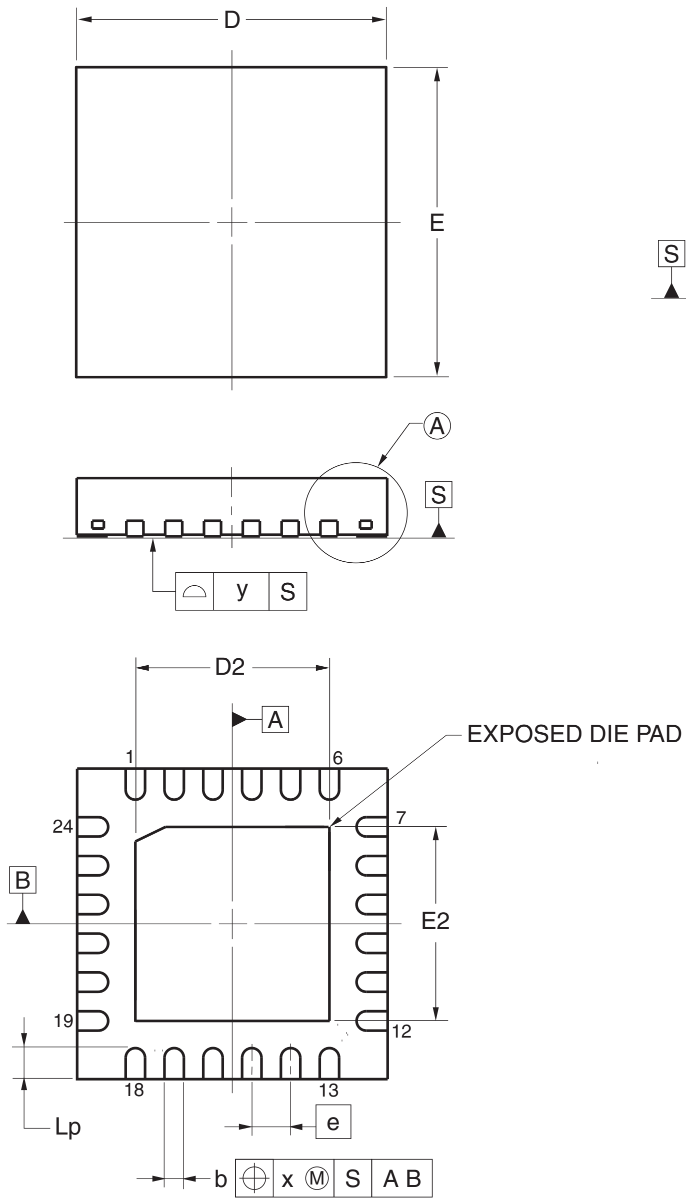
1.Dimensions "※1" and "※2" do not include mold flash.

2.Dimension "※3" does not include trim offset.

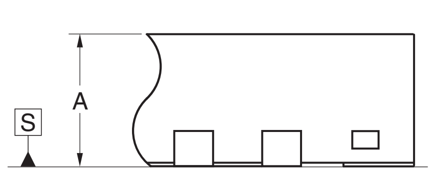
4.2 24-pin products

R5F1027AANA, R5F10279ANA, R5F10278ANA, R5F10277ANA
R5F1037AANA, R5F10379ANA, R5F10378ANA, R5F10377ANA
R5F1027ADNA, R5F10279DNA, R5F10278DNA, R5F10277DNA
R5F1037ADNA, R5F10379DNA, R5F10378DNA, R5F10377DNA
<R> R5F1027AGNA, R5F10279GNA, R5F10278GNA, R5F10277GNA

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-HWQFN24-4x4-0.50	PWQN0024KE-A	P24K8-50-CAB-1	0.04



DETAIL OF (A) PART



(UNIT:mm)

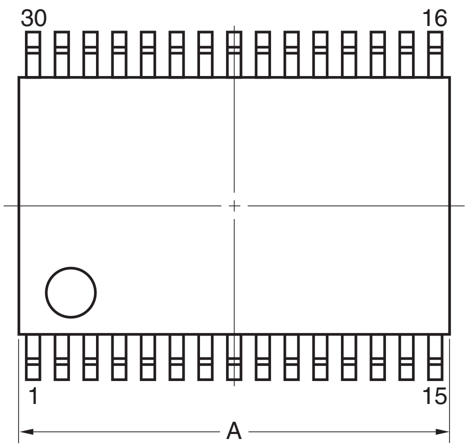
ITEM	DIMENSIONS
D	4.00±0.05
E	4.00±0.05
A	0.75±0.05
b	$0.25^{+0.05}_{-0.07}$
e	0.50
Lp	0.40±0.10
x	0.05
y	0.05

ITEM		D2			E2		
		MIN	NOM	MAX	MIN	NOM	MAX
EXPOSED DIE PAD VARIATIONS	A	2.45	2.50	2.55	2.45	2.50	2.55

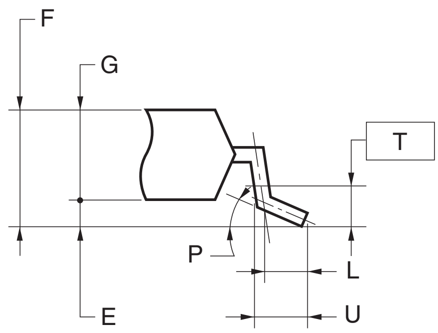
4.3 30-pin products

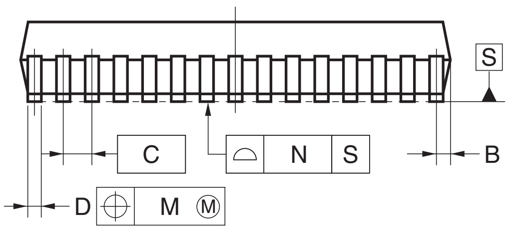
R5F102AAASP, R5F102A9ASP, R5F102A8ASP, R5F102A7ASP
R5F103AAASP, R5F103A9ASP, R5F103A8ASP, R5F103A7ASP
R5F102AADSP, R5F102A9DSP, R5F102A8DSP, R5F102A7DSP
R5F103AADSP, R5F103A9DSP, R5F103A8DSP, R5F103A7DSP
<R> R5F102AAGSP, R5F102A9GSP, R5F102A8GSP, R5F102A7GSP

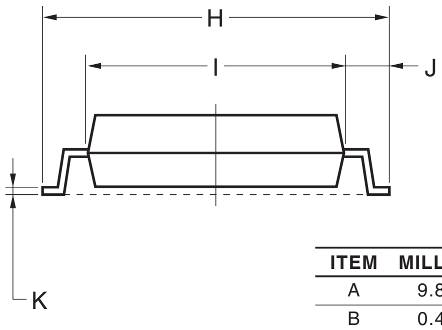
JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LSSOP30-0300-0.65	PLSP0030JB-B	S30MC-65-5A4-3	0.18



detail of lead end







ITEM	MILLIMETERS
A	9.85±0.15
B	0.45 MAX.
C	0.65 (T.P.)
D	$0.24^{+0.08}_{-0.07}$
E	0.1±0.05
F	1.3±0.1
G	1.2
H	8.1±0.2
I	6.1±0.2
J	1.0±0.2
K	0.17±0.03
L	0.5
M	0.13
N	0.10
P	$3°^{+5°}_{-3°}$
T	0.25
U	0.6±0.15

NOTE

Each lead centerline is located within 0.13 mm of its true position (T.P.) at maximum material condition.

Rev.	Date	Description	
		Page	Summary
1.00	Dec 10, 2012	-	First Edition issued
2.00	Sep 06, 2013	1	Modification of 1.1 Features
		3	Modification of 1.2 List of Part Numbers
		4	Modification of Table 1-1. List of Ordering Part Numbers, Note, and Caution
		7 to 9	Modification of package name in 1.4.1 to 1.4.3
		14	Modification of tables in 1.7 Outline of Functions
		17	Modification of description of table in 2.1 Absolute Maximum Ratings (T_A = 25°C)
		18	Modification of table, Note, and Caution in 2.2.1 X1 oscillator characteristics
		18	Modification of table in 2.2.2 On-chip oscillator characteristics
		19	Modification of Note 3 in 2.3.1 Pin characteristics (1/4)
		20	Modification of Note 3 in 2.3.1 Pin characteristics (2/4)
		23	Modification of Notes 1 and 2 in (1) 20-, 24-pin products (1/2)
		24	Modification of Notes 1 and 3 in (1) 20-, 24-pin products (2/2)
		25	Modification of Notes 1 and 2 in (2) 30-pin products (1/2)
		26	Modification of Notes 1 and 3 in (2) 30-pin products (2/2)
		27	Modification of (3) Peripheral functions (Common to all products)
		28	Modification of table in 2.4 AC Characteristics
		29	Addition of Minimum Instruction Execution Time during Main System Clock Operation
		30	Modification of figures of AC Timing Test Point and External Main System Clock Timing
		31	Modification of figure of AC Timing Test Point
		31	Modification of description and Note 2 in (1) During communication at same potential (UART mode)
		32	Modification of description in (2) During communication at same potential (CSI mode)
		33	Modification of description in (3) During communication at same potential (CSI mode)
		34	Modification of description in (4) During communication at same potential (CSI mode)
		36	Modification of table and Note 2 in (5) During communication at same potential (simplified I^2C mode)
		38, 39	Modification of table and Notes 1 to 9 in (6) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode)
		40	Modification of Remarks 1 to 3 in (6) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode)
		41	Modification of table in (7) Communication at different potential (2.5 V, 3 V) (CSI mode)
		42	Modification of Caution in (7) Communication at different potential (2.5 V, 3 V) (CSI mode)
		43	Modification of table in (8) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (1/3)
		44	Modification of table and Notes 1 and 2 in (8) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (2/3)
		45	Modification of table, Note 1, and Caution 1 in (8) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (3/3)
		47	Modification of table in (9) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode)
		50	Modification of table, Note 1, and Caution 1 in (10) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified I^2C mode)
		52	Modification of Remark in 2.5.2 Serial interface IICA
		53	Addition of table to 2.6.1 A/D converter characteristics
		53	Modification of description in 2.6.1 (1)
		54	Modification of Notes 3 to 5 in 2.6.1 (1)
		54	Modification of description and Notes 2 to 4 in 2.6.1 (2)

Rev.	Date	Description	
		Page	Summary
2.00	Sep 06, 2013	55	Modification of description and Notes 3 and 4 in 2.6.1 (3)
		56	Modification of description and Notes 3 and 4 in 2.6.1 (4)
		57	Modification of table in 2.6.2 Temperature sensor/internal reference voltage characteristics
		57	Modification of table and Note in 2.6.3 POR circuit characteristics
		58	Modification of table in 2.6.4 LVD circuit characteristics
		59	Modification of table of LVD detection voltage of interrupt & reset mode
		59	Modification of number and title to 2.6.5 Power supply voltage rising slope characteristics
		61	Modification of table, figure, and Remark in 2.10 Timing of Entry to Flash Memory Programming Modes
		62 to 103	Addition of products of industrial applications (G: T_A = -40 to +105°C)
		104 to 106	Addition of products of industrial applications (G: T_A = -40 to +105°C)
2.10	Mar 25, 2016	6	Modification of Figure 1-1 Part Number, Memory Size, and Package of RL78/G12
		7	Modification of Table 1-1 List of Ordering Part Numbers
		8	Addition of product name (RL78/G12) and description (Top View) in 1.4.1 20-pin products
		9	Addition of product name (RL78/G12) and description (Top View) in 1.4.2 24-pin products
		10	Addition of product name (RL78/G12) and description (Top View) in 1.4.3 30-pin products
		15	Modification of description in 1.7 Outline of Functions
		16	Modification of description, and addition of target products
		52	Modification of note 2 in 2.5.2 Serial interface IICA
		60	Modification of title and note, and addition of caution in 2.7 RAM Data Retention Characteristics
		60	Modification of conditions in 2.8 Flash Memory Programming Characteristics
		62	Modification of description, and addition of target products and remark
		94	Modification of note 2 in 3.5.2 Serial interface IICA
		102	Modification of title and note in 3.7 RAM Data Retention Characteristics
		102	Modification of conditions in 3.8 Flash Memory Programming Characteristics
		104 to 106	Addition of package name

NOTES FOR CMOS DEVICES

(1) VOLTAGE APPLICATION WAVEFORM AT INPUT PIN: Waveform distortion due to input noise or a reflected wave may cause malfunction. If the input of the CMOS device stays in the area between VIL (MAX) and VIH (MIN) due to noise, etc., the device may malfunction. Take care to prevent chattering noise from entering the device when the input level is fixed, and also in the transition period when the input level passes through the area between VIL (MAX) and VIH (MIN).

(2) HANDLING OF UNUSED INPUT PINS: Unconnected CMOS device inputs can be cause of malfunction. If an input pin is unconnected, it is possible that an internal input level may be generated due to noise, etc., causing malfunction. CMOS devices behave differently than Bipolar or NMOS devices. Input levels of CMOS devices must be fixed high or low by using pull-up or pull-down circuitry. Each unused pin should be connected to VDD or GND via a resistor if there is a possibility that it will be an output pin. All handling related to unused pins must be judged separately for each device and according to related specifications governing the device.

(3) PRECAUTION AGAINST ESD: A strong electric field, when exposed to a MOS device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it when it has occurred. Environmental control must be adequate. When it is dry, a humidifier should be used. It is recommended to avoid using insulators that easily build up static electricity. Semiconductor devices must be stored and transported in an anti-static container, static shielding bag or conductive material. All test and measurement tools including work benches and floors should be grounded. The operator should be grounded using a wrist strap. Semiconductor devices must not be touched with bare hands. Similar precautions need to be taken for PW boards with mounted semiconductor devices.

(4) STATUS BEFORE INITIALIZATION: Power-on does not necessarily define the initial status of a MOS device. Immediately after the power source is turned ON, devices with reset functions have not yet been initialized. Hence, power-on does not guarantee output pin levels, I/O settings or contents of registers. A device is not initialized until the reset signal is received. A reset operation must be executed immediately after power-on for devices with reset functions.

(5) POWER ON/OFF SEQUENCE: In the case of a device that uses different power supplies for the internal operation and external interface, as a rule, switch on the external power supply after switching on the internal power supply. When switching the power supply off, as a rule, switch off the external power supply and then the internal power supply. Use of the reverse power on/off sequences may result in the application of an overvoltage to the internal elements of the device, causing malfunction and degradation of internal elements due to the passage of an abnormal current. The correct power on/off sequence must be judged separately for each device and according to related specifications governing the device.

(6) INPUT OF SIGNAL DURING POWER OFF STATE : Do not input signals or an I/O pull-up power supply while the device is not powered. The current injection that results from input of such a signal or I/O pull-up power supply may cause malfunction and the abnormal current that passes in the device at this time may cause degradation of internal elements. Input of signals during the power off state must be judged separately for each device and according to related specifications governing the device.

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